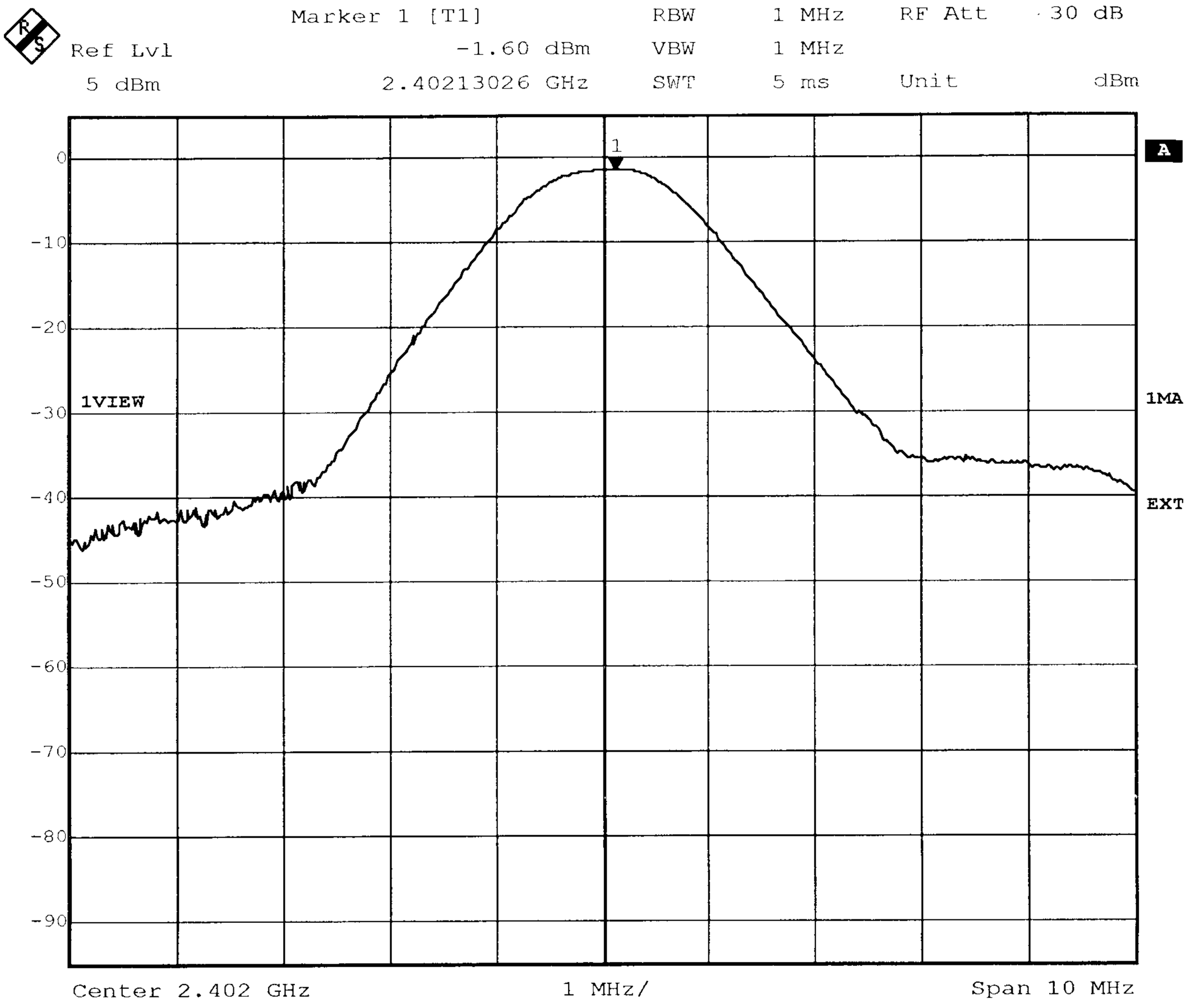
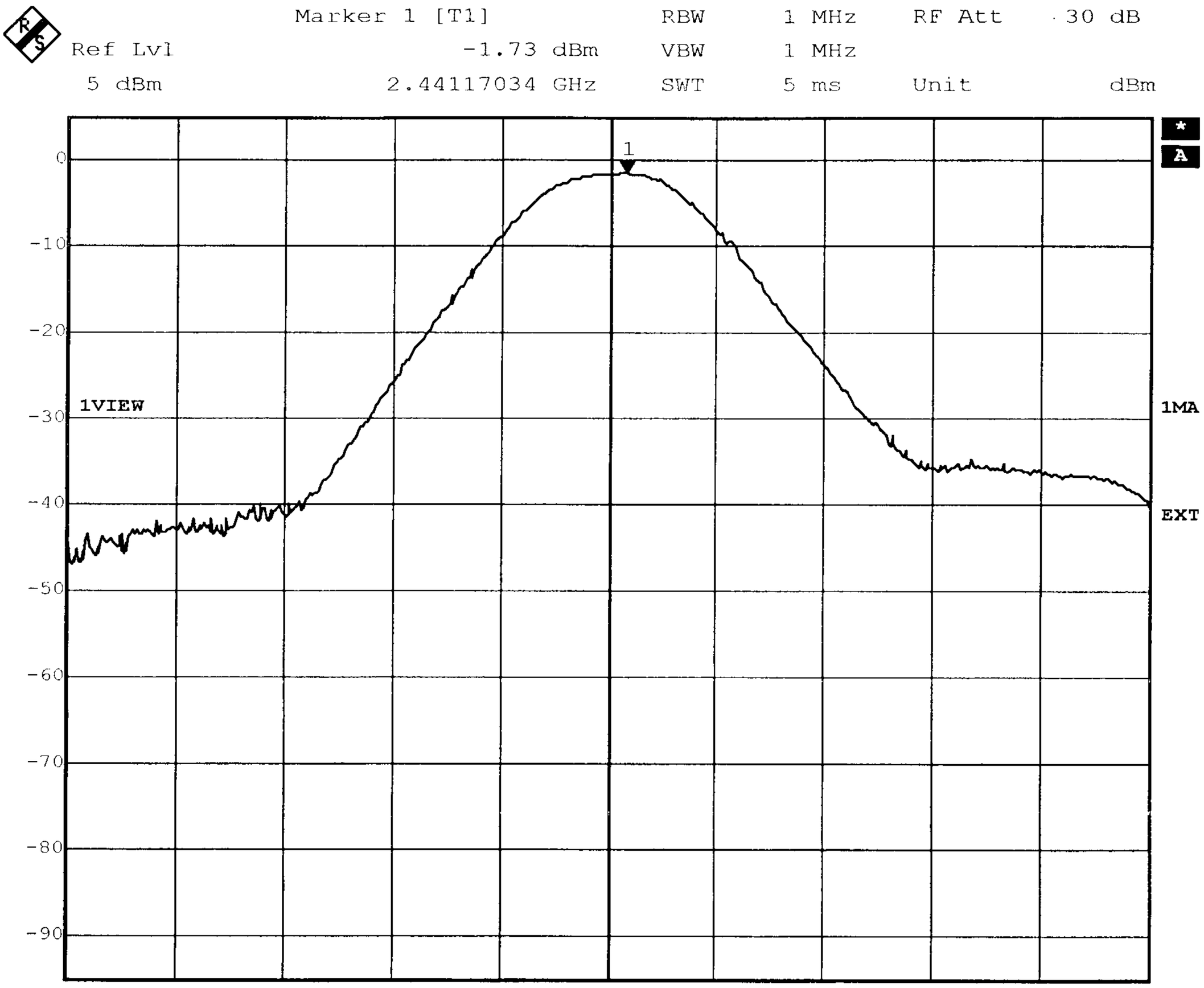
Appendix B

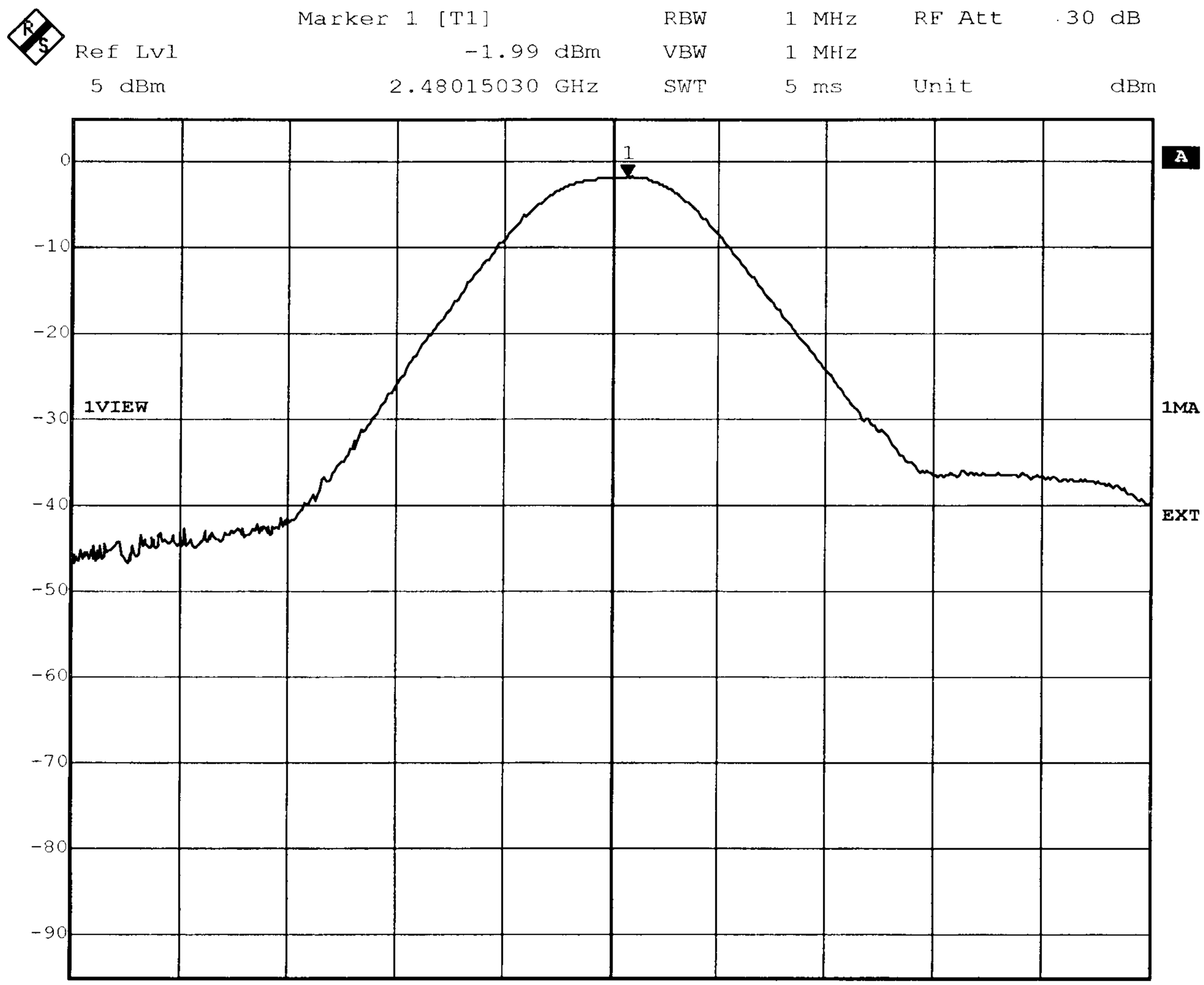
Peak Output Power



Title: Peak Output Power conducted Ch.: 0
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 11:22:01



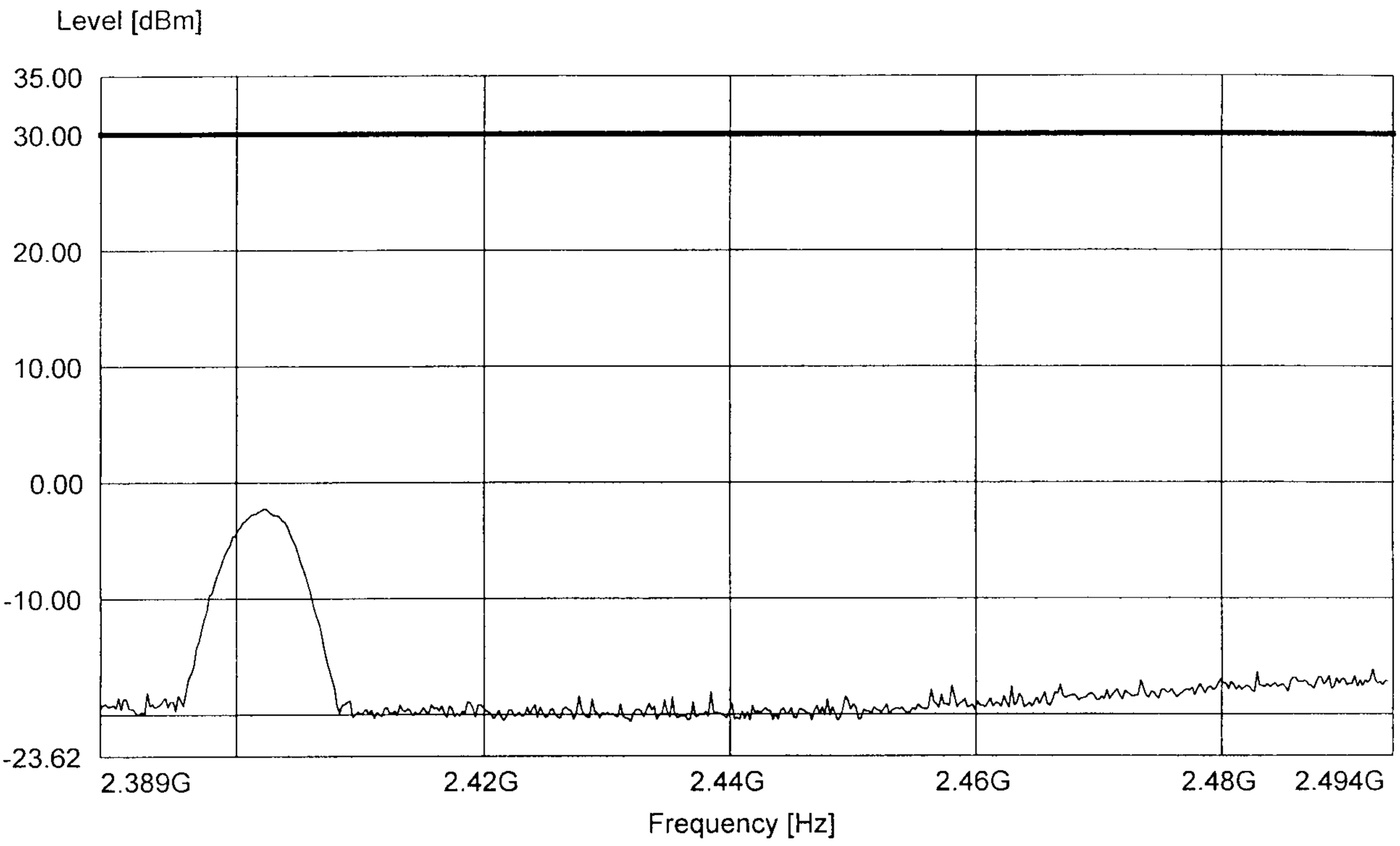
Title: Peak Output Power Conducted Ch.: 39
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 11:00:47



Title: Peak Output Power conducted Ch.: 78
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 11:23:57

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

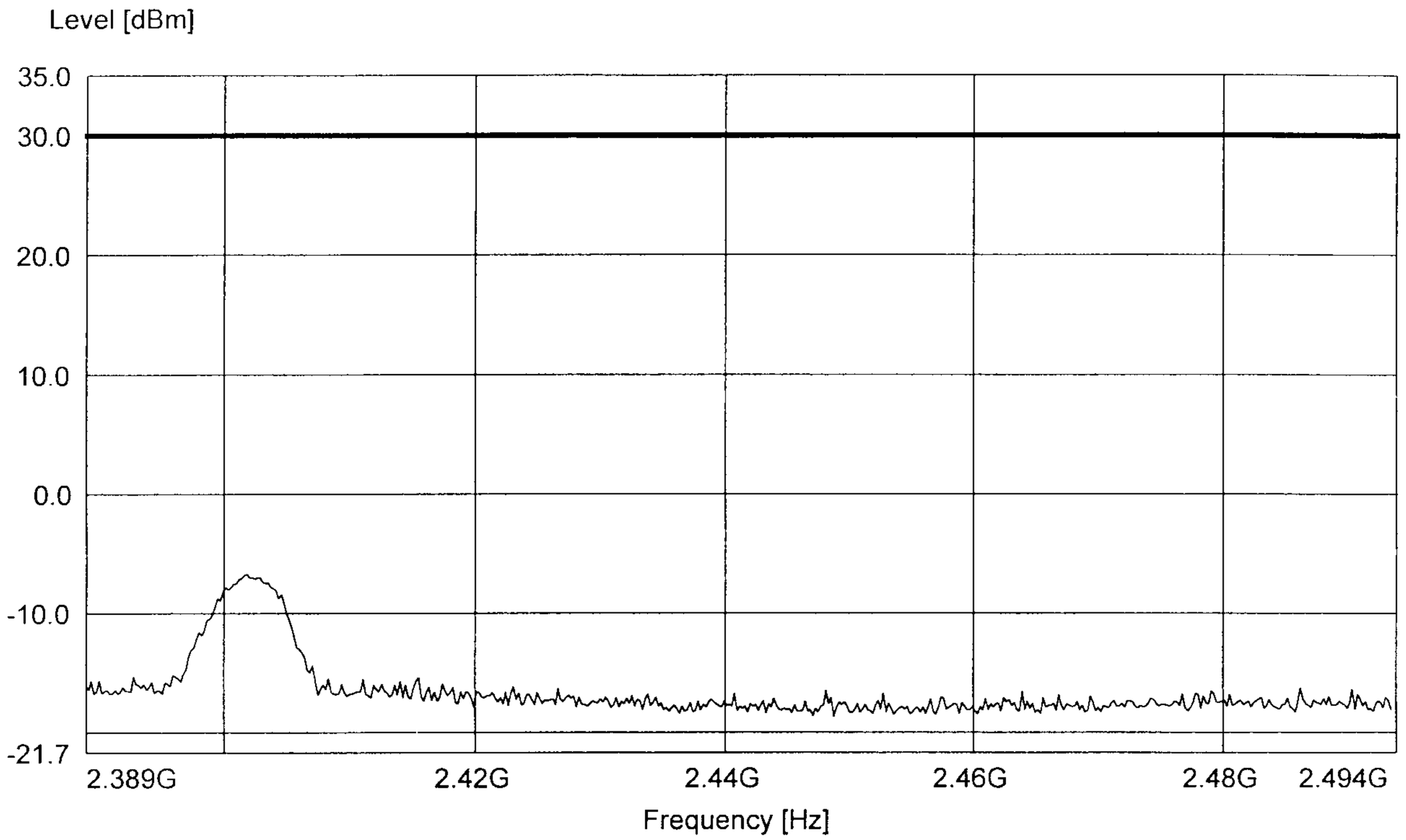
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.402GHz, Pmax: -2.25dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM - FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

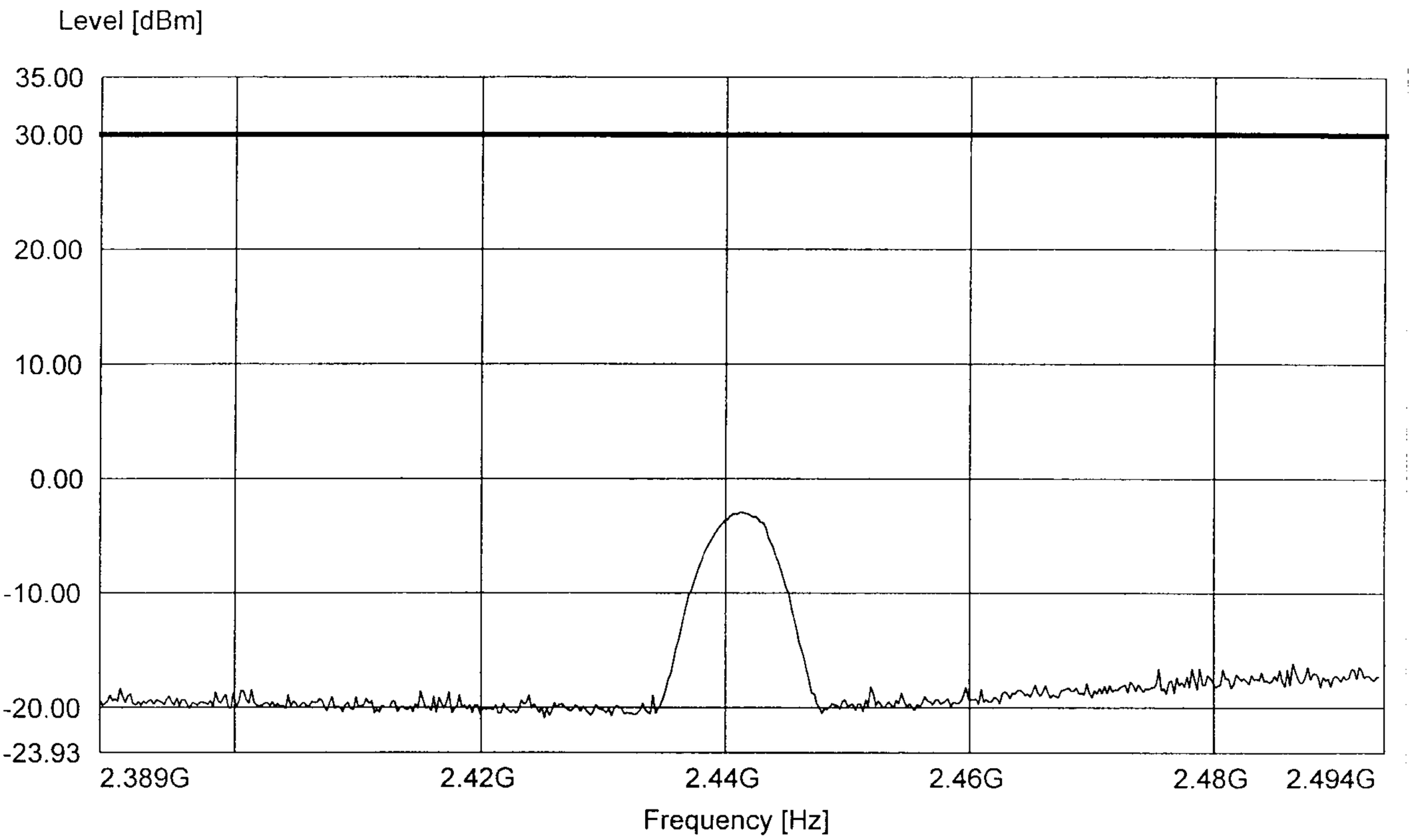
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.402GHz, Pmax: -6.73dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

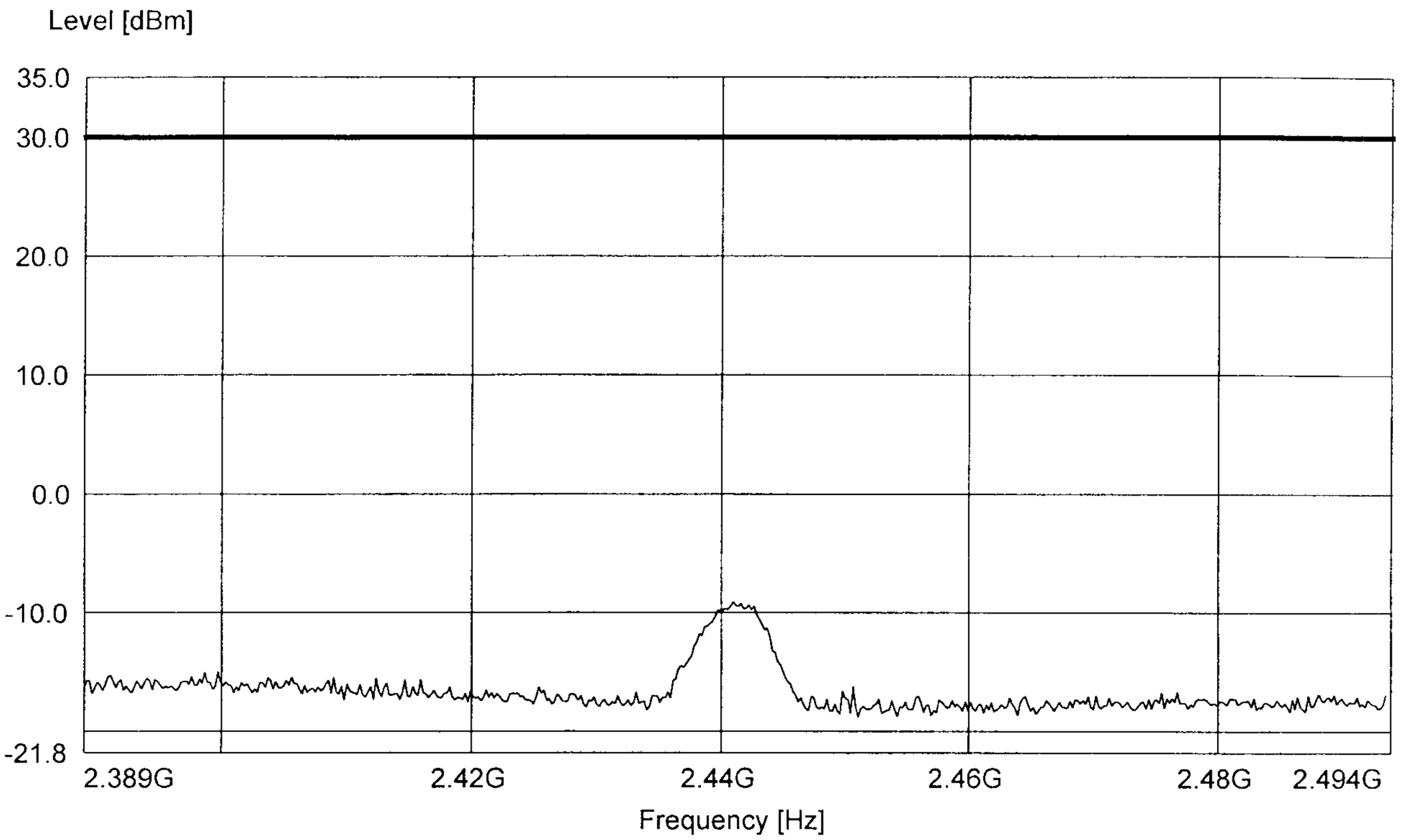
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.441GHz, Pmax: -2.89dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

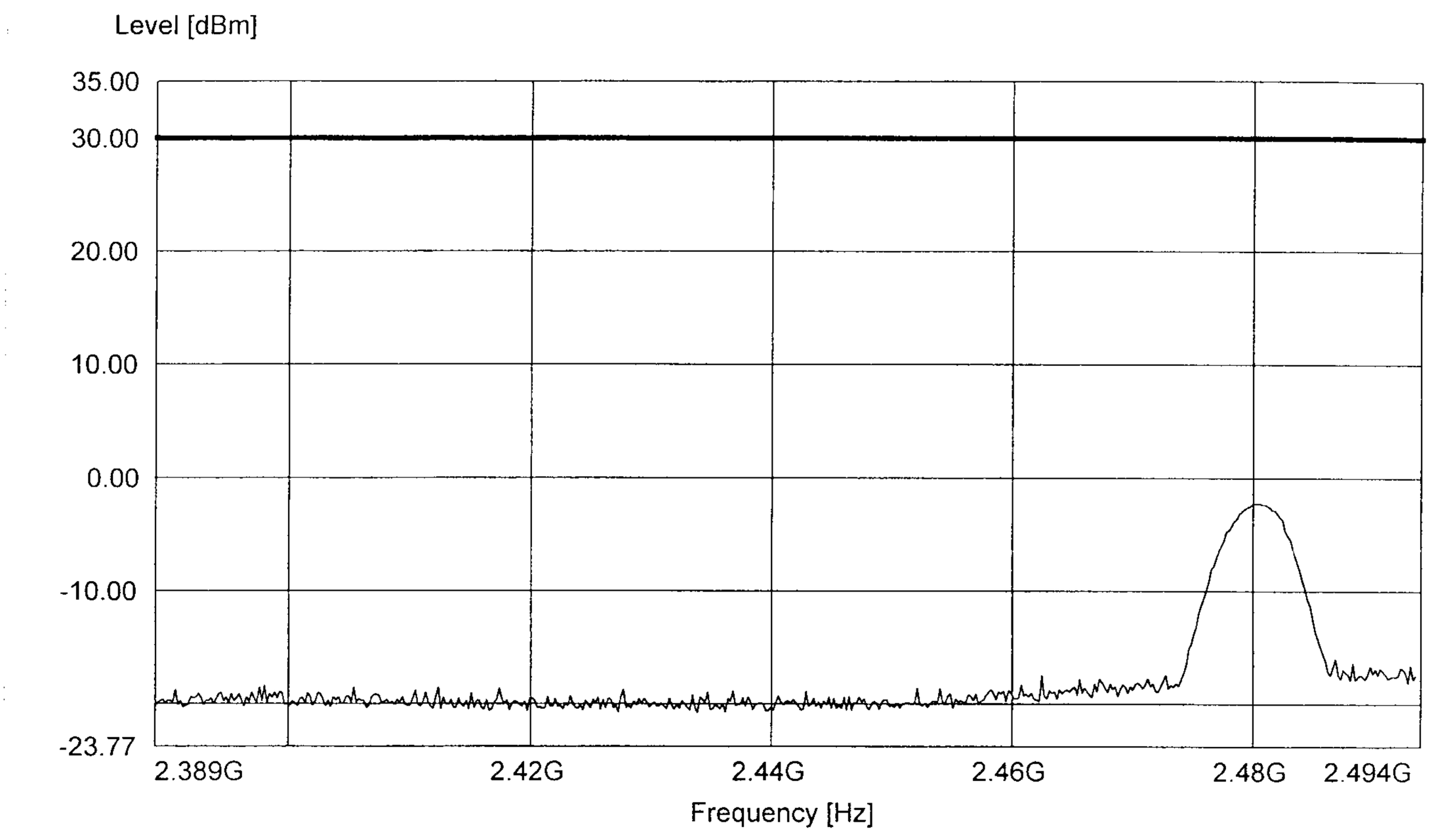
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.441GHz, Pmax: -9.07dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM - FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

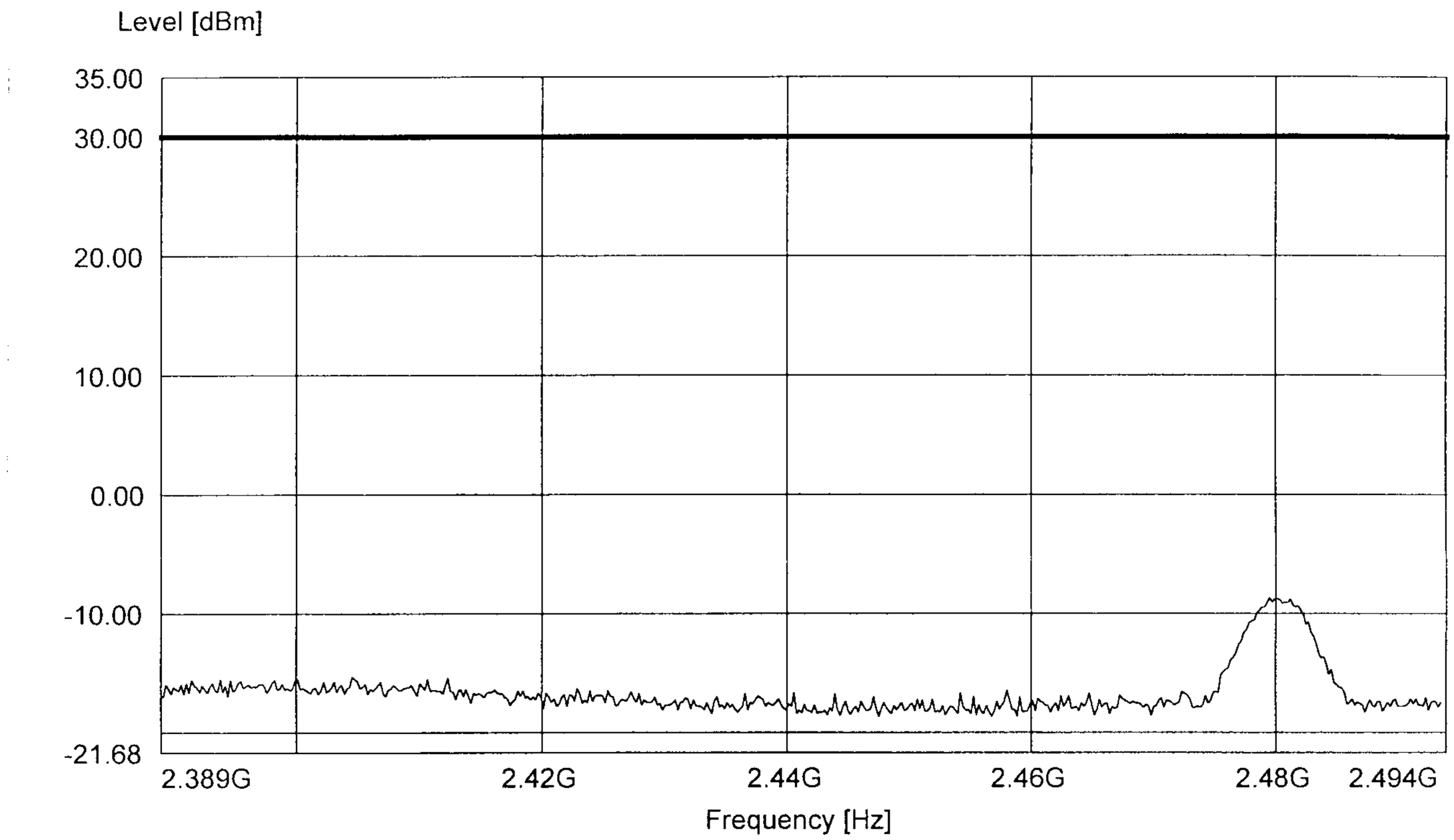
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.481GHz, Pmax: -2.24dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

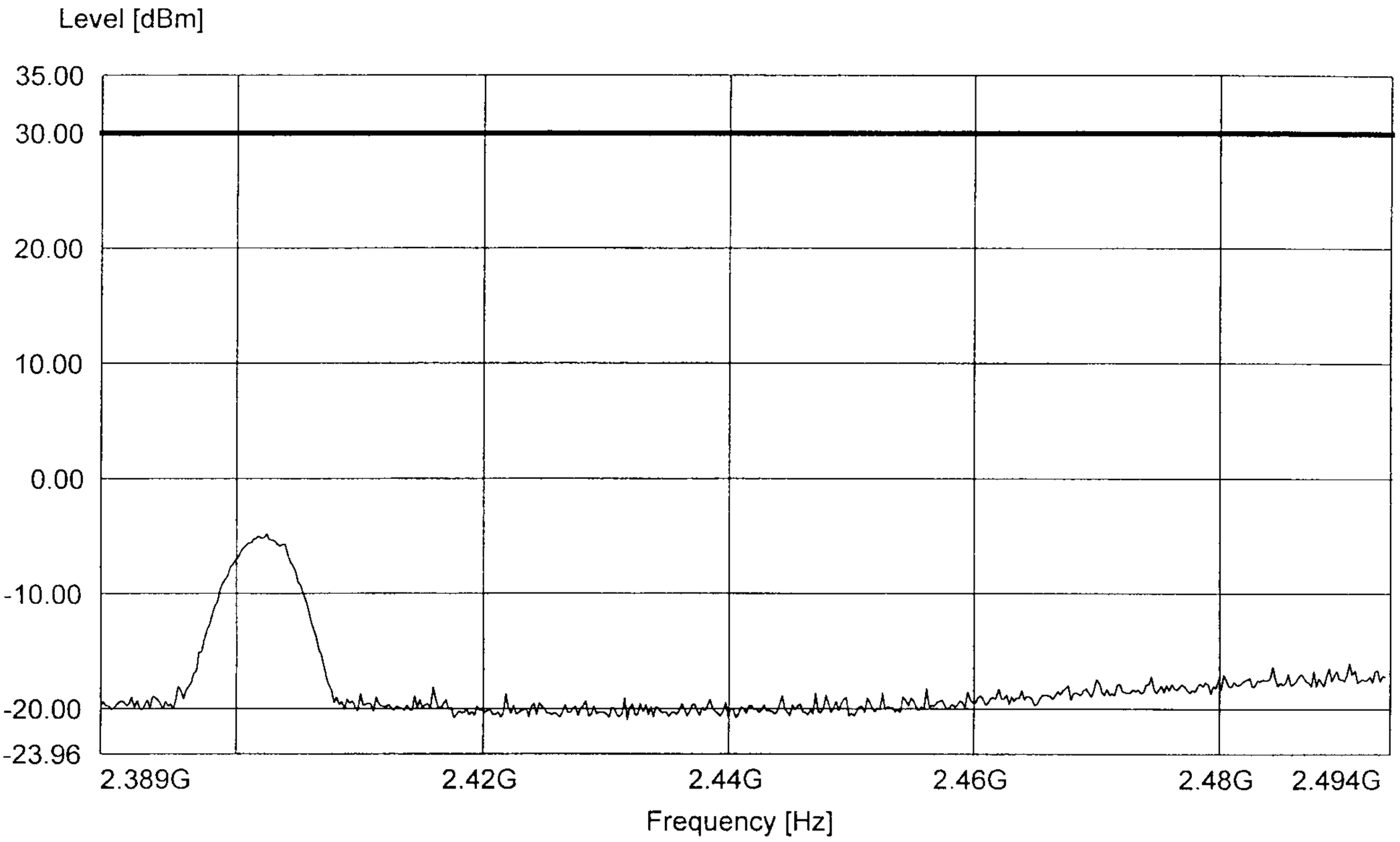
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.479GHz, Pmax: -8.69dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

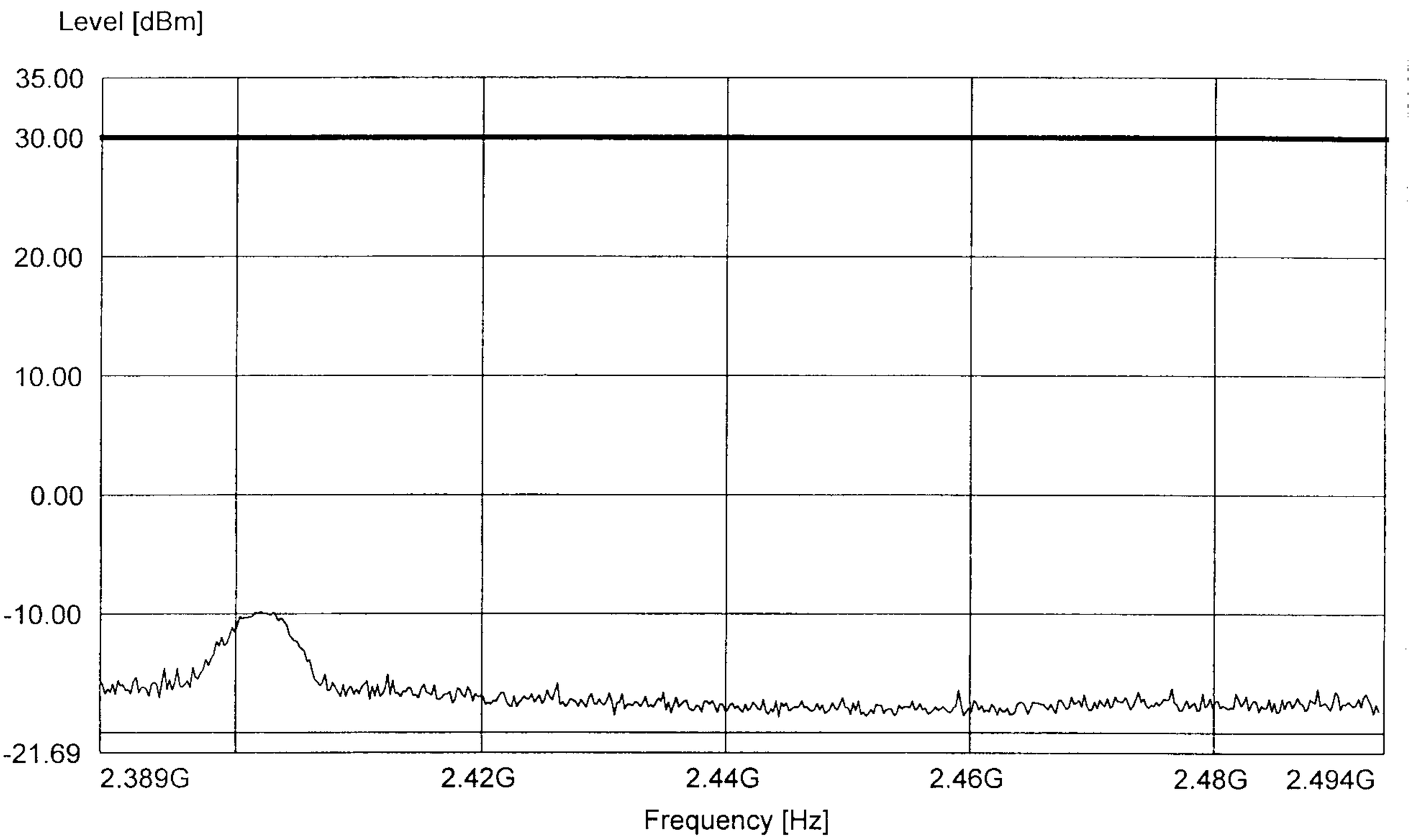
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.402GHz, Pmax: -4.82dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

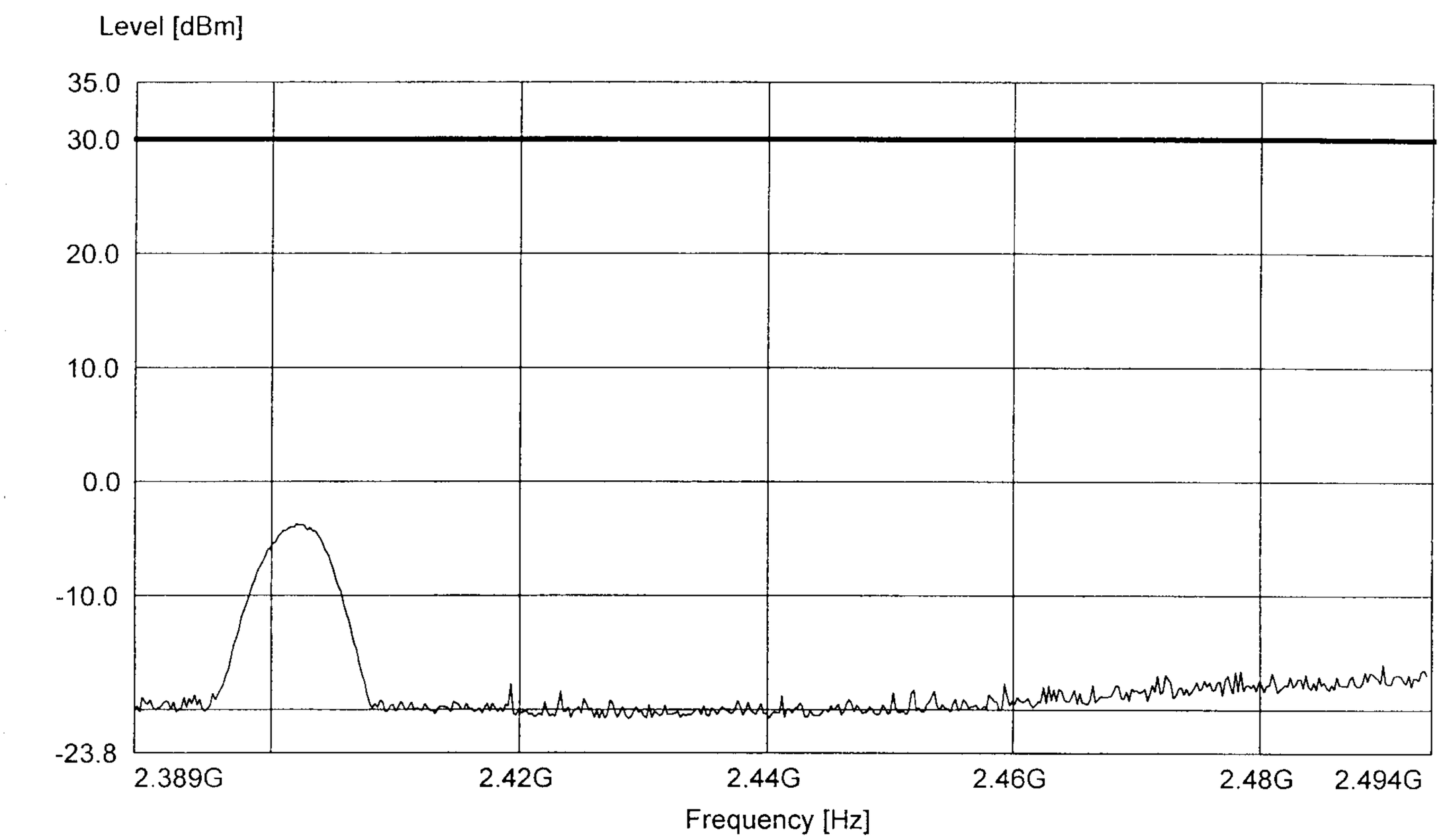
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.402GHz, Pmax: -9.82dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

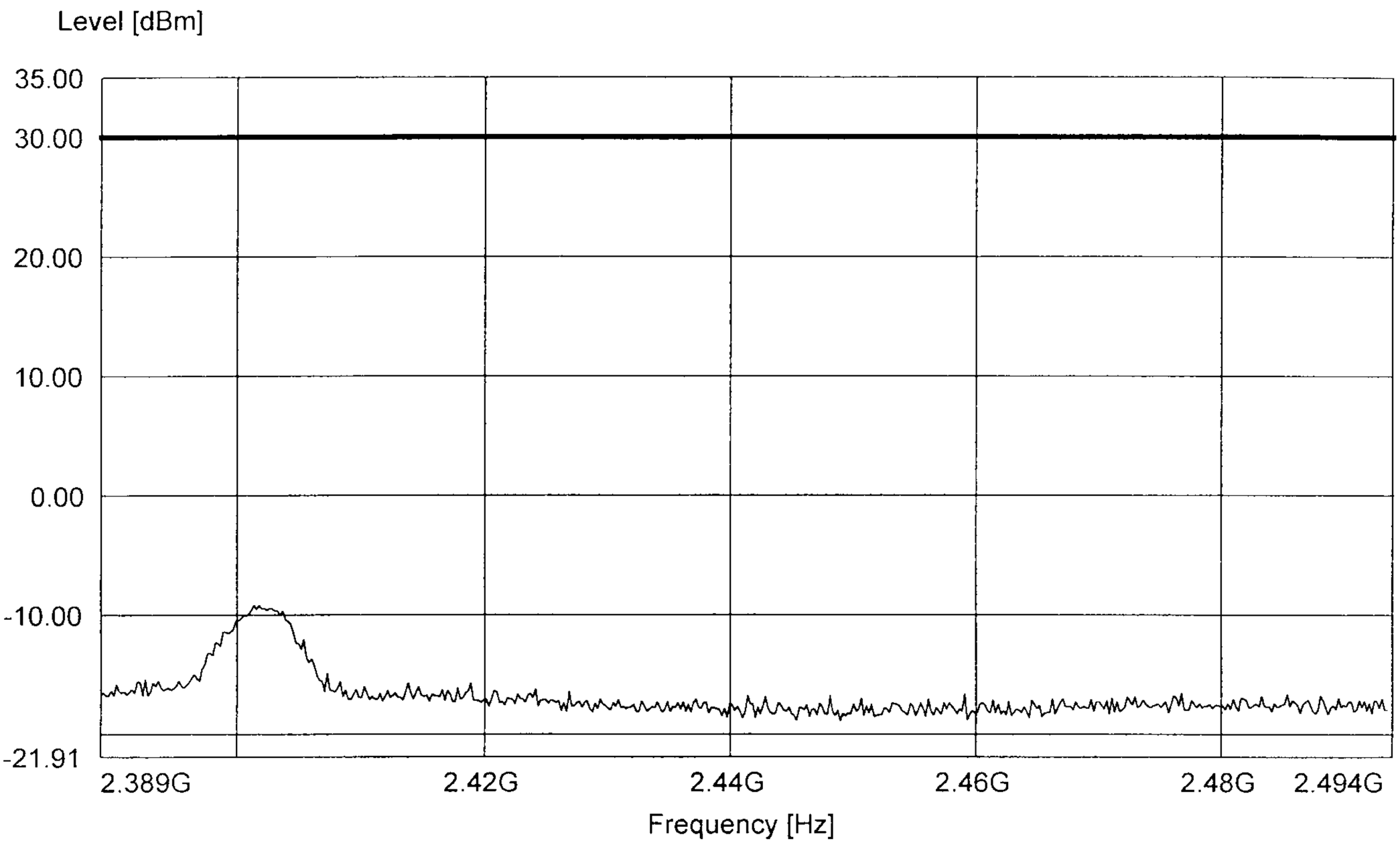
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.402GHz, Pmax: -3.72dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

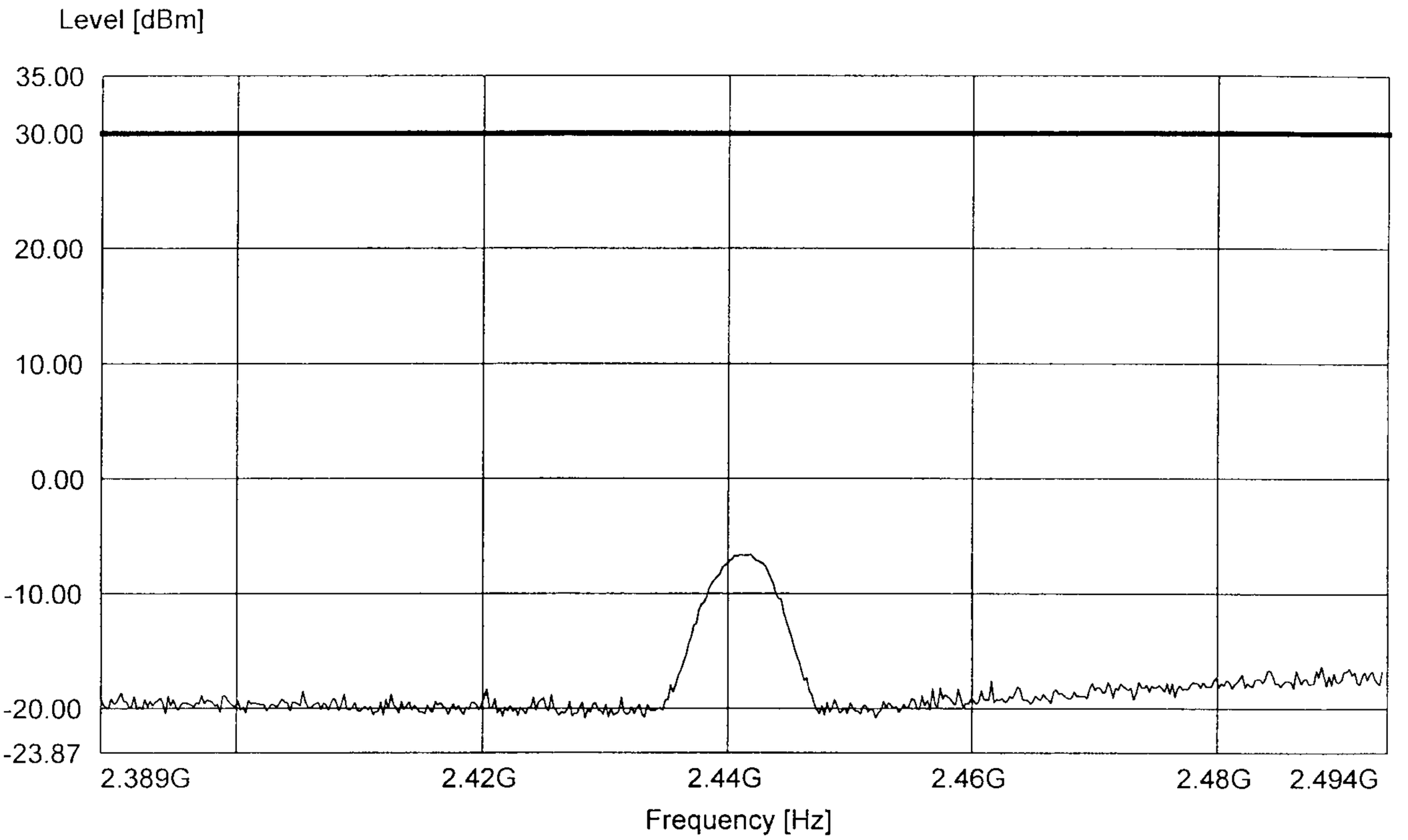
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.401GHz, Pmax: -9.19dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

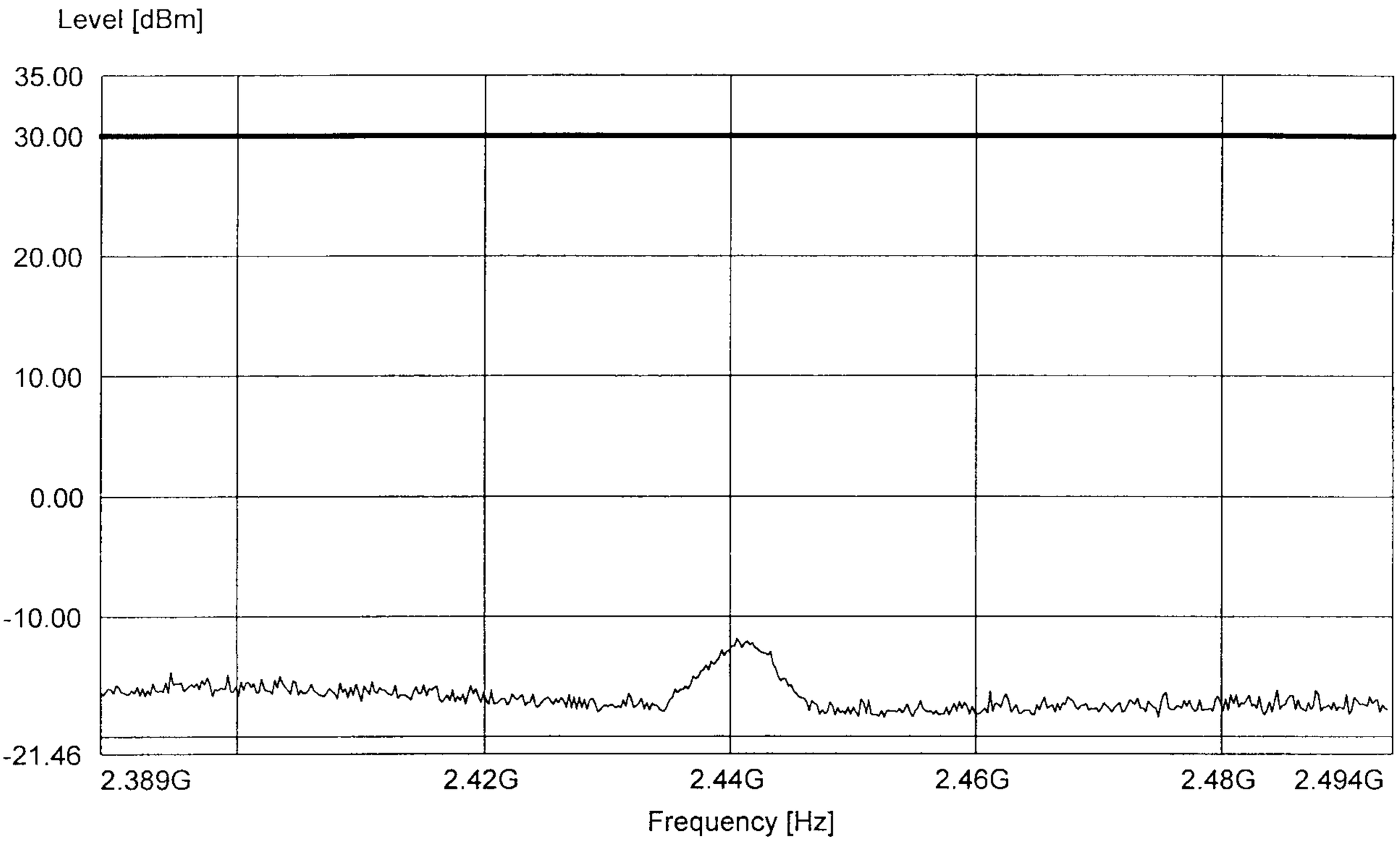
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.442GHz, Pmax: -6.59dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

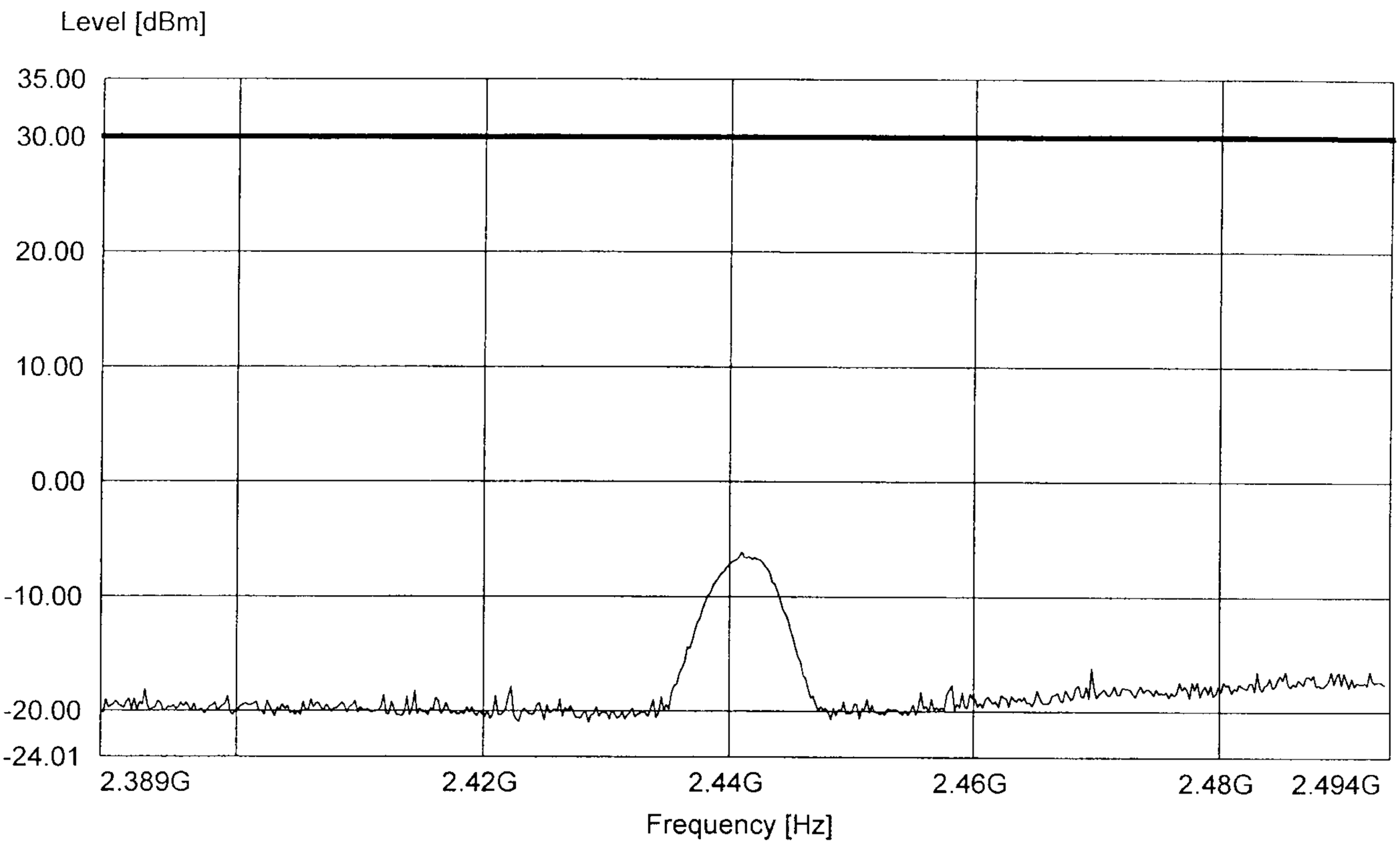
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.441GHz, Pmax: -11.85dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM - FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

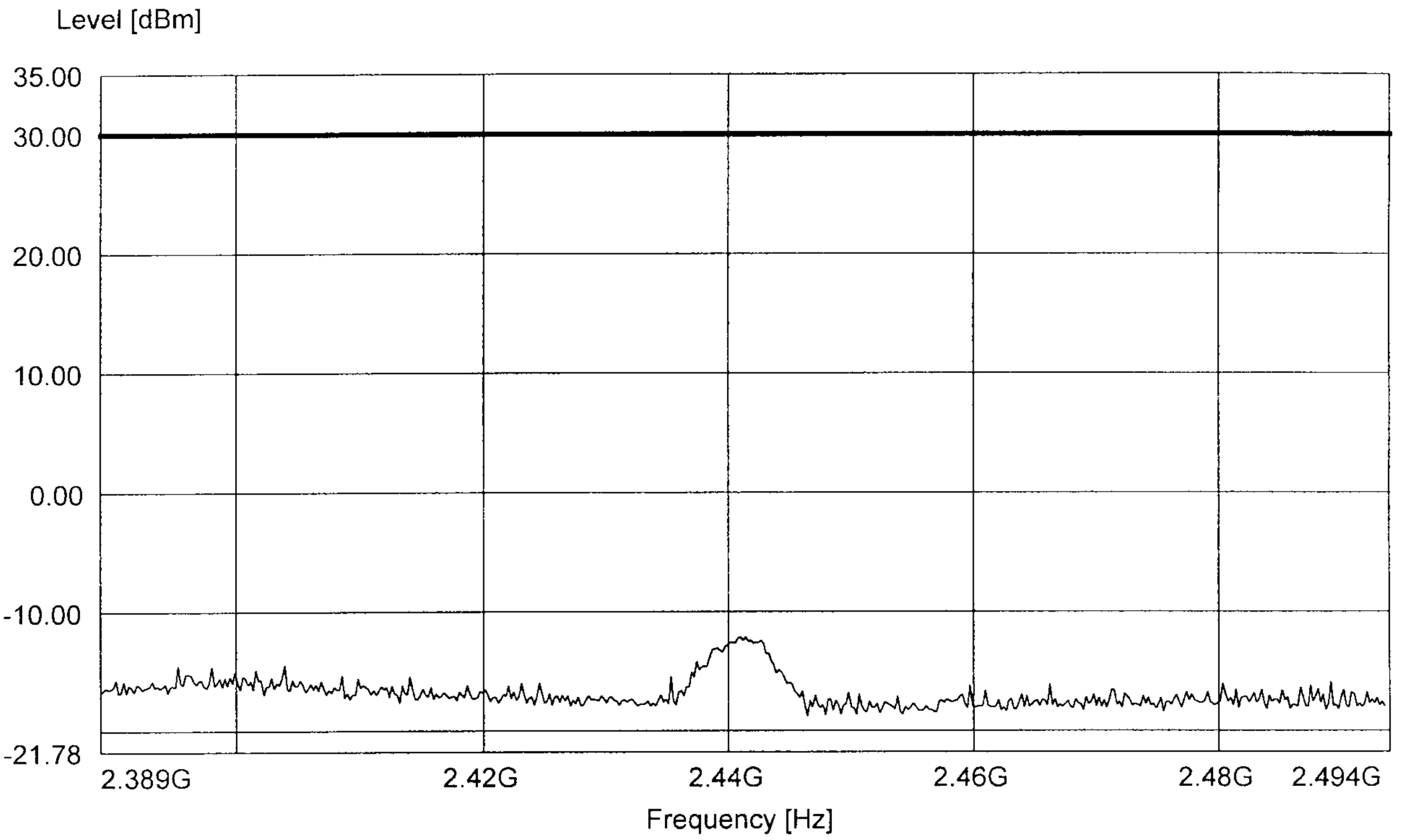
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.441GHz, Pmax: -6.12dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM - FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

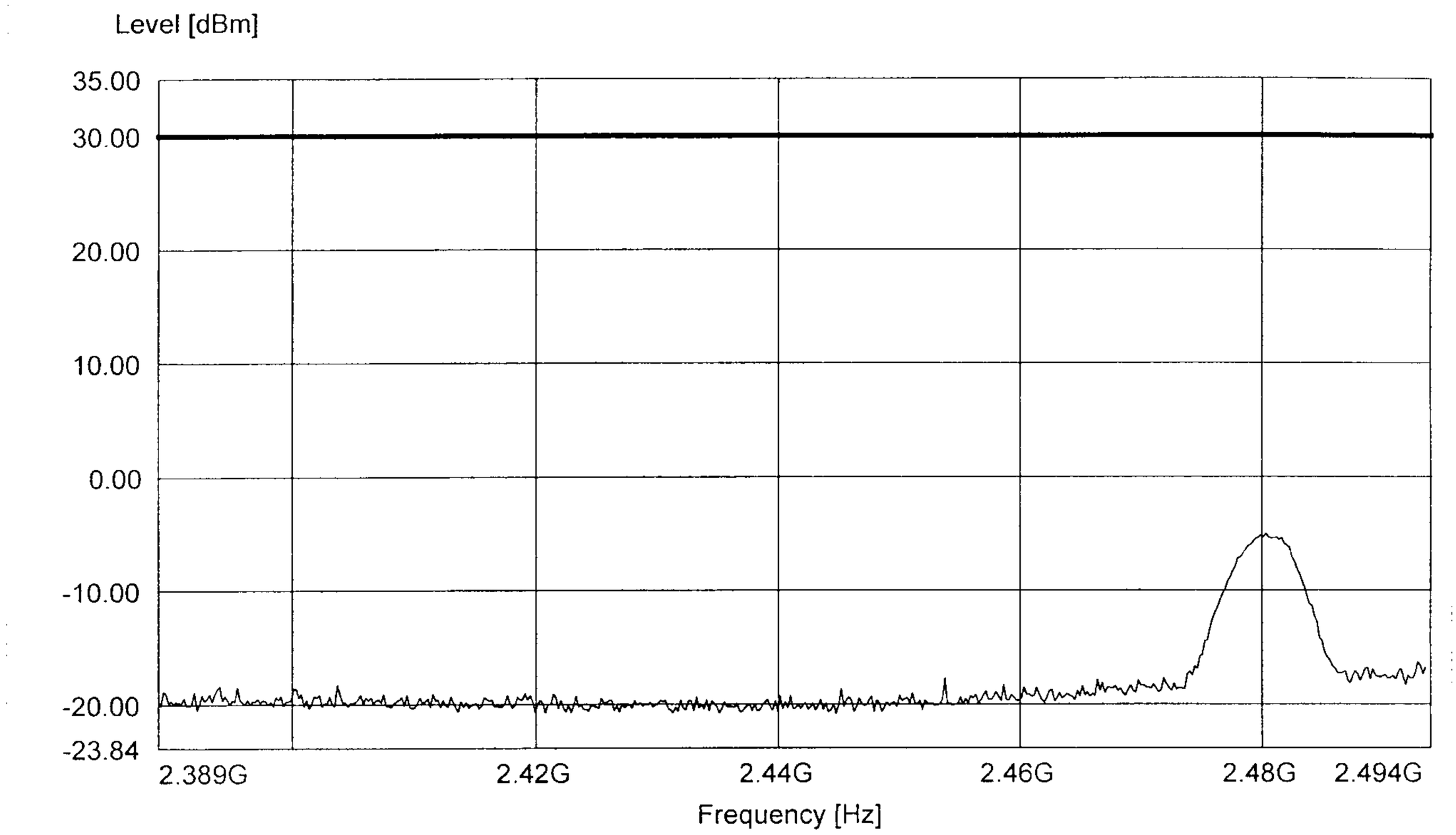
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.441GHz, Pmax: -12.12dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

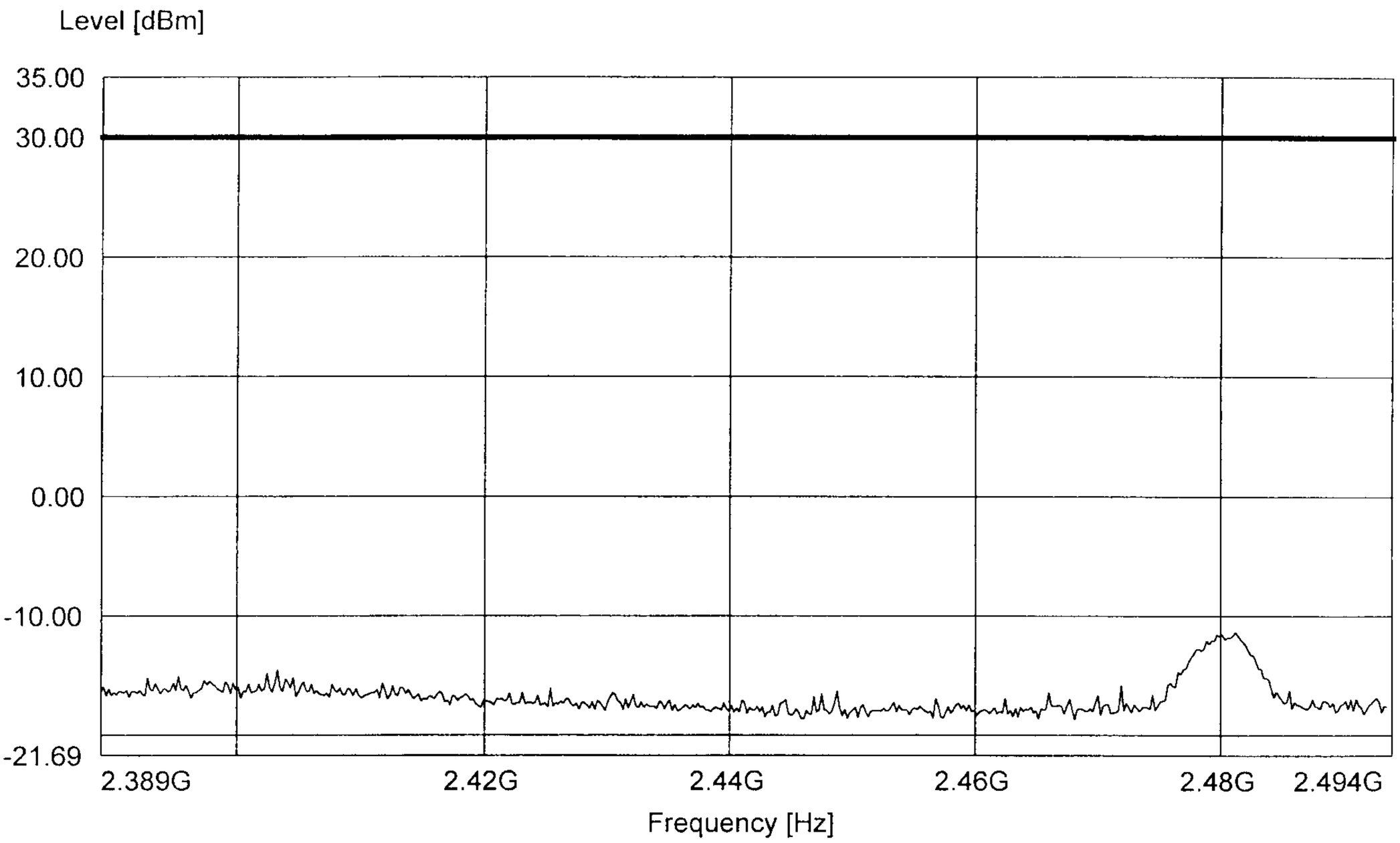
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.480GHz, Pmax: -4.99dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

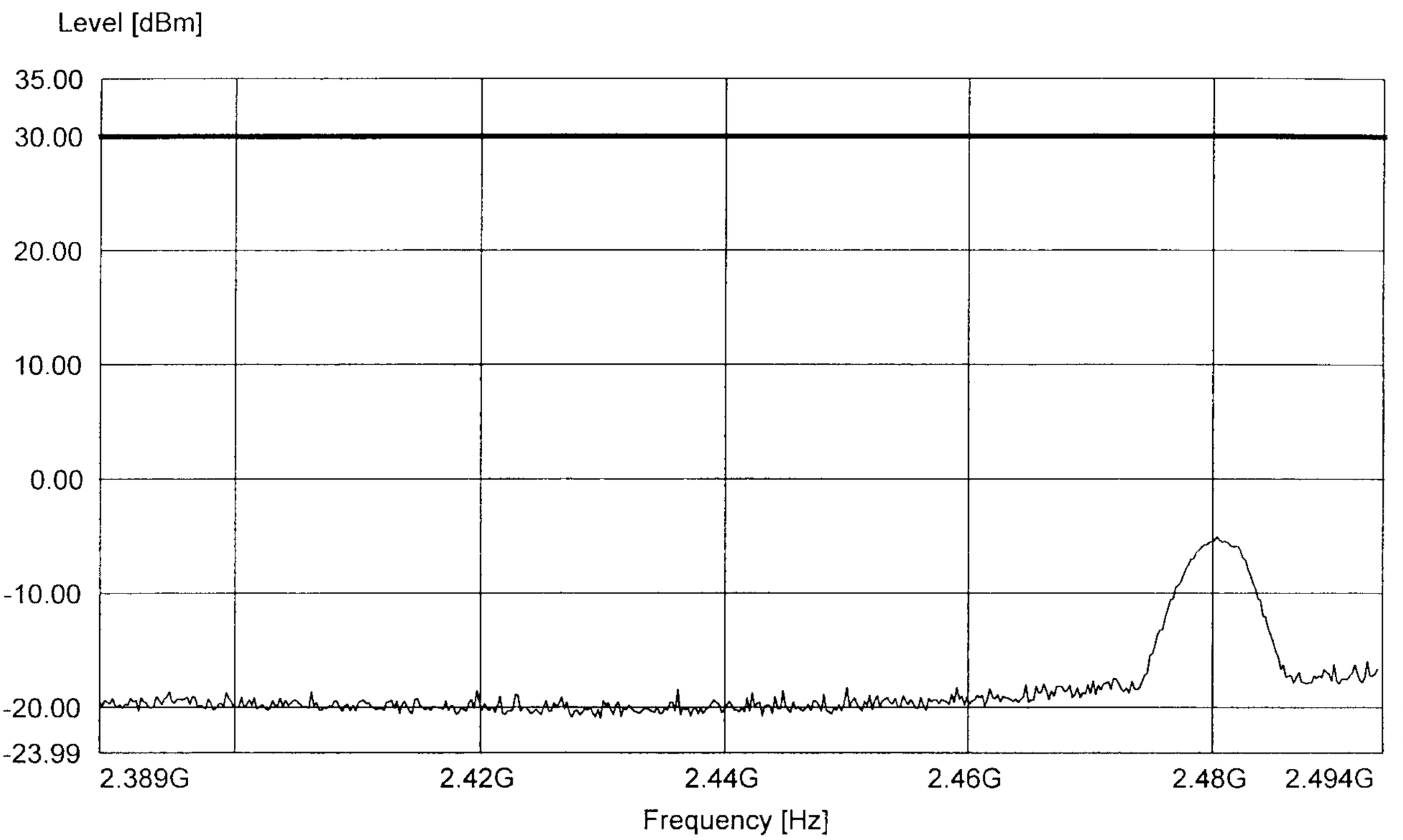
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V -15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.481GHz, Pmax: -11.35dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_h
LIM FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

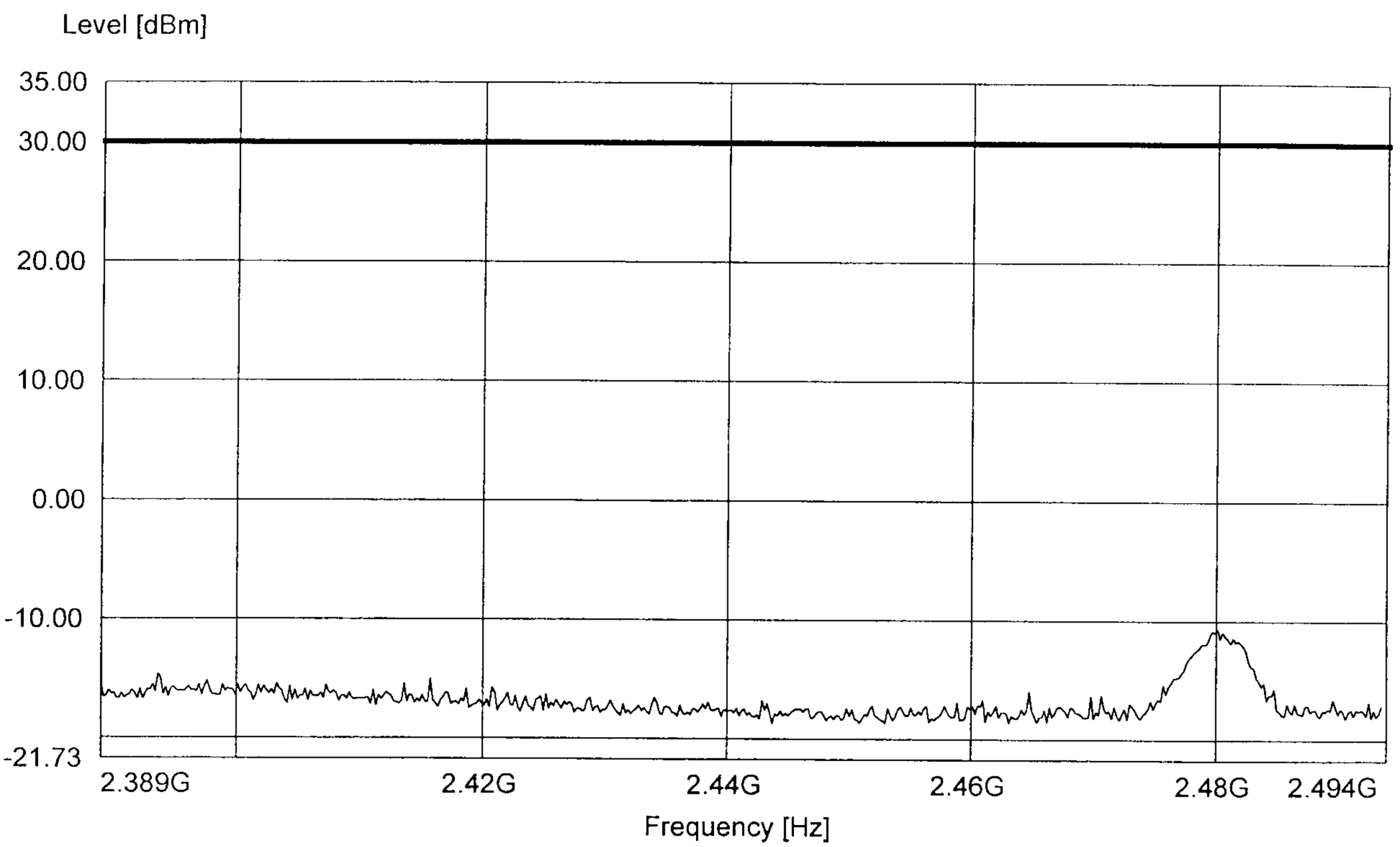
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.480GHz, Pmax: -5.05dBm, RBW: 5MHz



MES 10. FCC_2.4G_dBm_v
LIM - FCC_30dBm

Carrier power (dBm)
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 230 V +15% AC (AC/DC adaptor), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA9120D
Comment 2:	Freq: 2.480GHz, Pmax: -10.64dBm, RBW: 5MHz



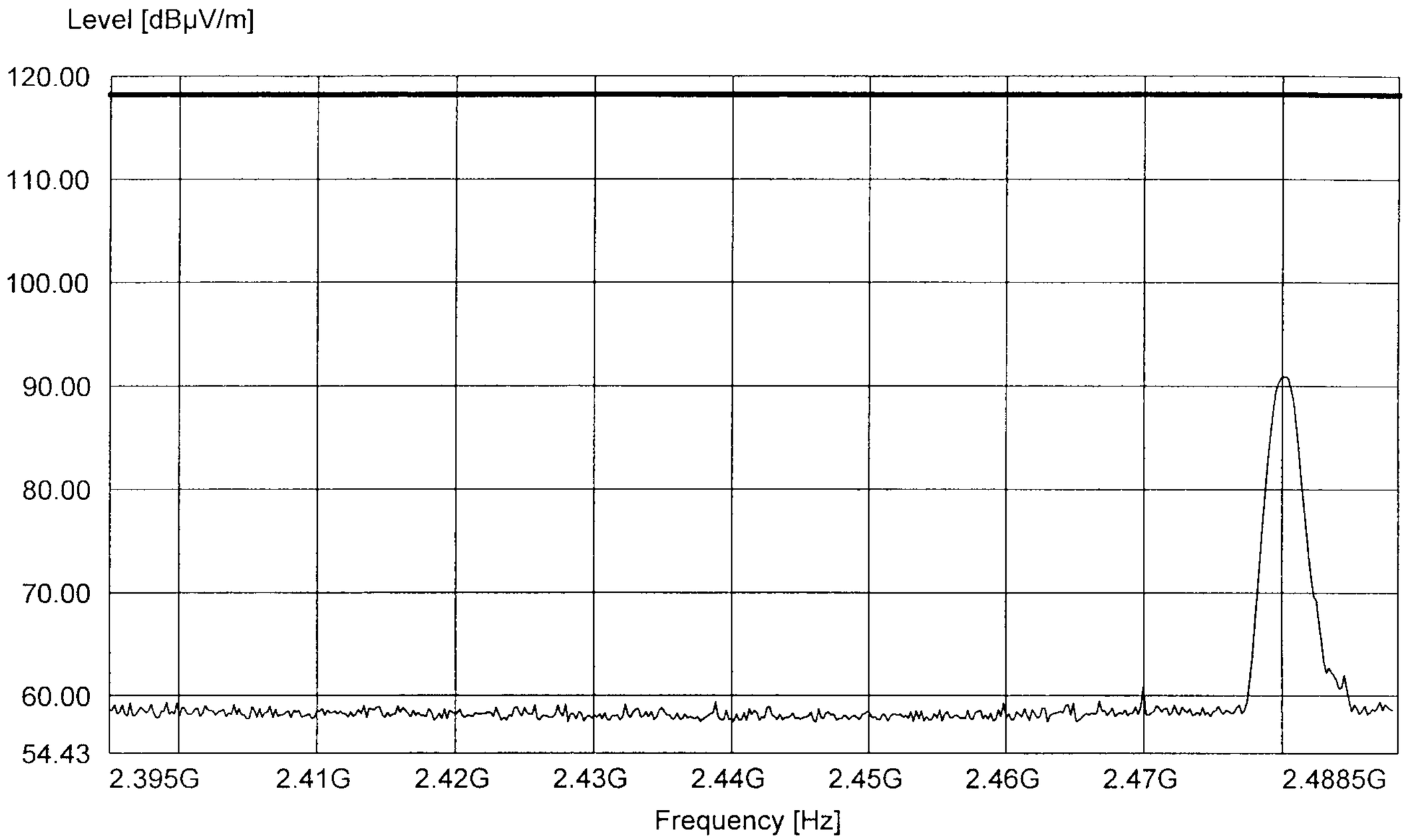
MES 10. FCC_2.4G_dBm_h
LIM - FCC_30dBm

Appendix C

Spurious Emissions radiated - Transmitter operating

Carrier power (Field Strength)
FCC RULES PART 15, SUBPART C

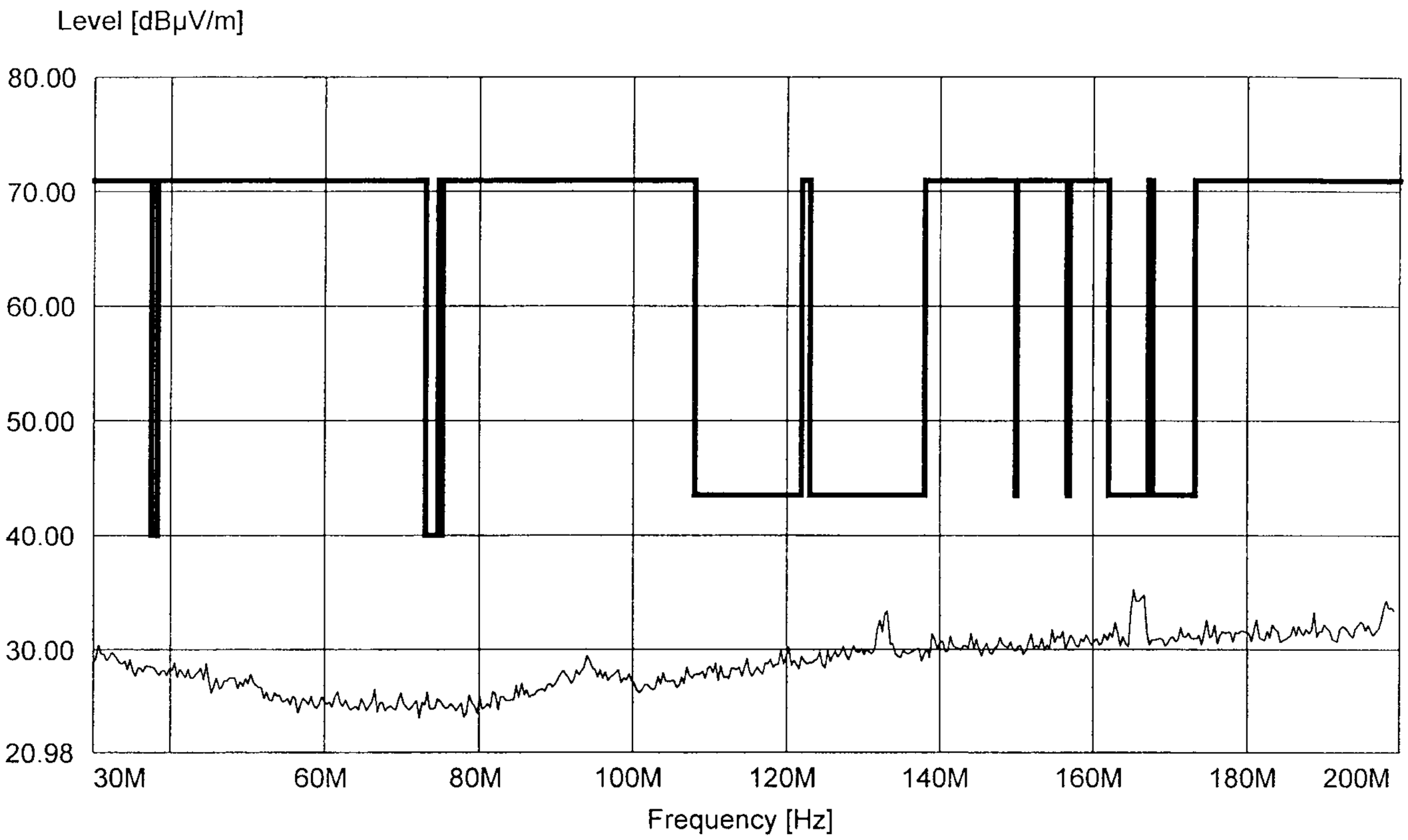
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D
Comment 2:	Freq: 2.480GHz, Emax: 90.96dBµV/m, RBW: 1MHz



MES 8. FCC_part_15_harm
LIM FCC_Tx

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

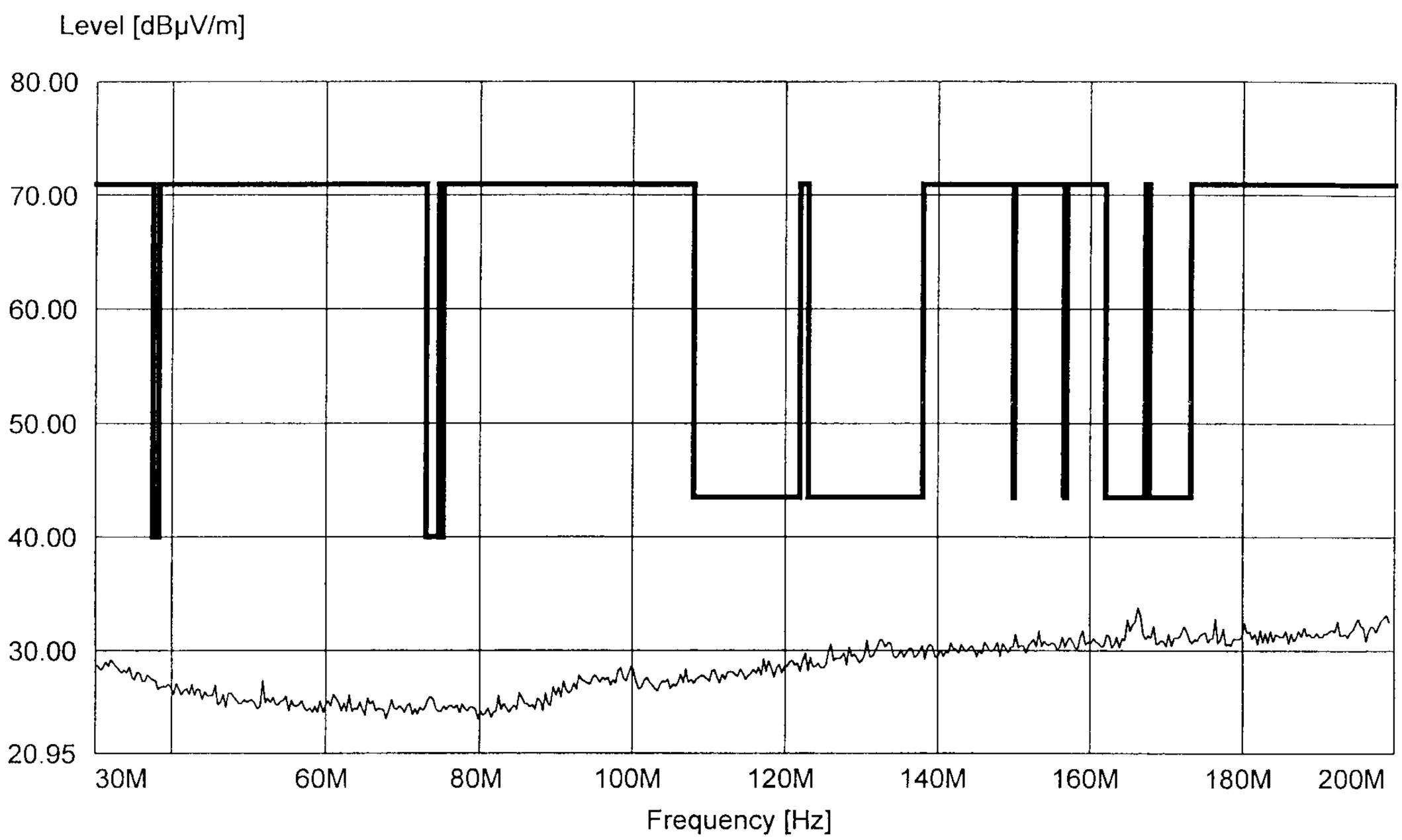
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 165.251MHz, Emax: 35.28dBµV/m, RBW: 100kHz



MES 1. . FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

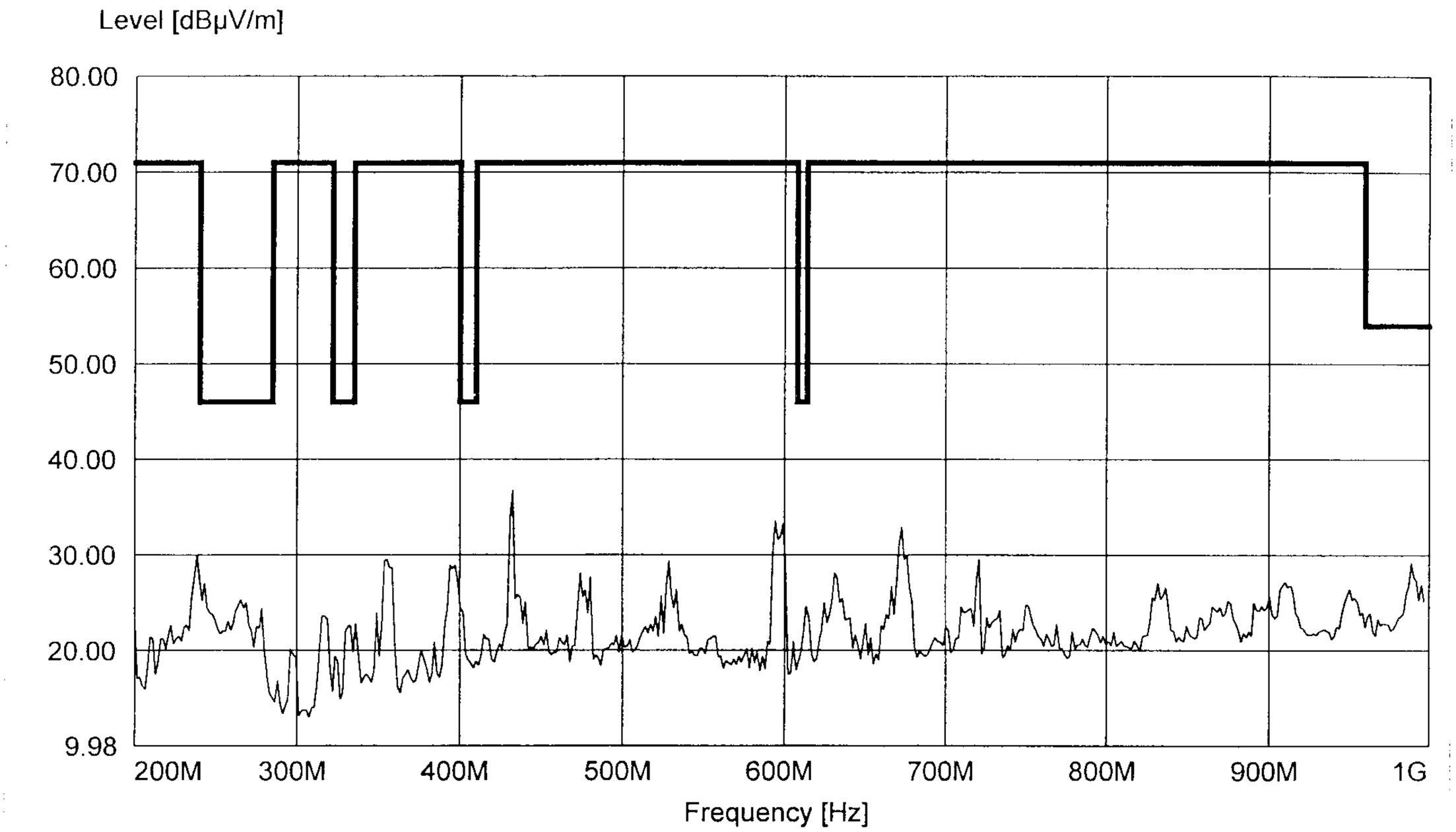
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 166.273MHz, Emax: 33.76dBµV/m, RBW: 100kHz



MES 1[illegible]. FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

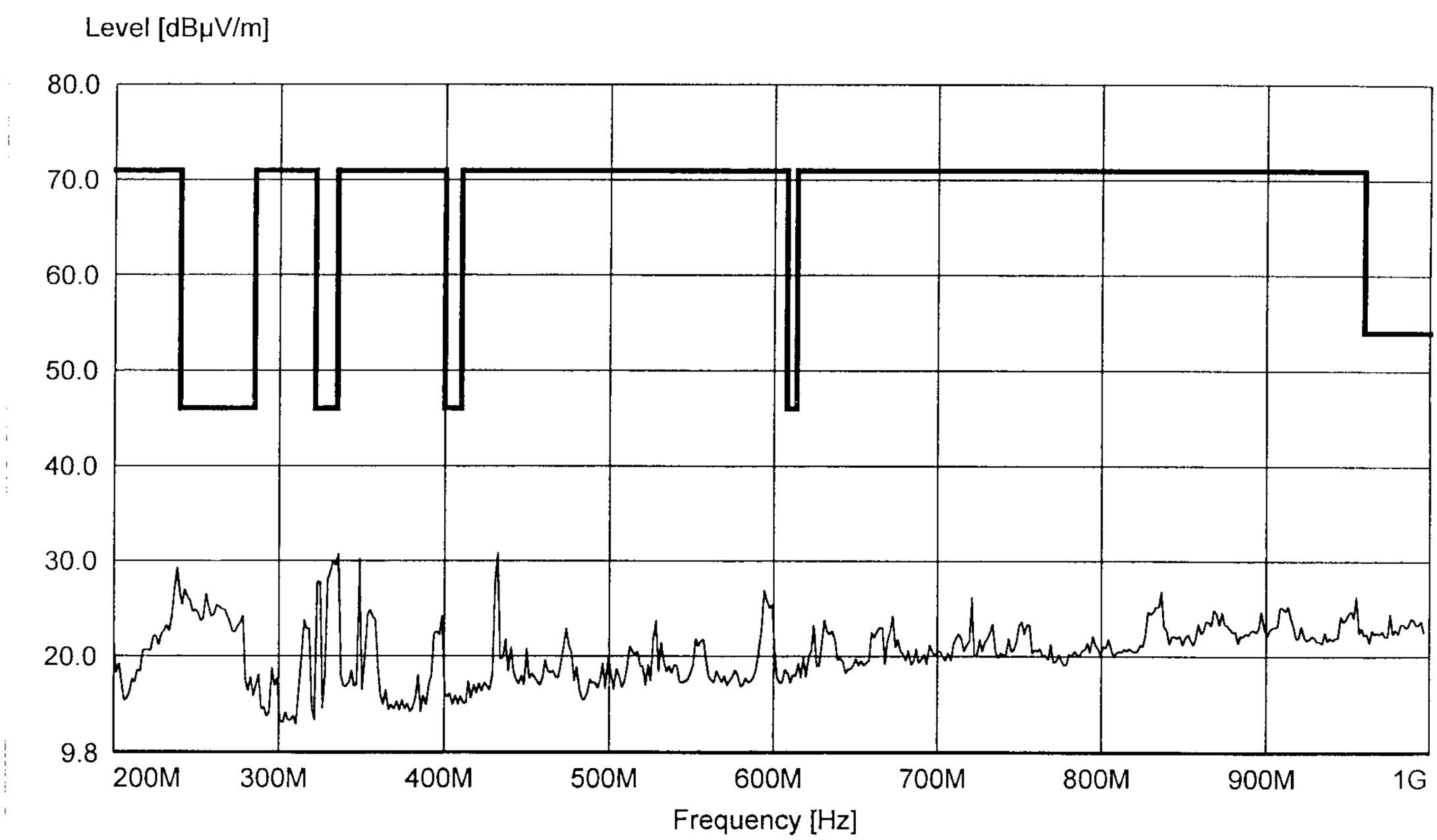
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 432.465MHz, Emax: 36.75dBµV/m, RBW: 100kHz



MES 2[illegible]. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

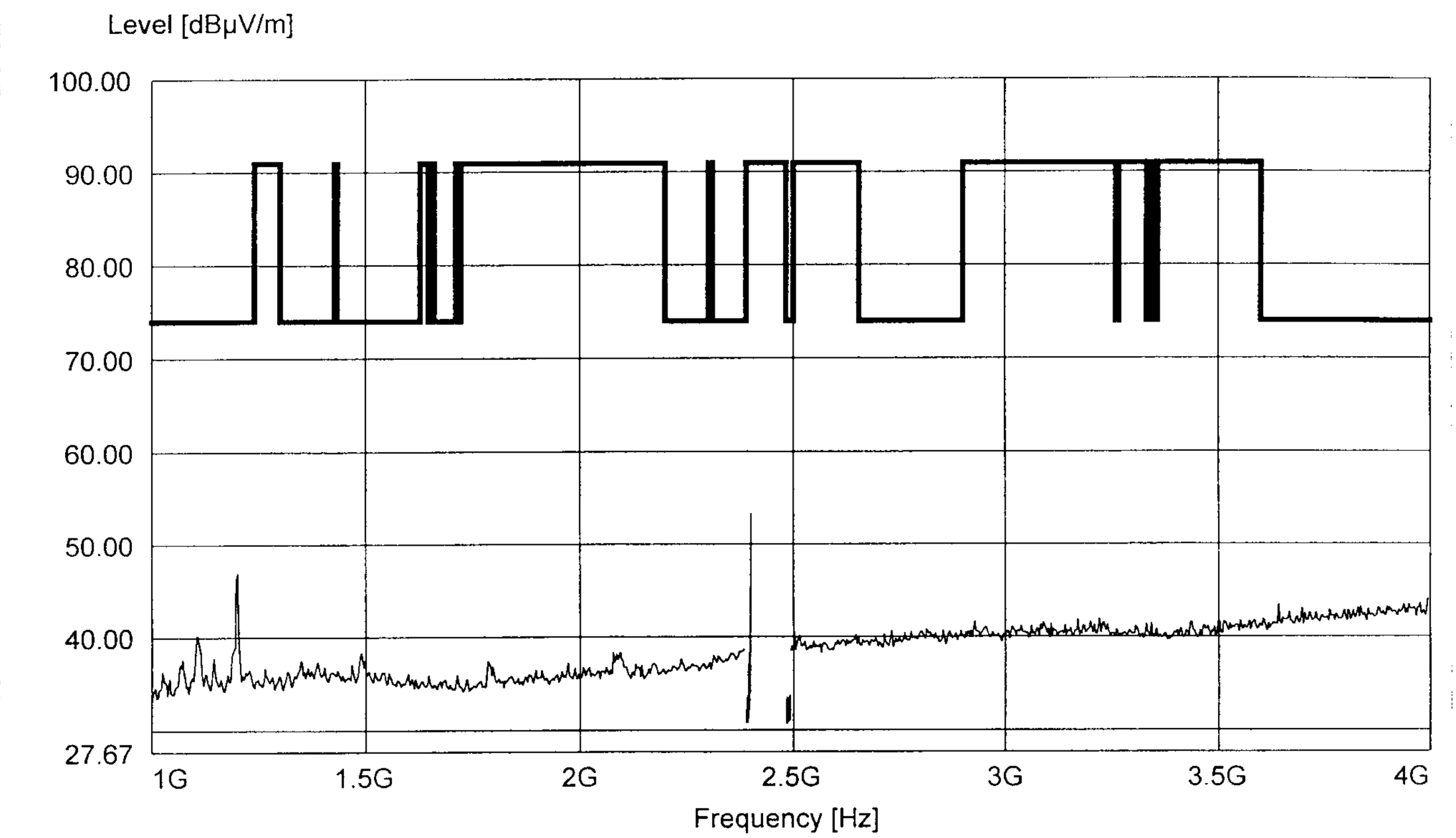
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 432.465MHz, Emax: 30.86dBµV/m, RBW: 100kHz



MES 2. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

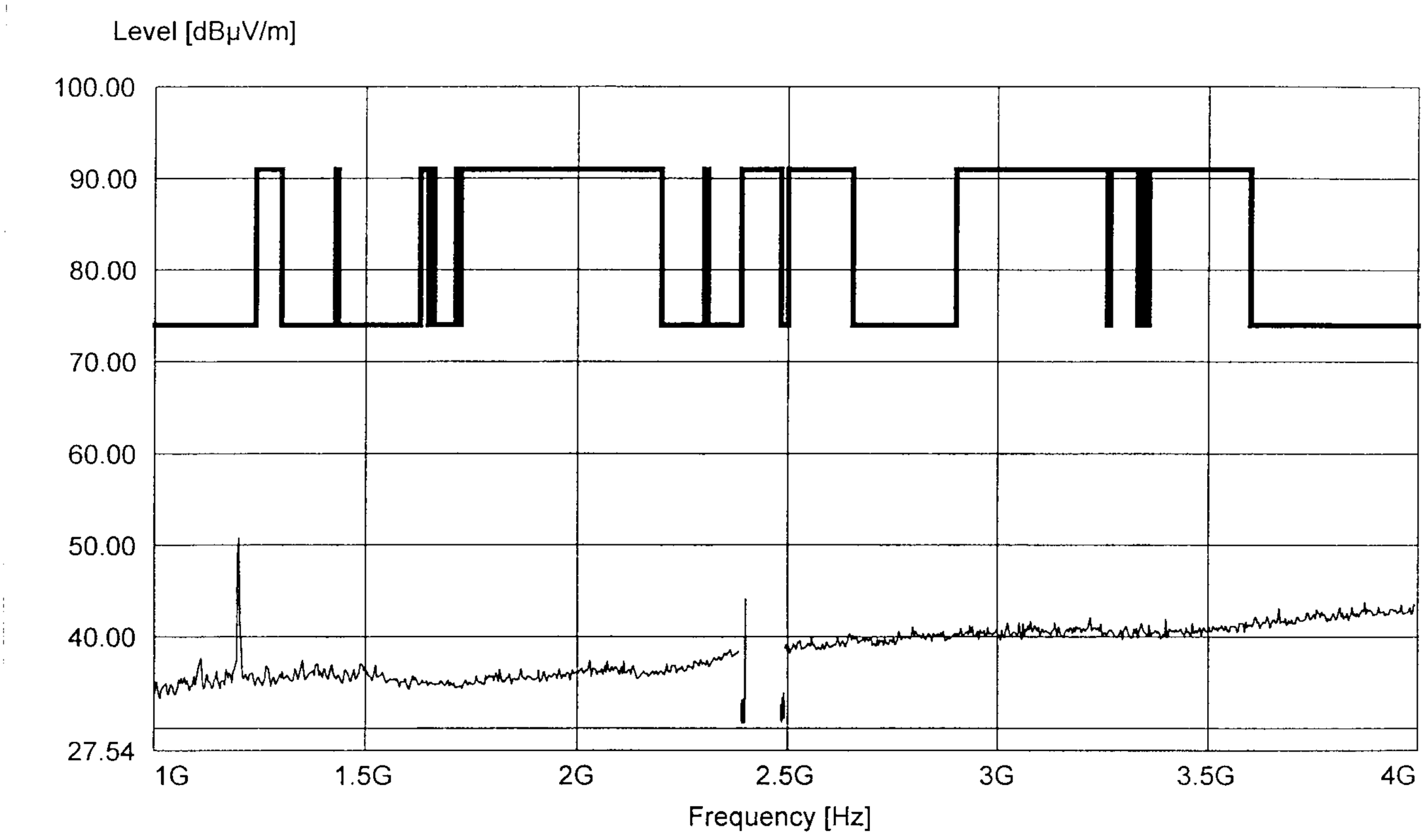
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 2.400GHz, Emax: 53.34dBµV/m, RBW: 1MHz



MES 3 . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

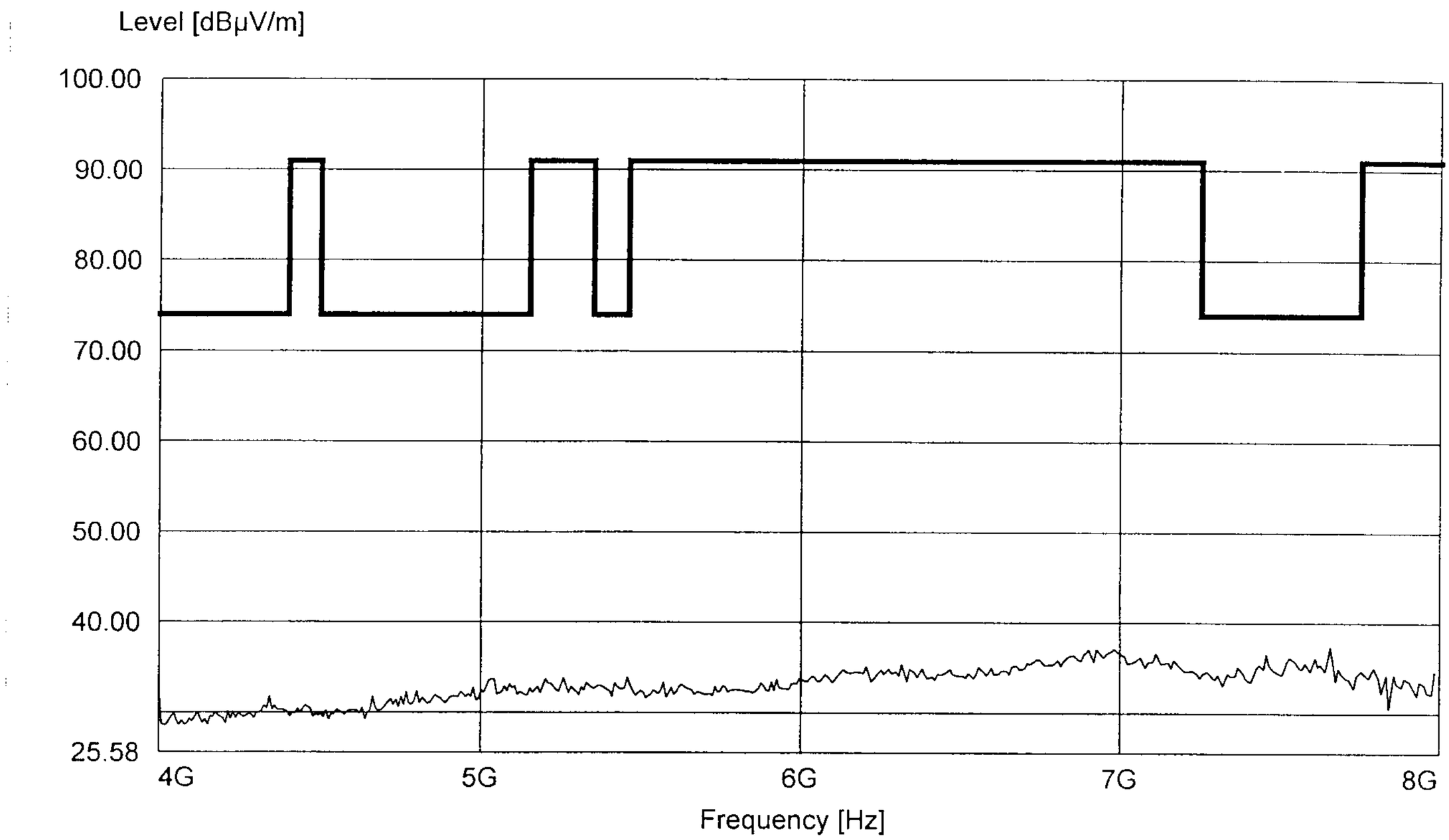
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 1.201GHz, Emax: 50.78dBµV/m, RBW: 1MHz



MES 3[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 7.655GHz, Emax: 37.37dBµV/m, RBW: 1MHz



MES 4[illegible]. FCC_part_15
LIM - FCC_restricted

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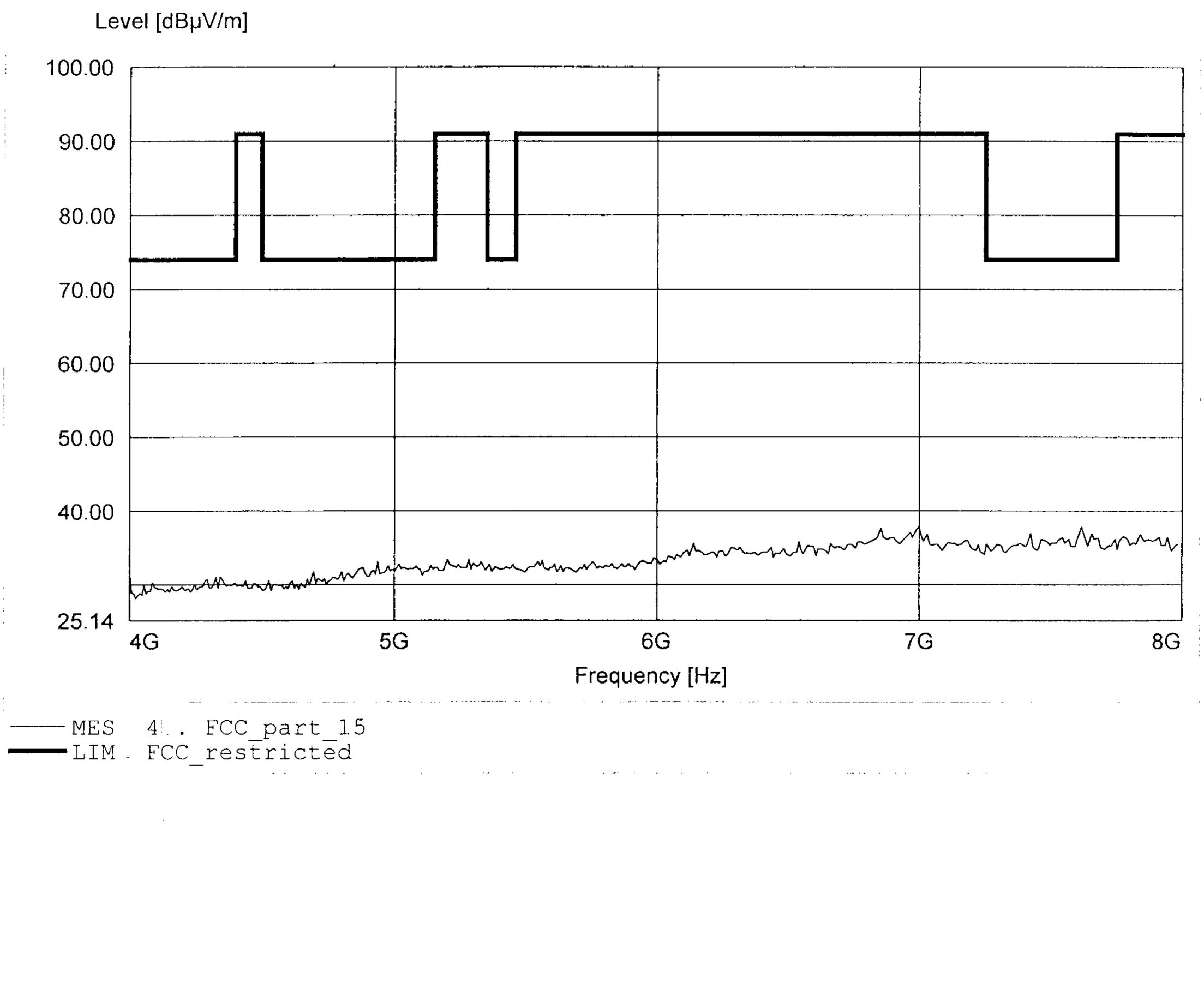
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

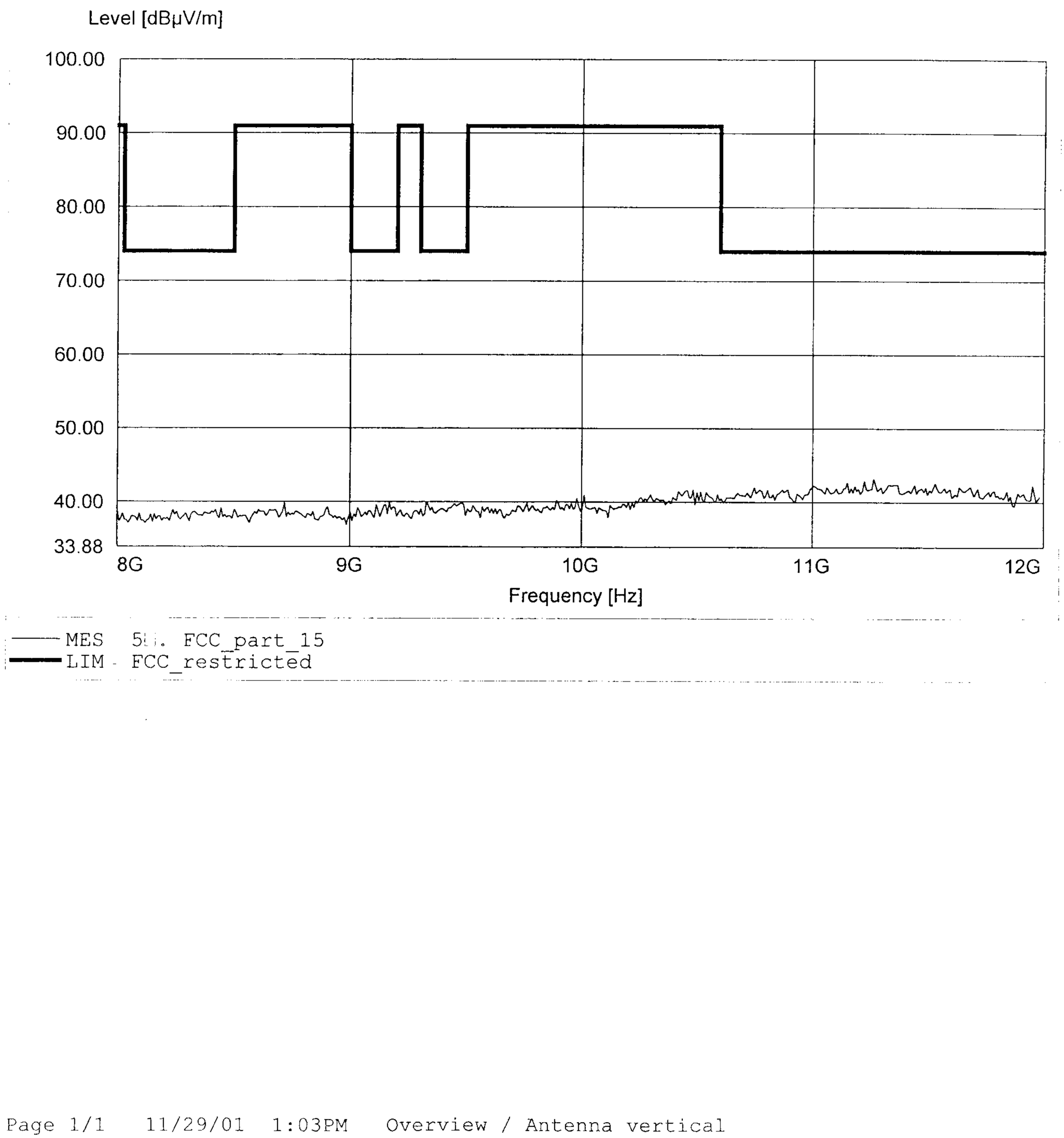
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 7.615GHz, Emax: 37.88dBµV/m, RBW: 1MHz



MES 4[illegible]. FCC_part_15
LIM . FCC_restricted

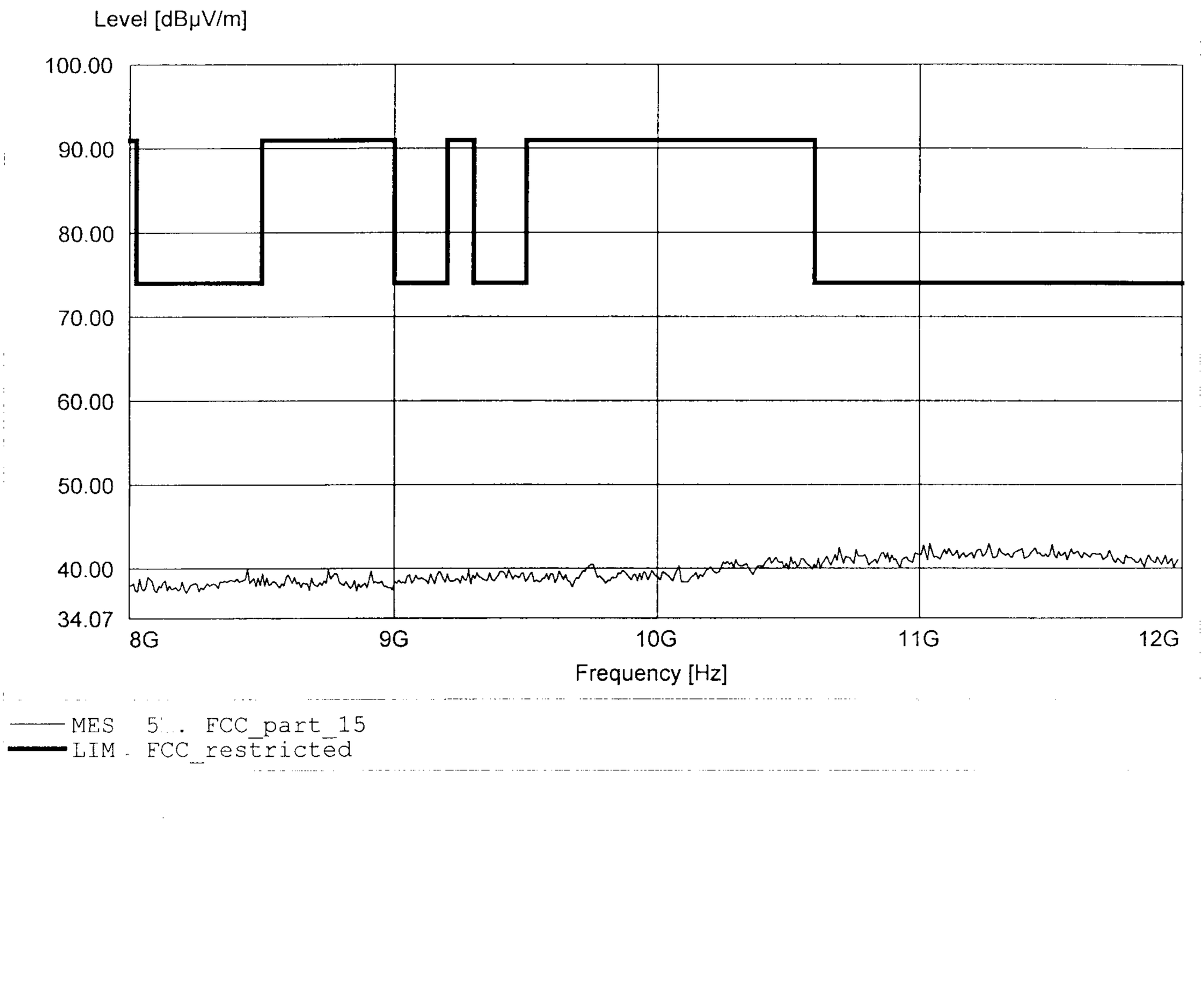
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.263GHz, Emax: 43.21dBµV/m, RBW: 1MHz



Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

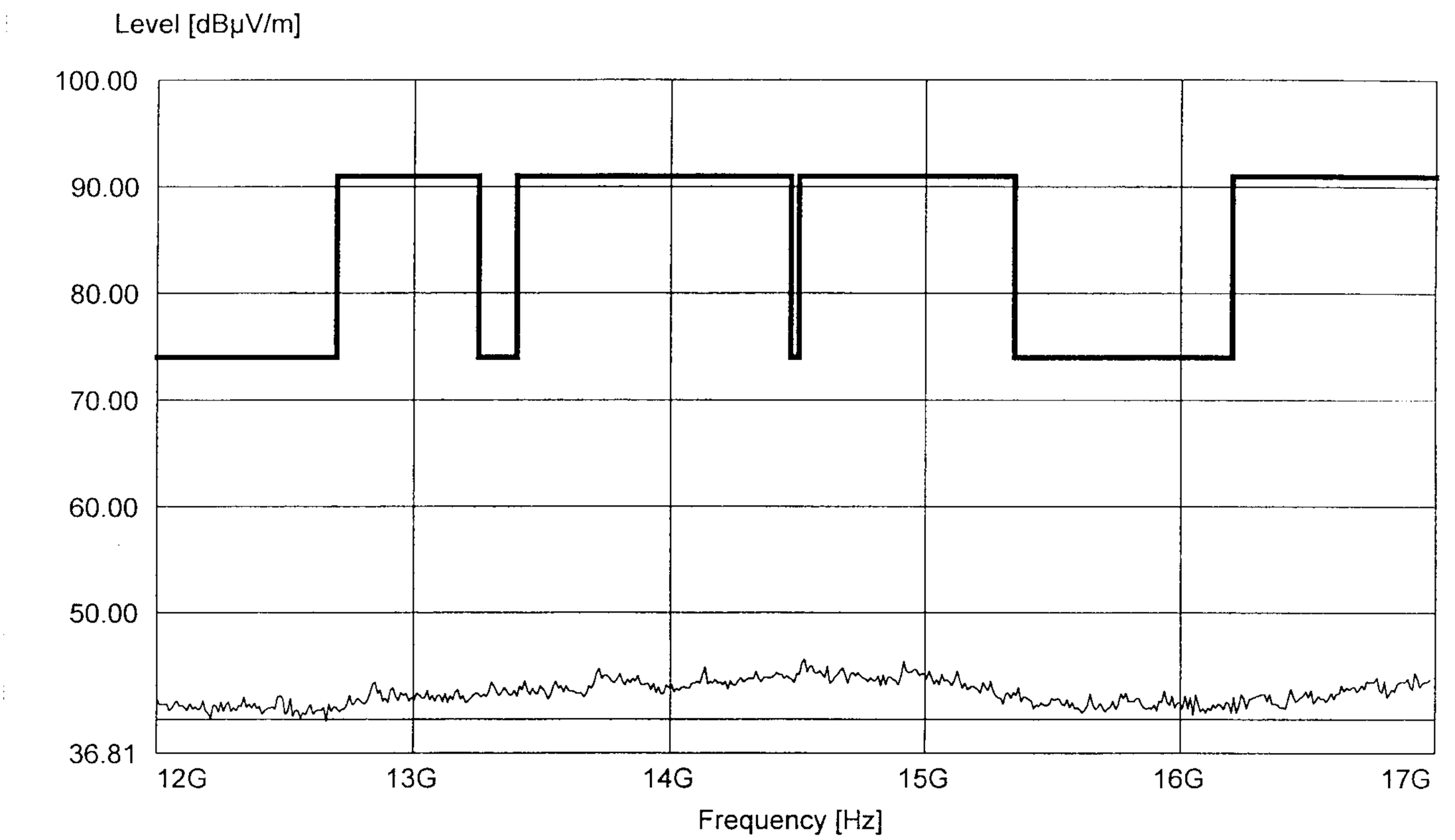
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.038GHz, Emax: 43.00dBµV/m, RBW: 1MHz



MES 5[illegible]. FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

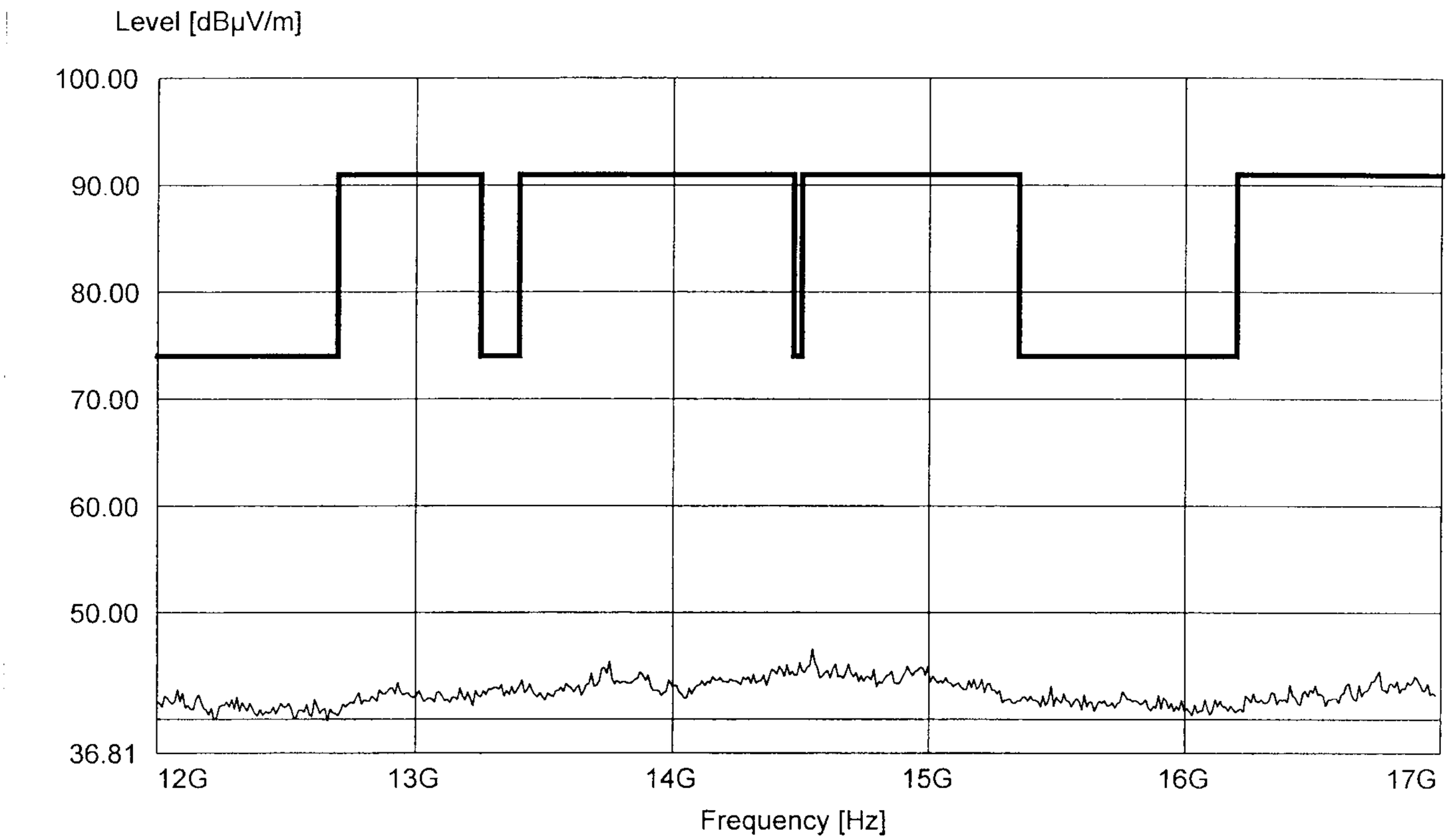
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.525GHz, Emax: 45.61dBµV/m, RBW: 1MHz



MES 6[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

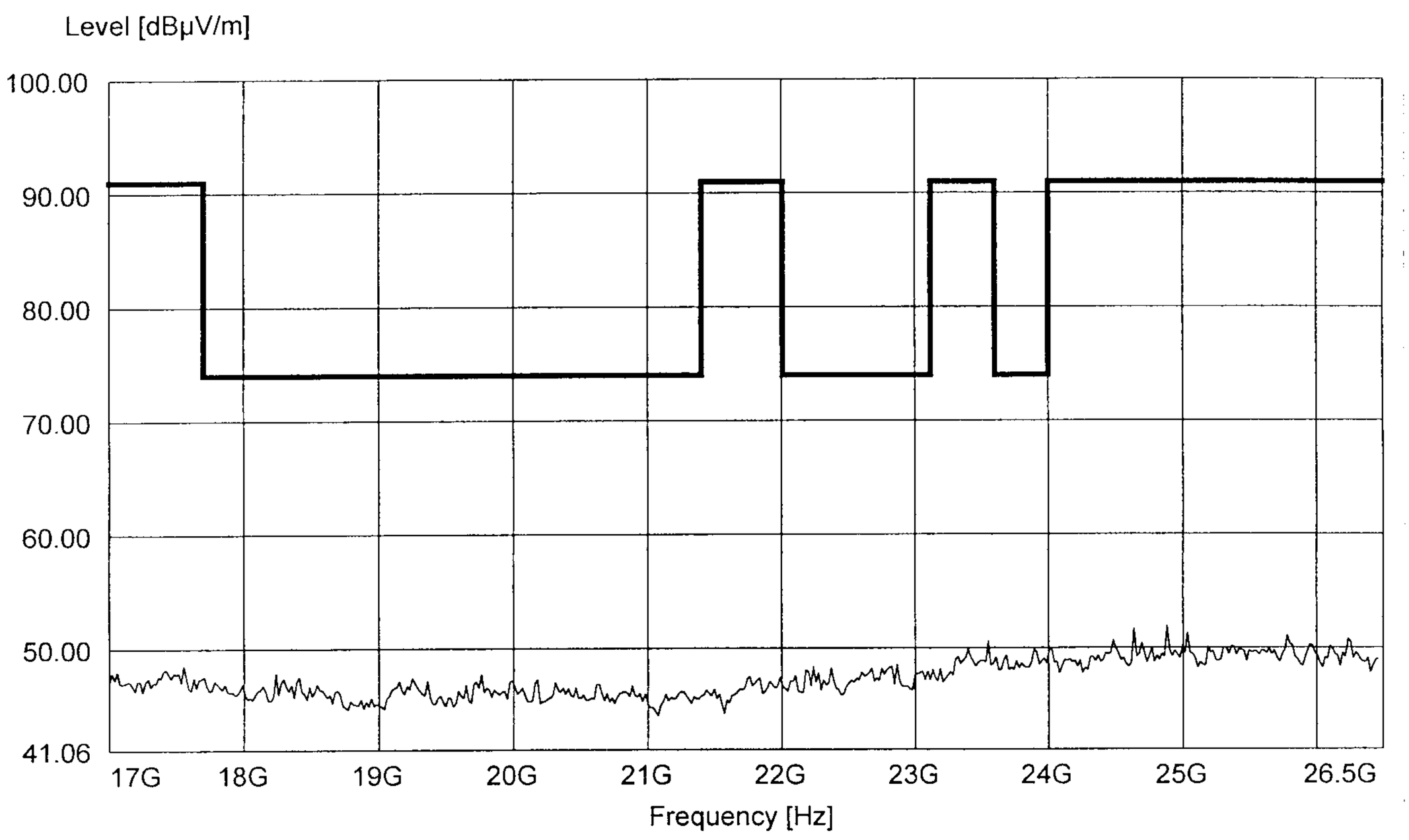
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.545GHz, Emax: 46.57dBµV/m, RBW: 1MHz



MES 6 . FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

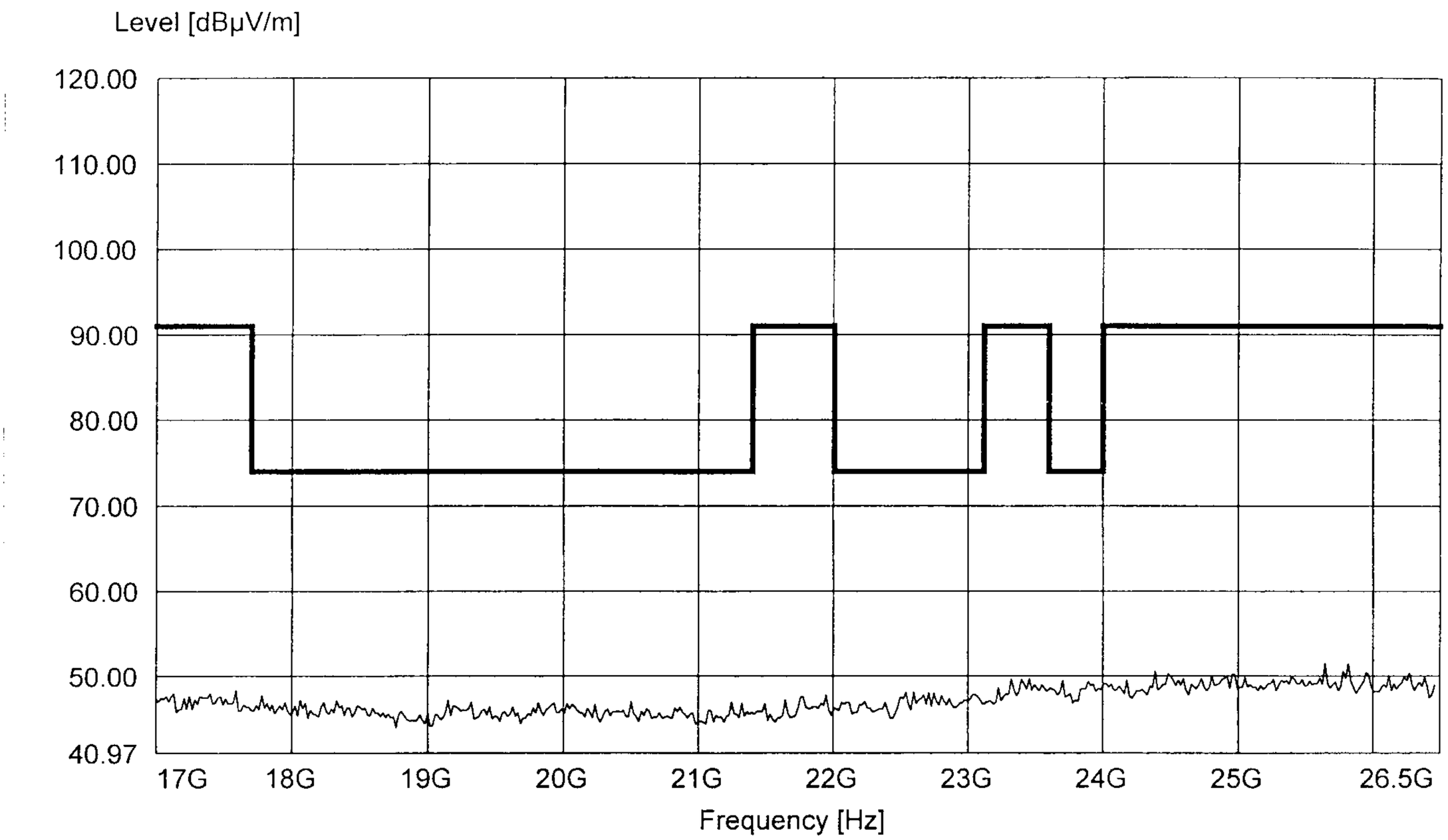
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 24.882GHz, Emax: 51.89dBµV/m, RBW: 1MHz



MES 7. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

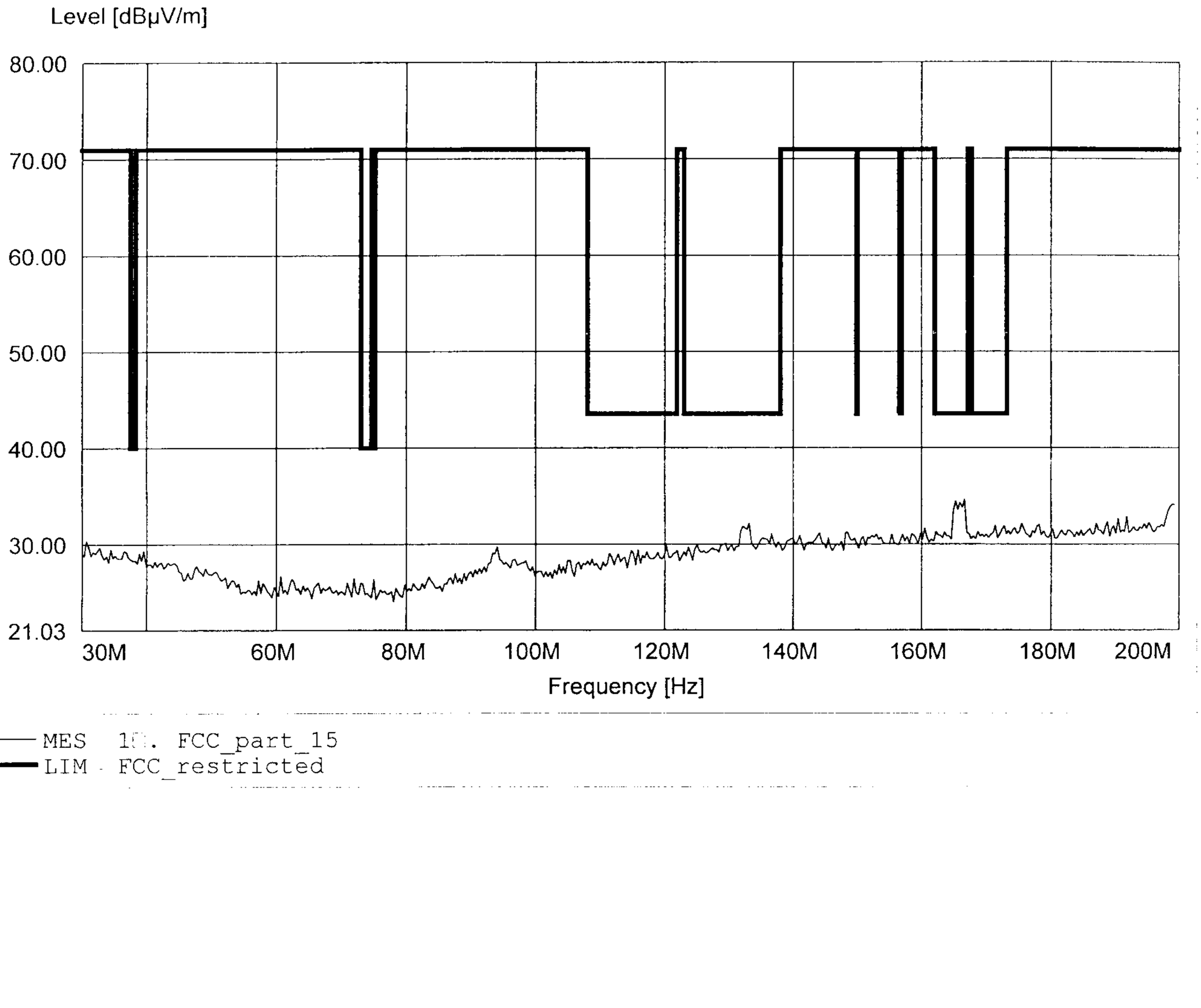
EUT:	Bluetooth CompactFlash Card / TX: 2402 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 25.643GHz, Emax: 51.54dBµV/m, RBW: 1MHz



MES 7[illegible]. FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

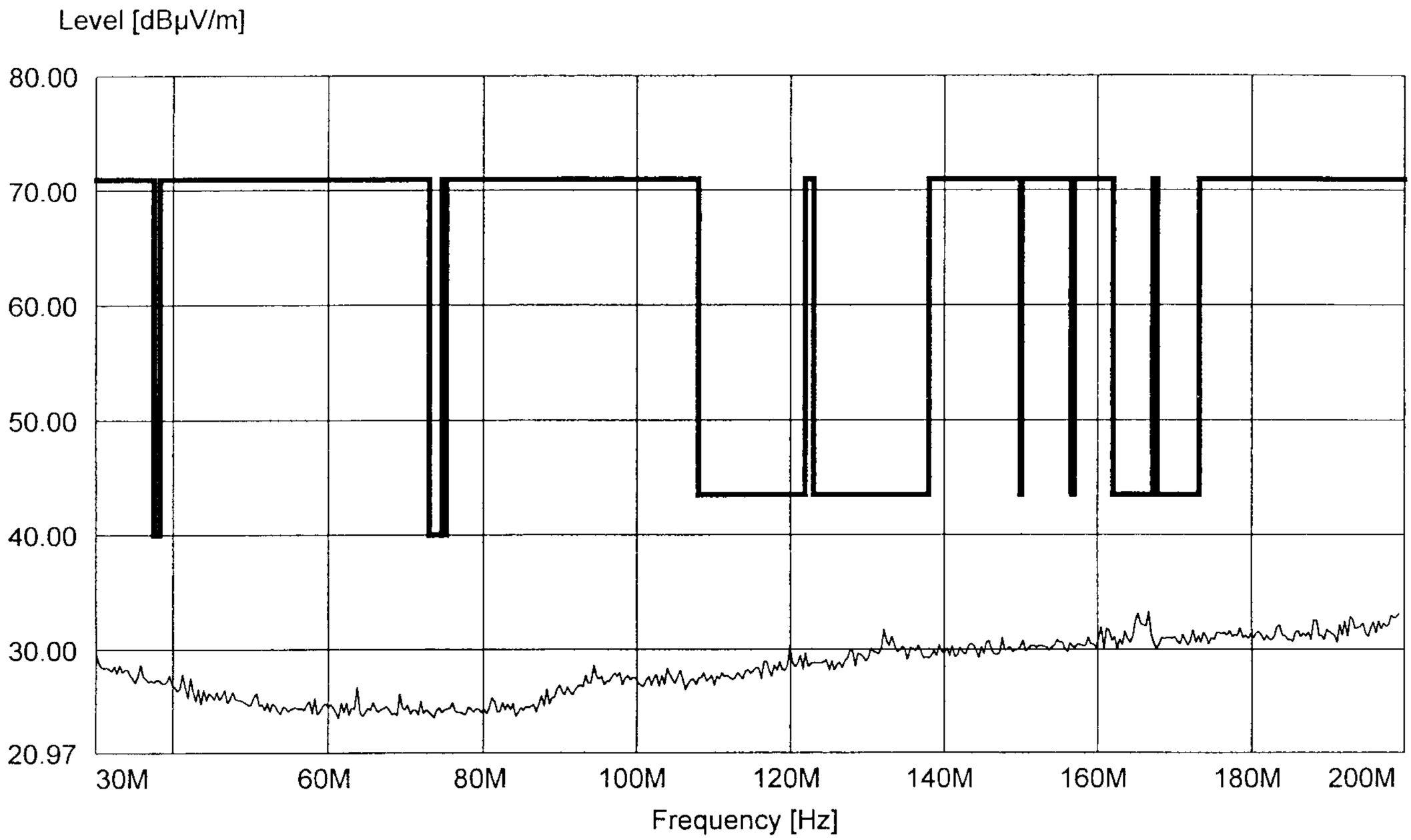
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 166.613MHz, Emax: 34.63dBµV/m, RBW: 100kHz



MES 1[illegible]. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

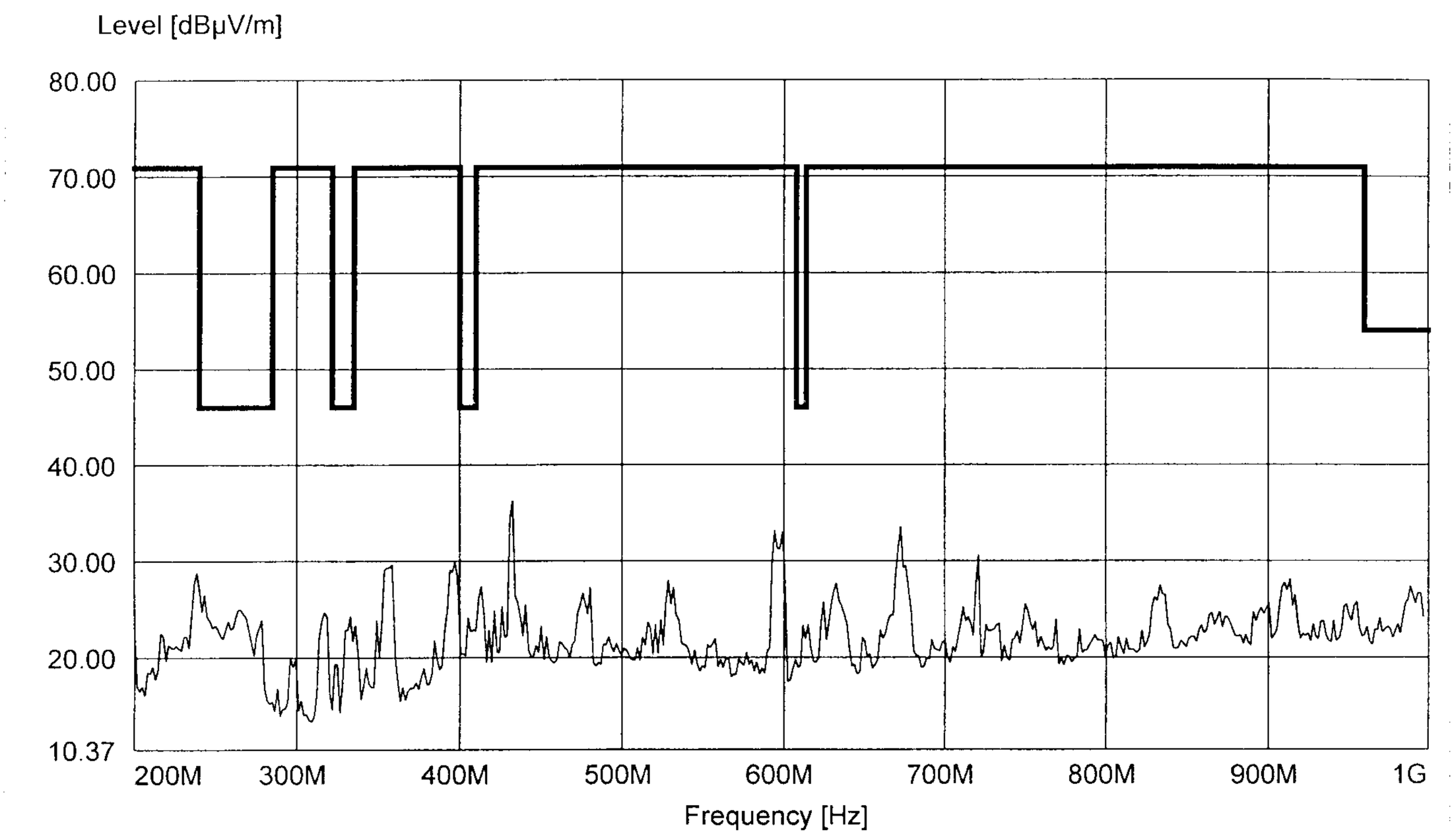
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 166.613MHz, Emax: 33.25dBµV/m, RBW: 100kHz



MES 1.. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

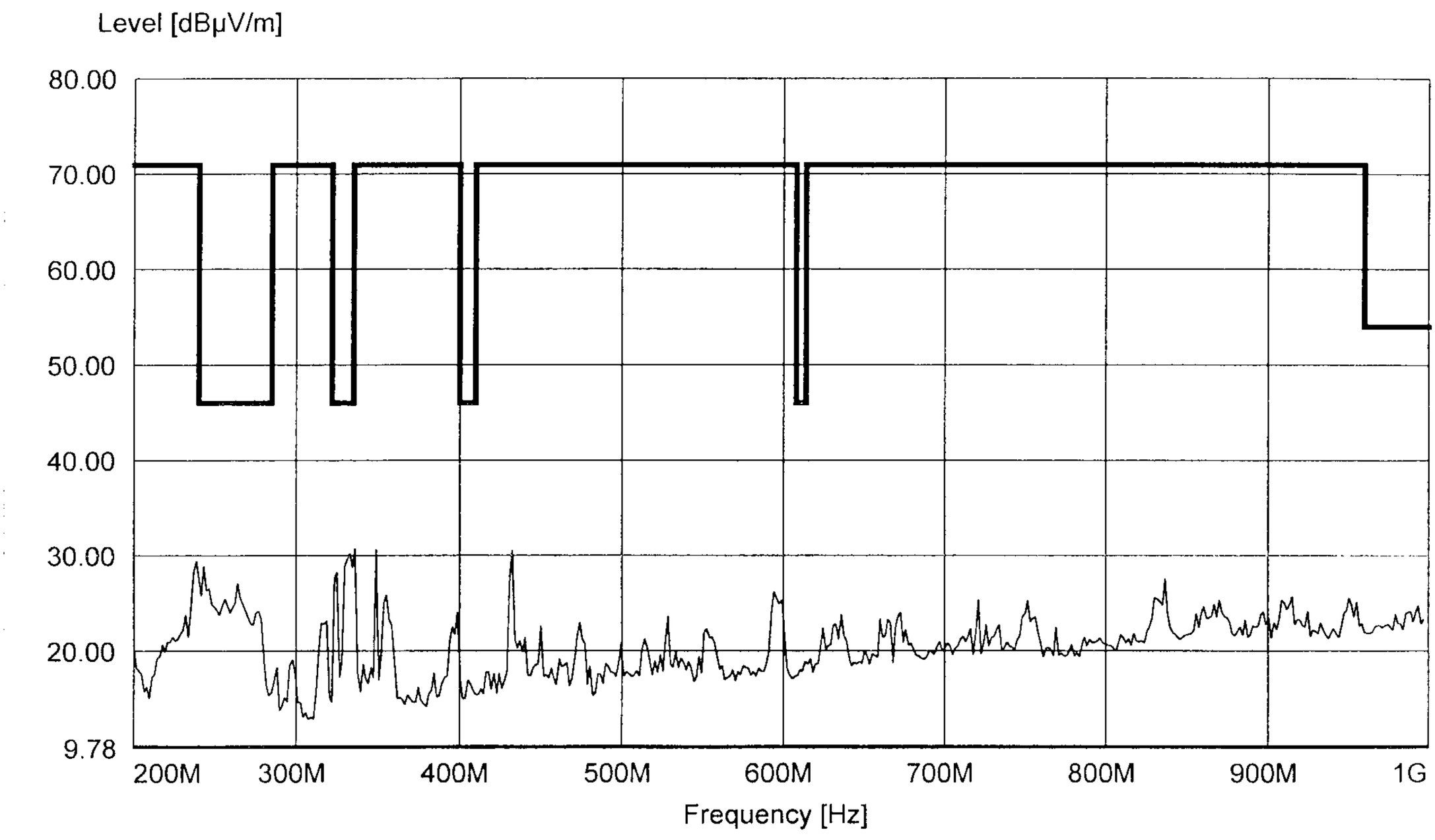
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 432.465MHz, Emax: 36.27dBµV/m, RBW: 100kHz



MES 2[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

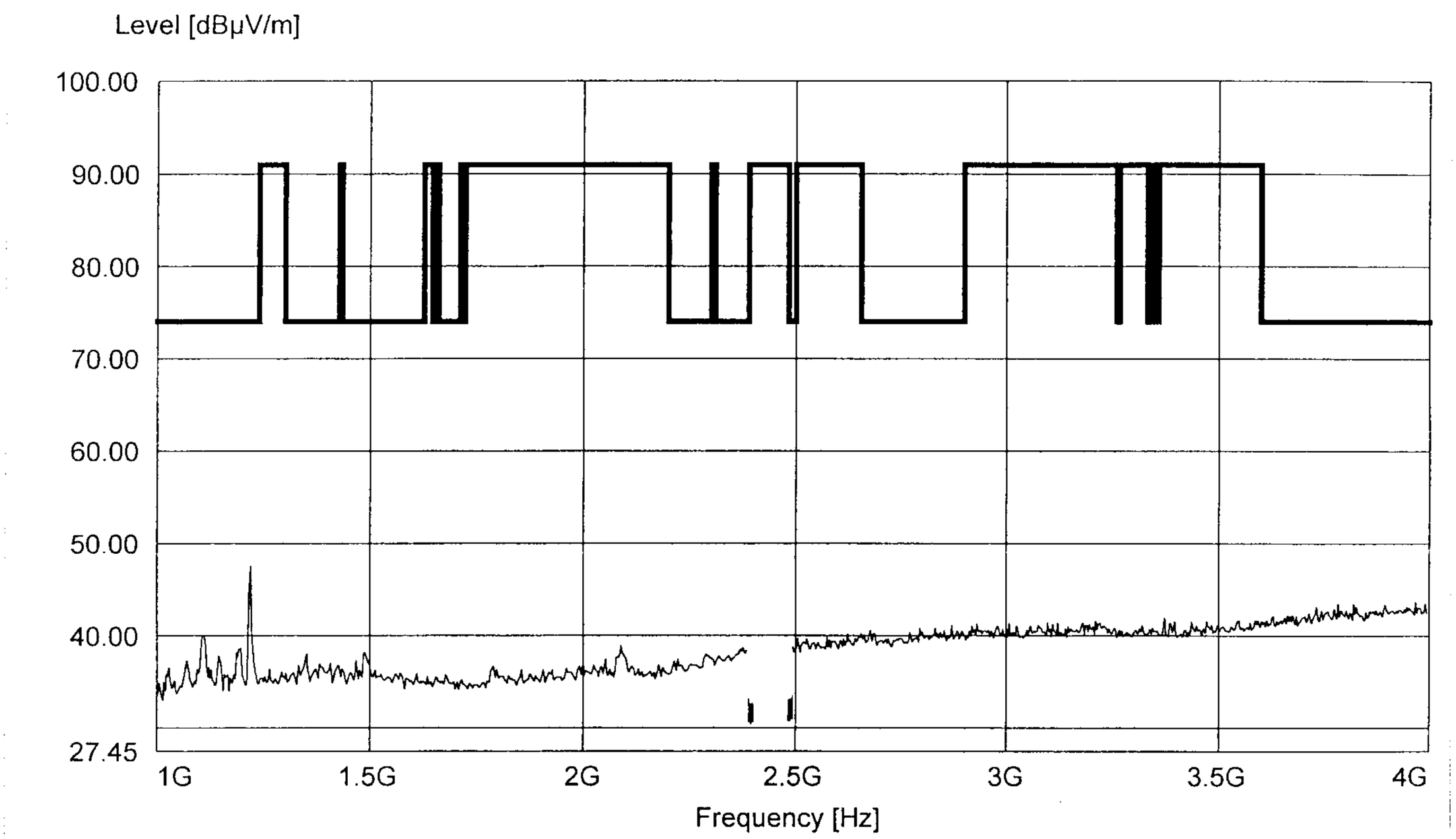
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 336.273MHz, Emax: 30.74dBµV/m, RBW: 100kHz



MES 2 . FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

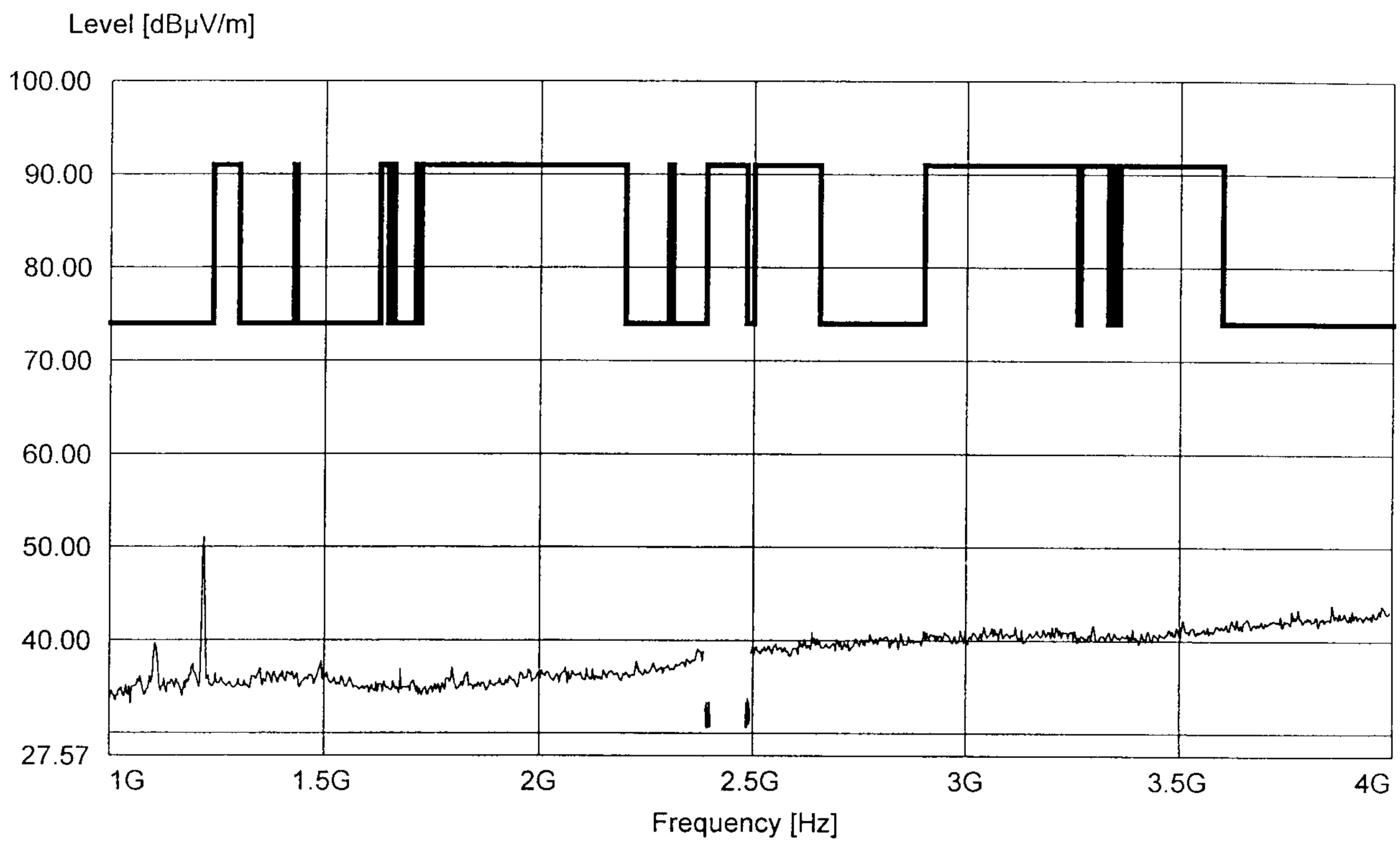
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 1.220GHz, Emax: 47.61dBµV/m, RBW: 1MHz



MES 3[illegible]. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

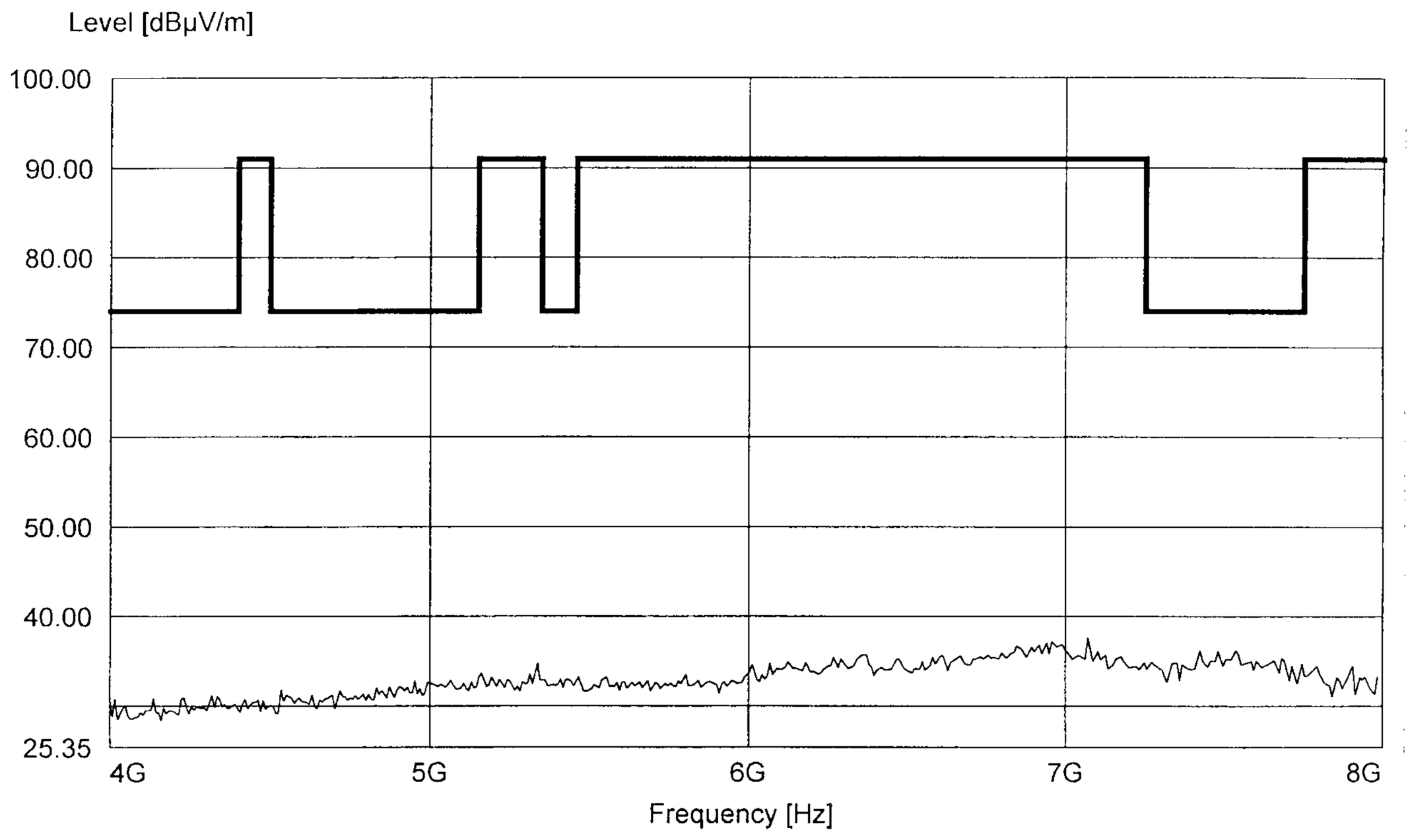
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 1.220GHz, Emax: 51.09dBµV/m, RBW: 1MHz



MES 3[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

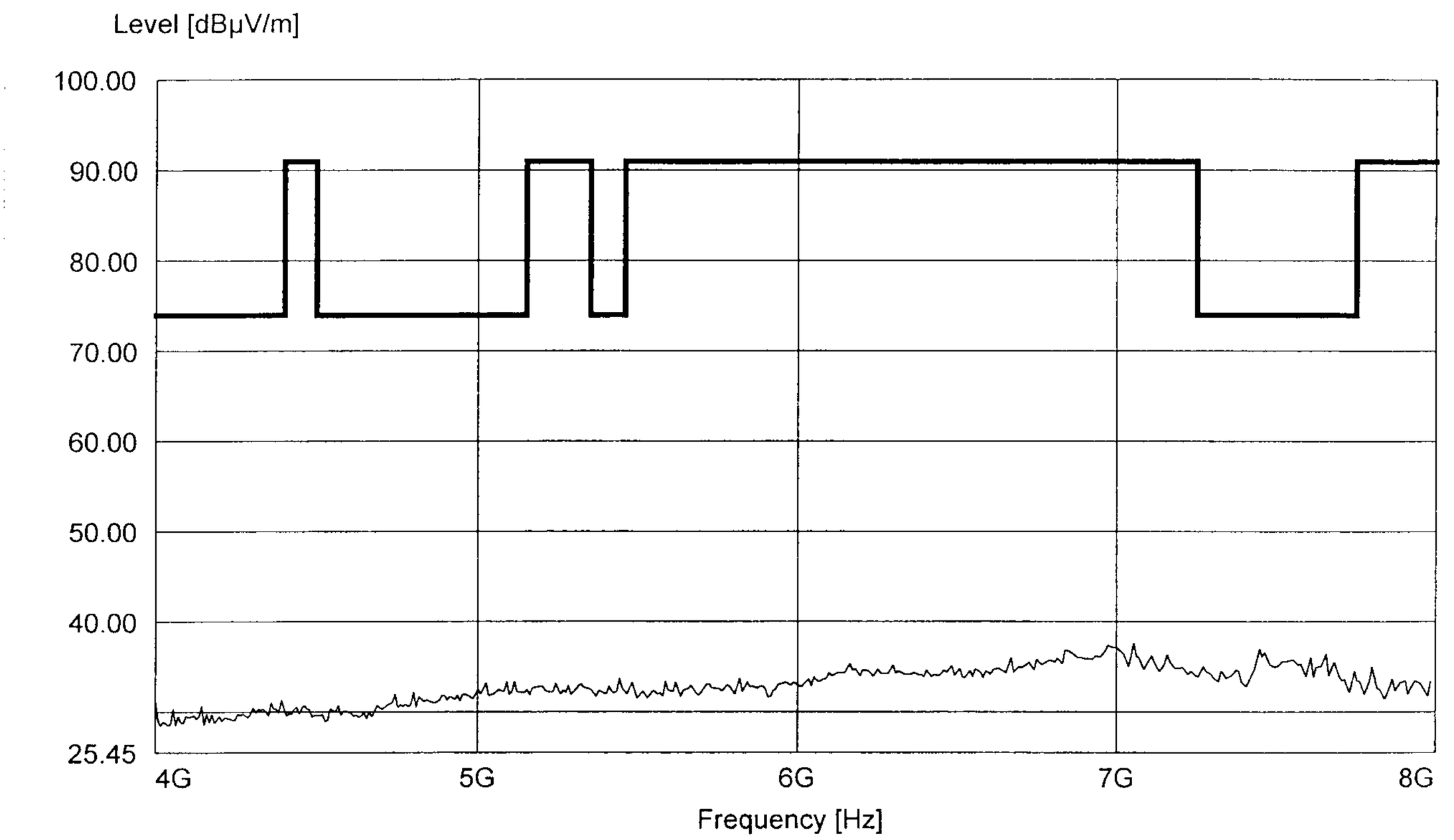
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 7.070GHz, Emax: 37.61dBµV/m, RBW: 1MHz



MES 4[illegible] . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

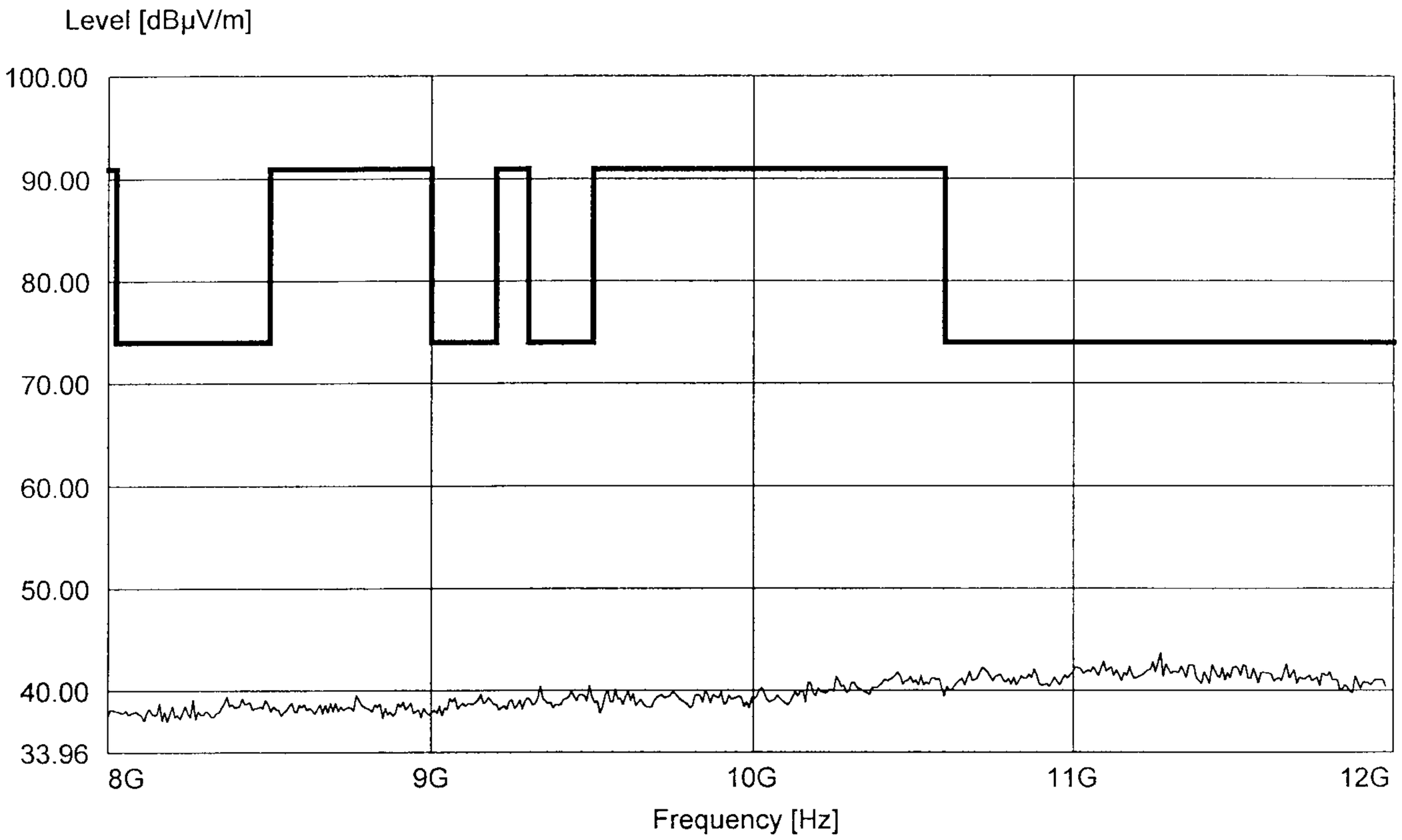
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 7.054GHz, Emax: 37.60dBµV/m, RBW: 1MHz



MES 4[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

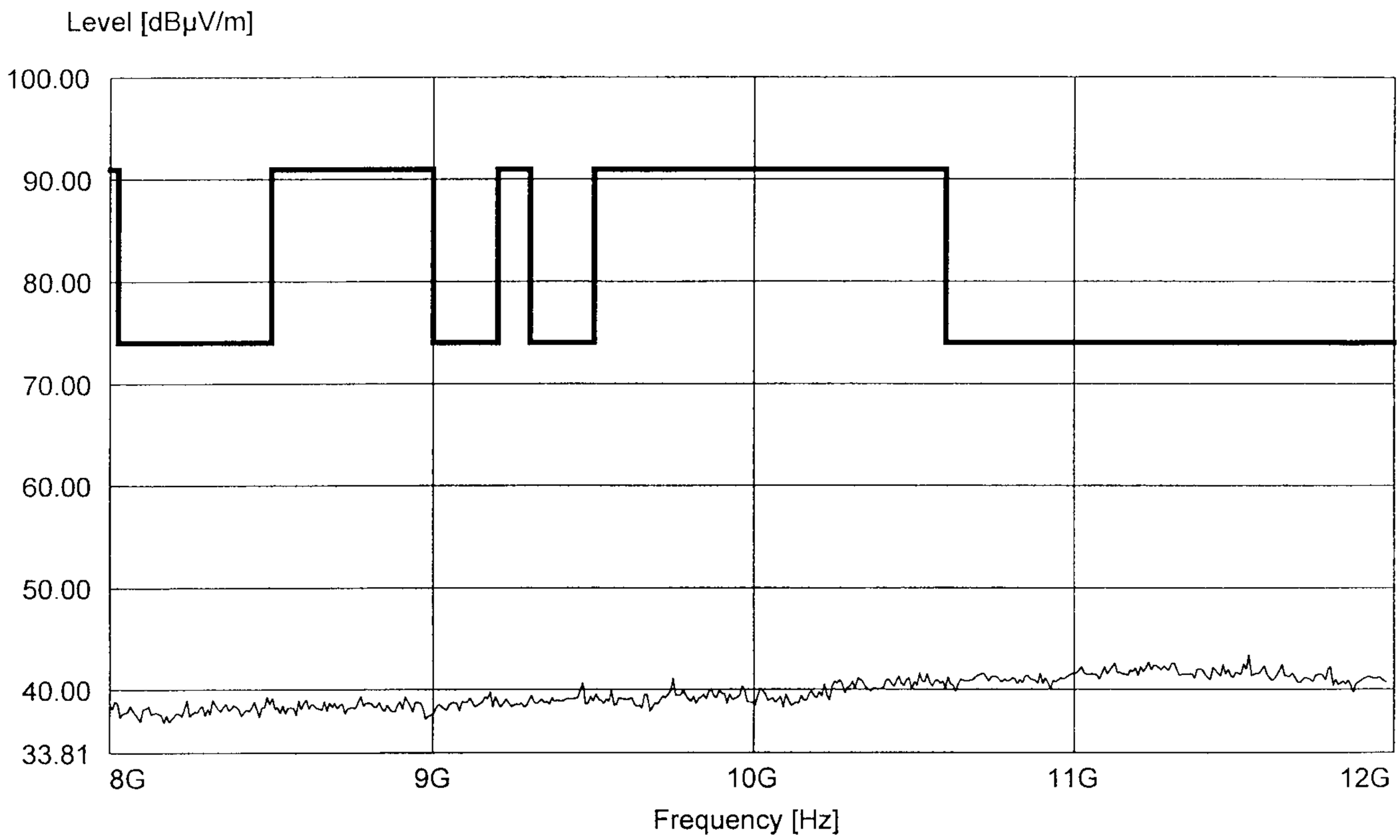
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.271GHz, Emax: 43.68dBµV/m, RBW: 1MHz



MES 5 . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

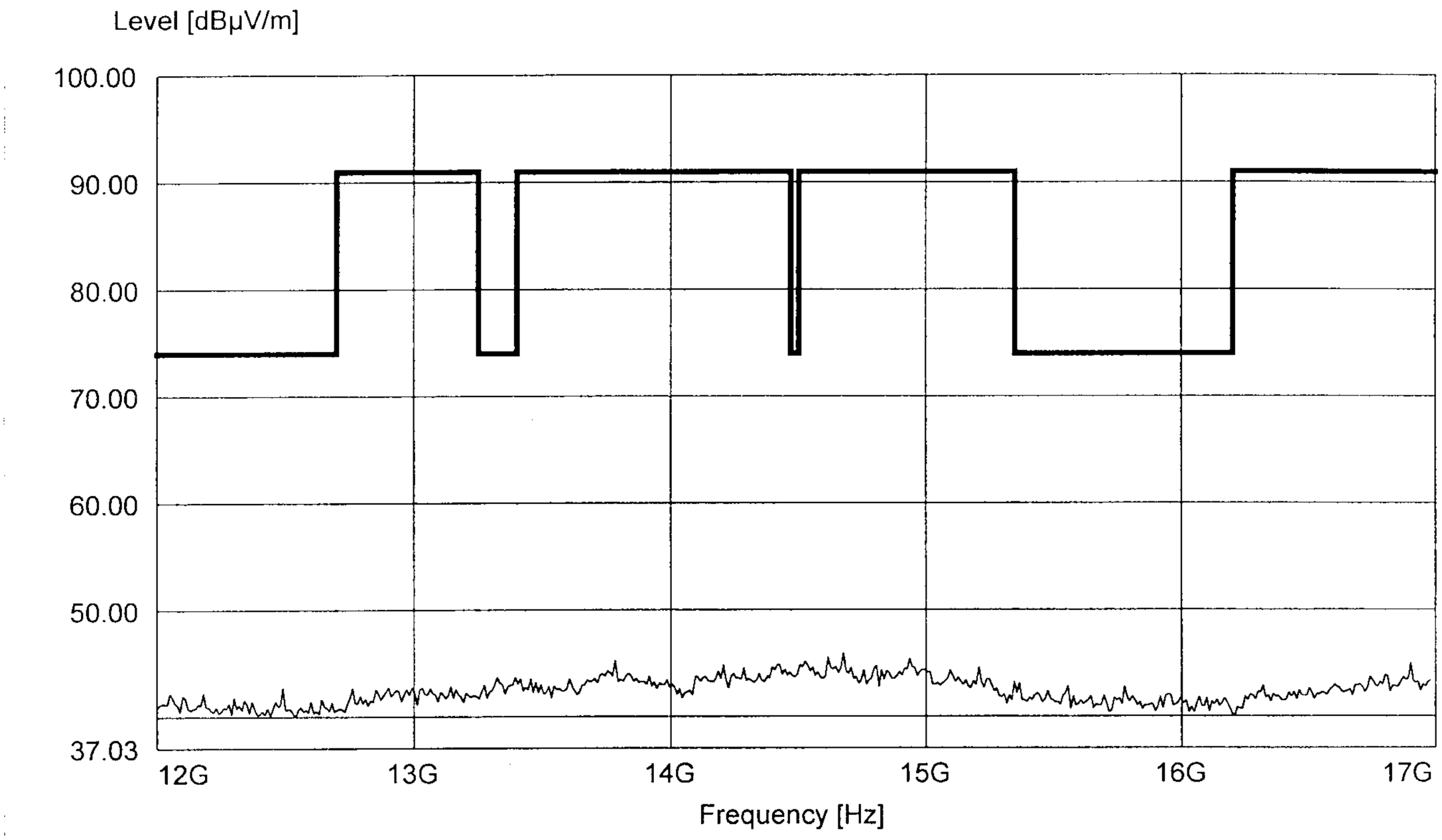
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.543GHz, Emax: 43.40dBµV/m, RBW: 1MHz



MES 5 . FCC_part_15
LIM . FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

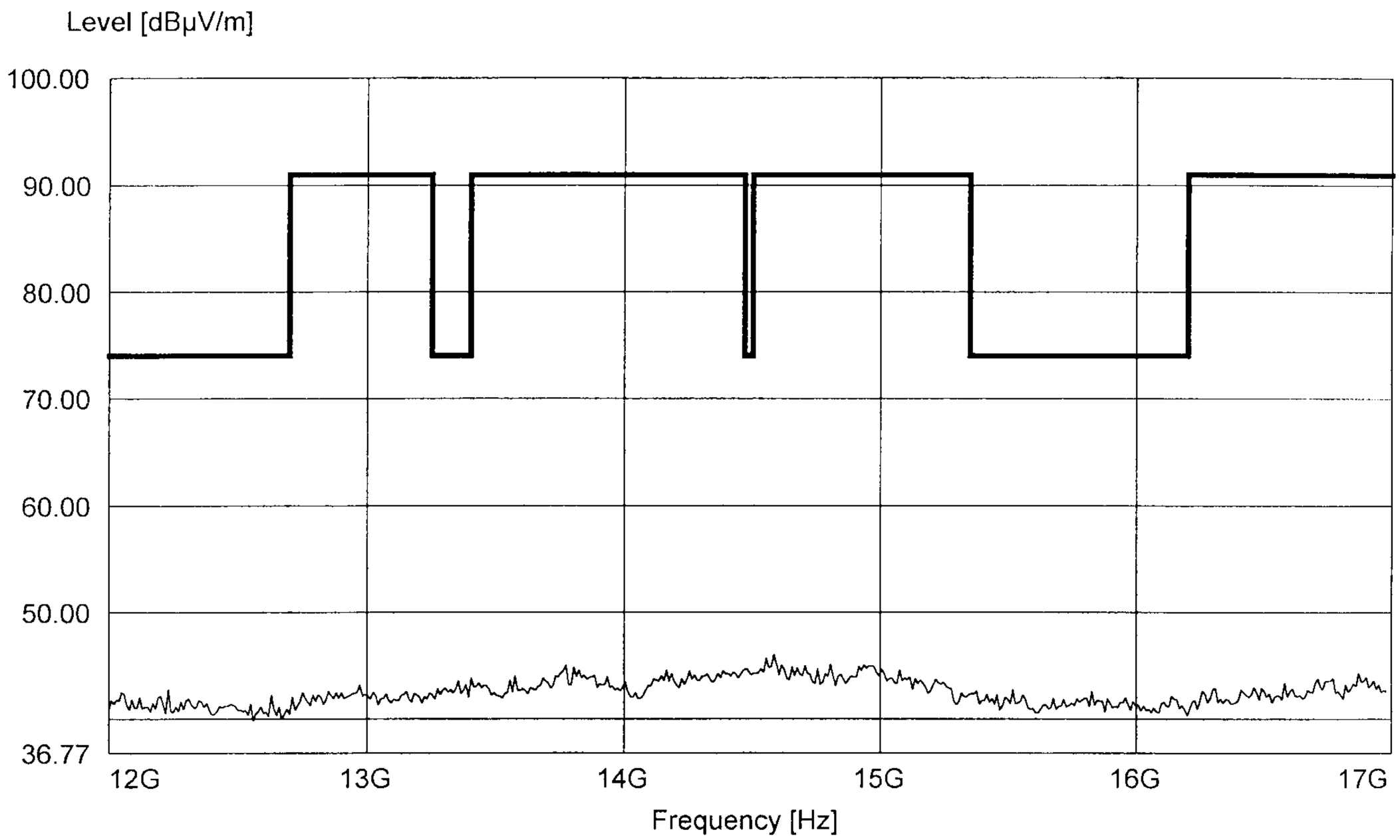
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.675GHz, Emax: 45.94dBµV/m, RBW: 1MHz



MES 6 . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.585GHz, Emax: 46.03dBµV/m, RBW: 1MHz



MES 6. FCC_part_15
LIM FCC_restricted

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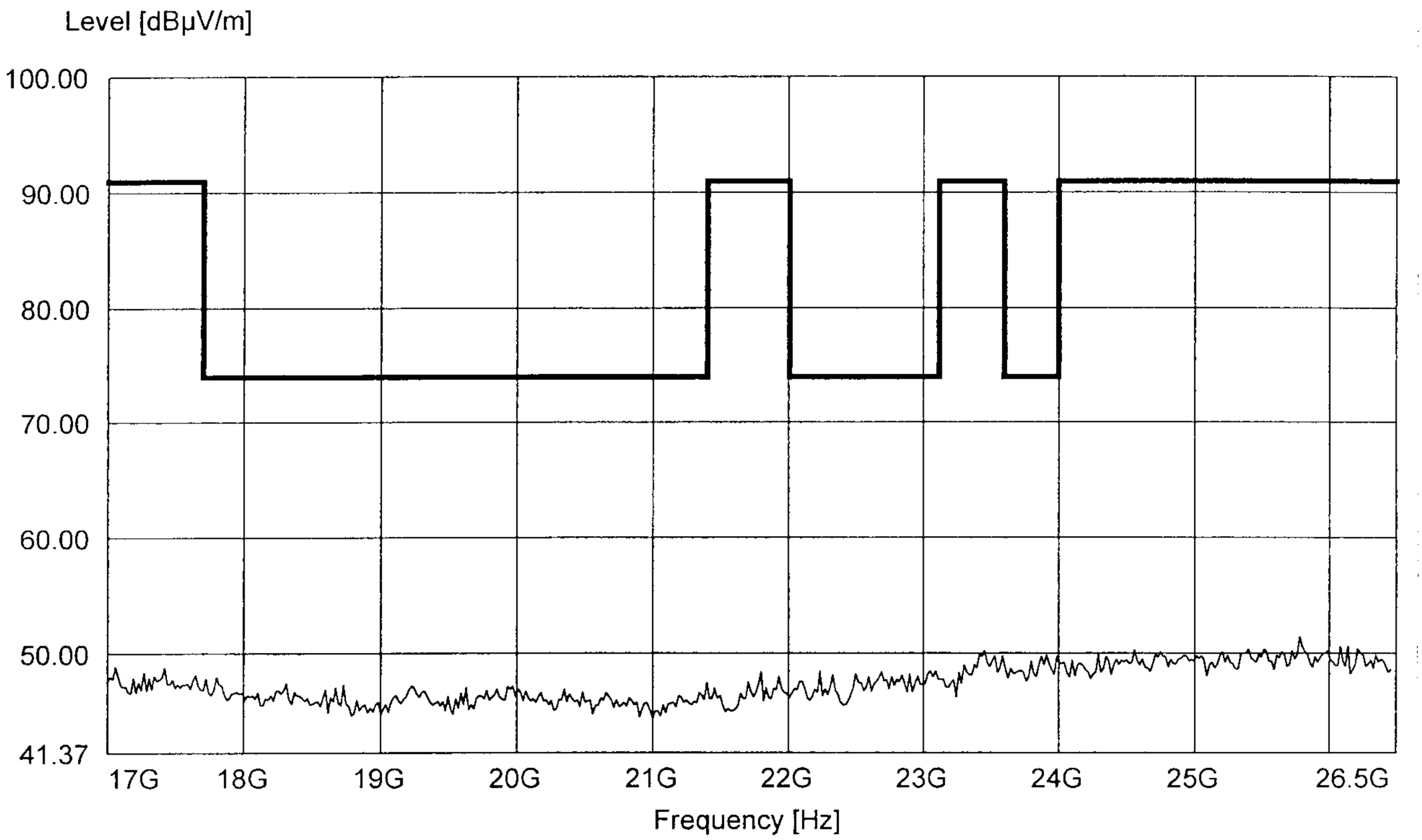
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

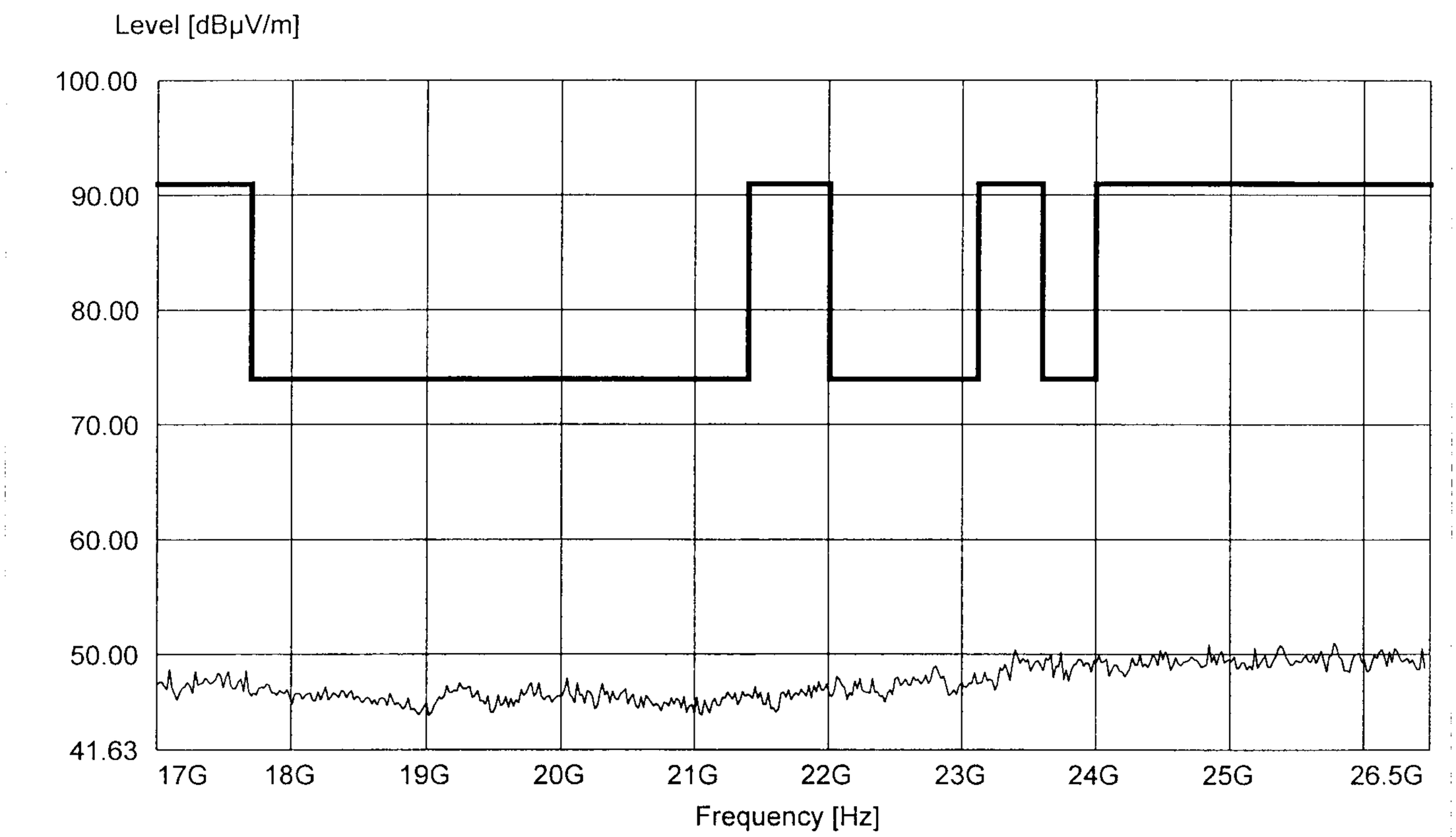
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 25.777GHz, Emax: 51.40dBµV/m, RBW: 1MHz



MES 7. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

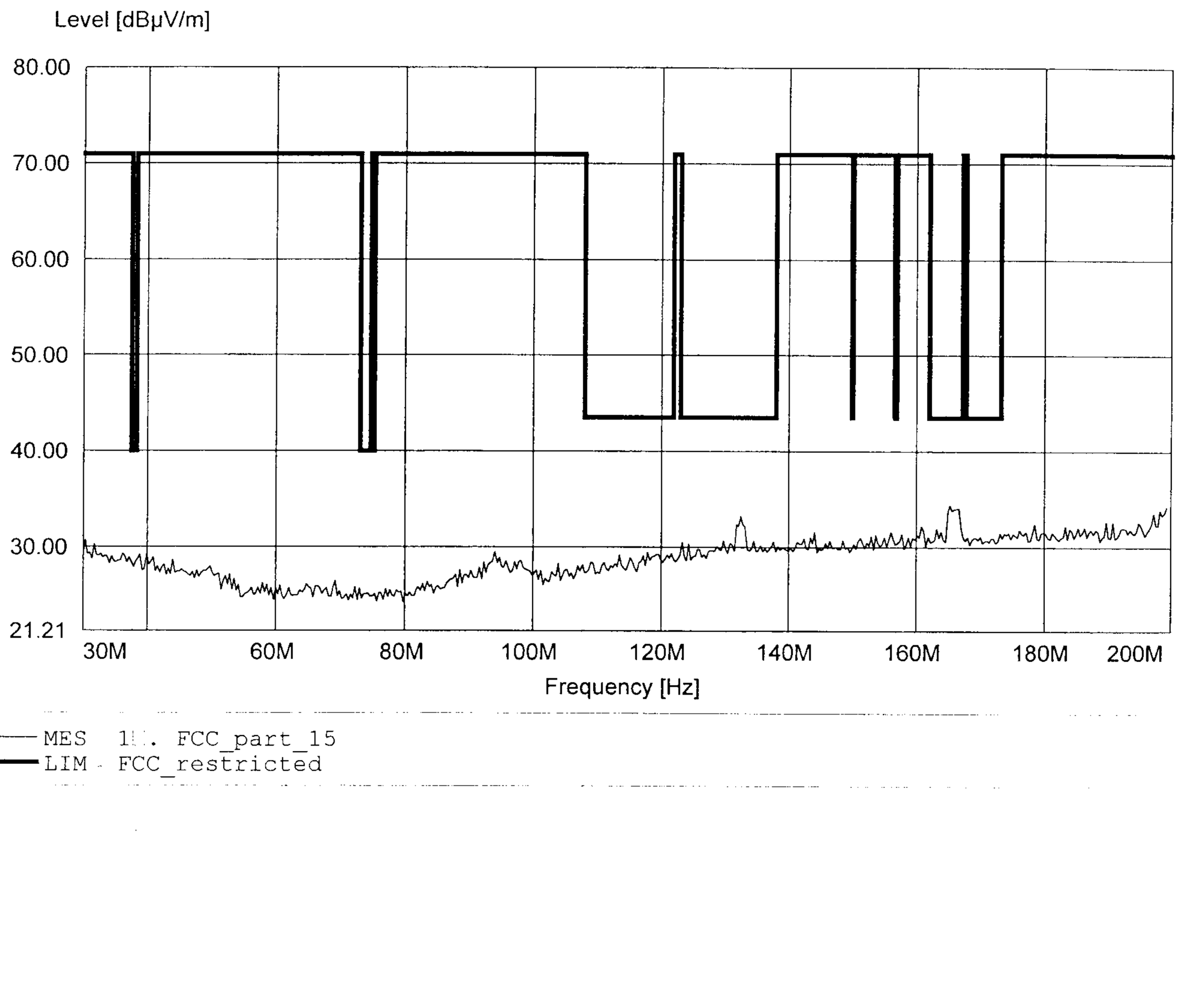
EUT:	Bluetooth CompactFlash Card / TX: 2441 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 25.777GHz, Emax: 51.00dBµV/m, RBW: 1MHz



MES 7[illegible]. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

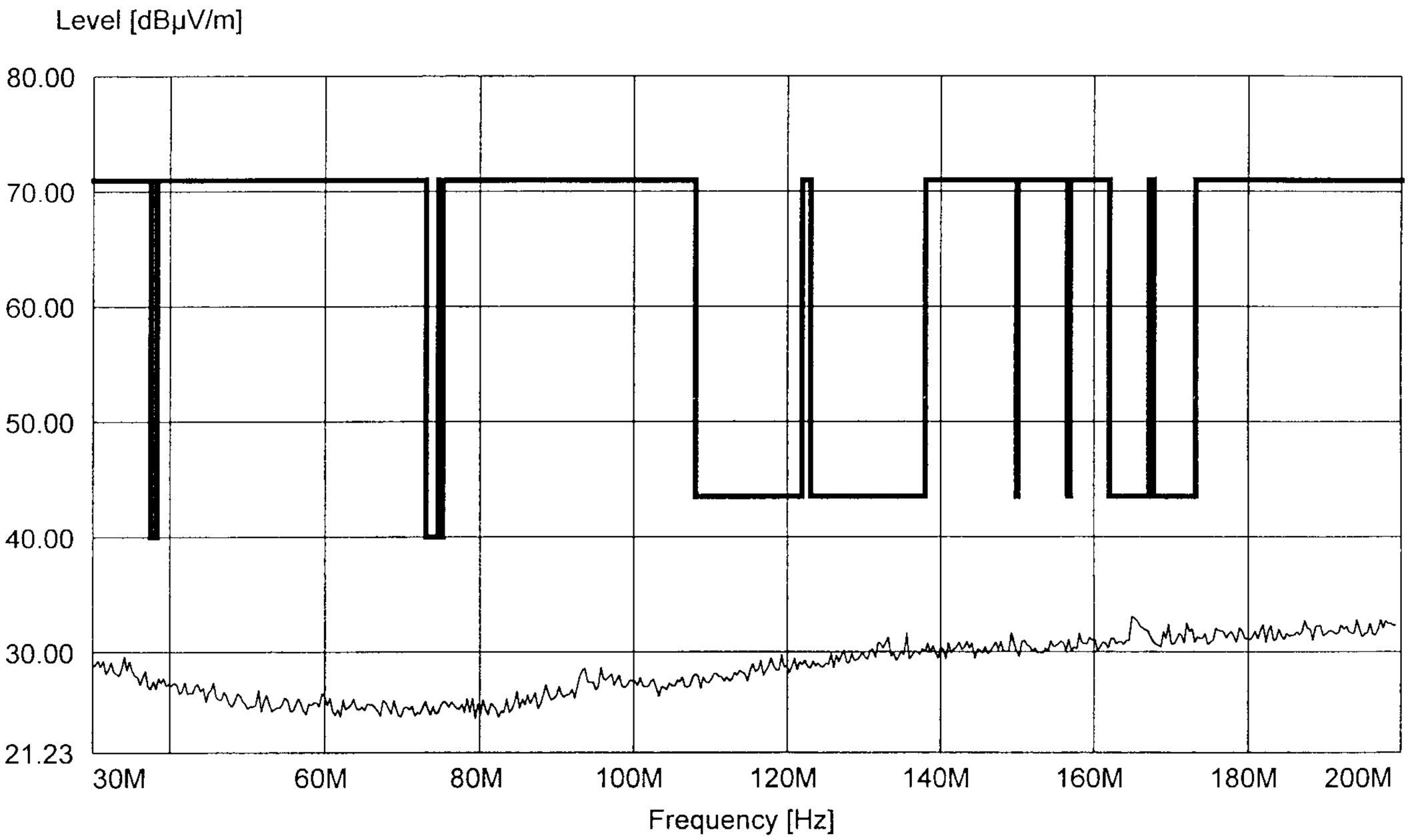
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 165.251MHz, Emax: 34.37dBµV/m, RBW: 100kHz



MES 1[illegible]. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

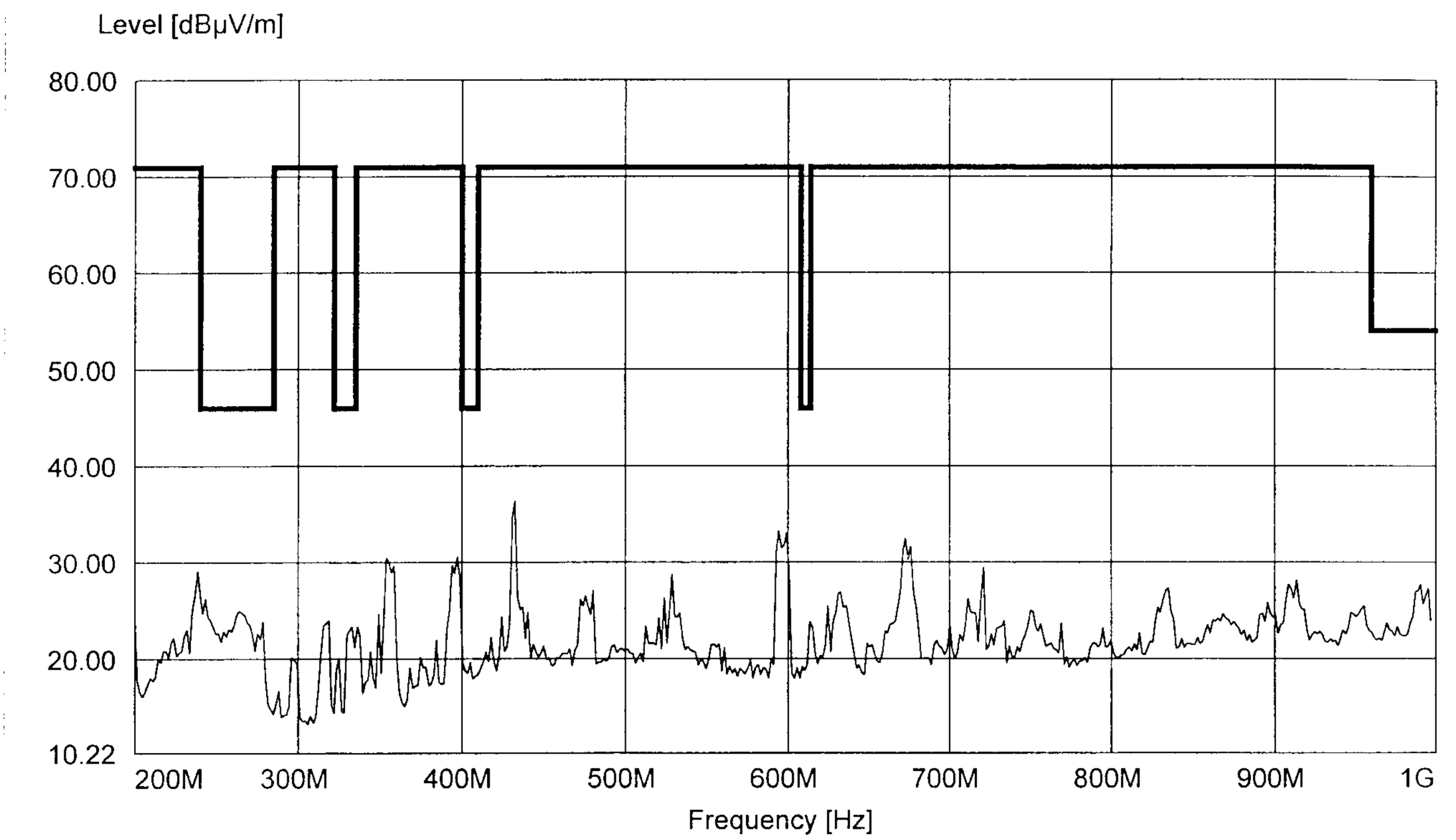
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HK 116
Comment 2:	Freq: 164.910MHz, Emax: 33.00dBµV/m, RBW: 100kHz



MES 1 . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

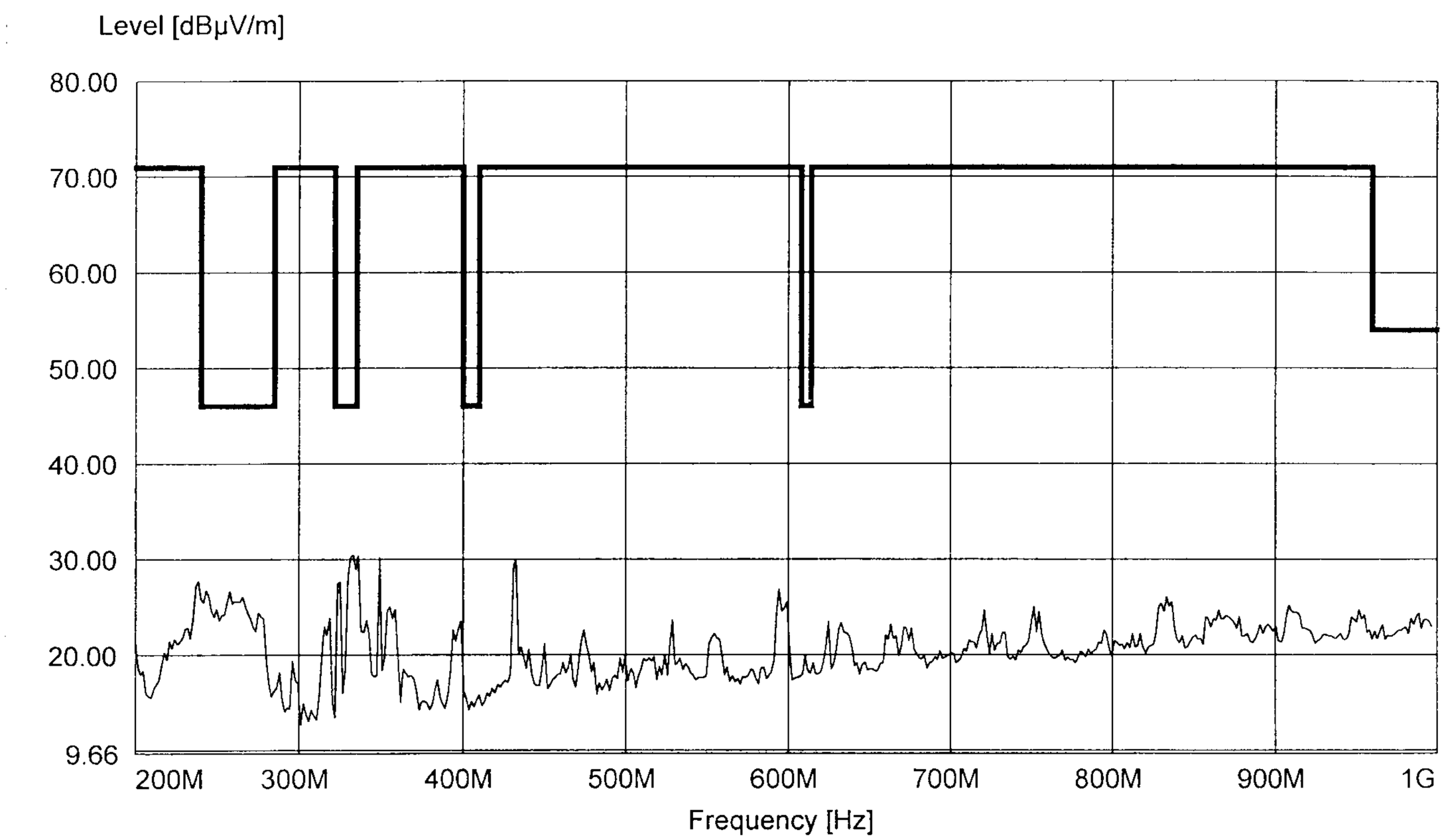
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 432.465MHz, Emax: 36.40dBµV/m, RBW: 100kHz



MES 2. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

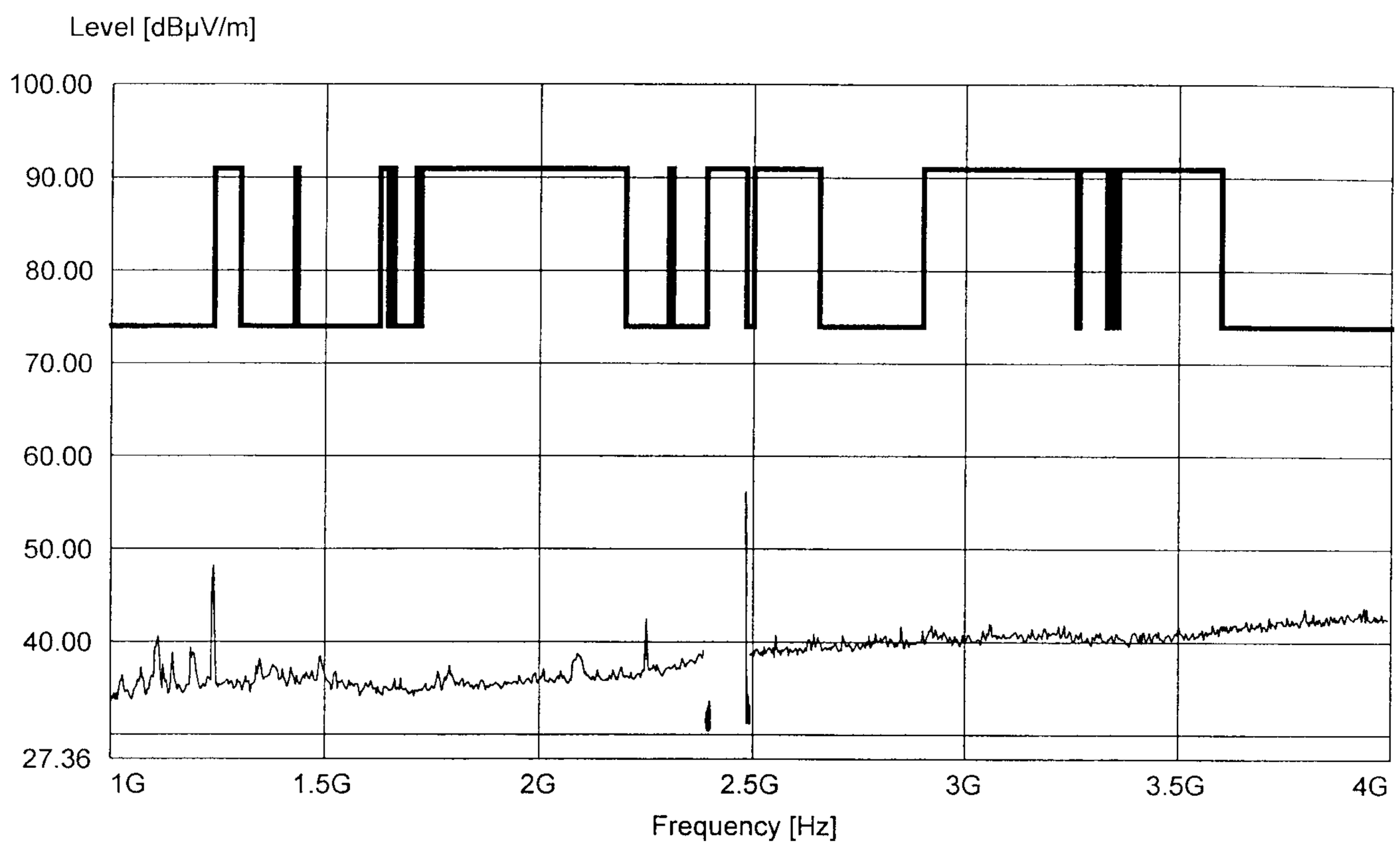
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15.247 / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL 223, amplif.
Comment 2:	Freq: 333.066MHz, Emax: 30.44dBµV/m, RBW: 100kHz



MES 2[illegible]. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

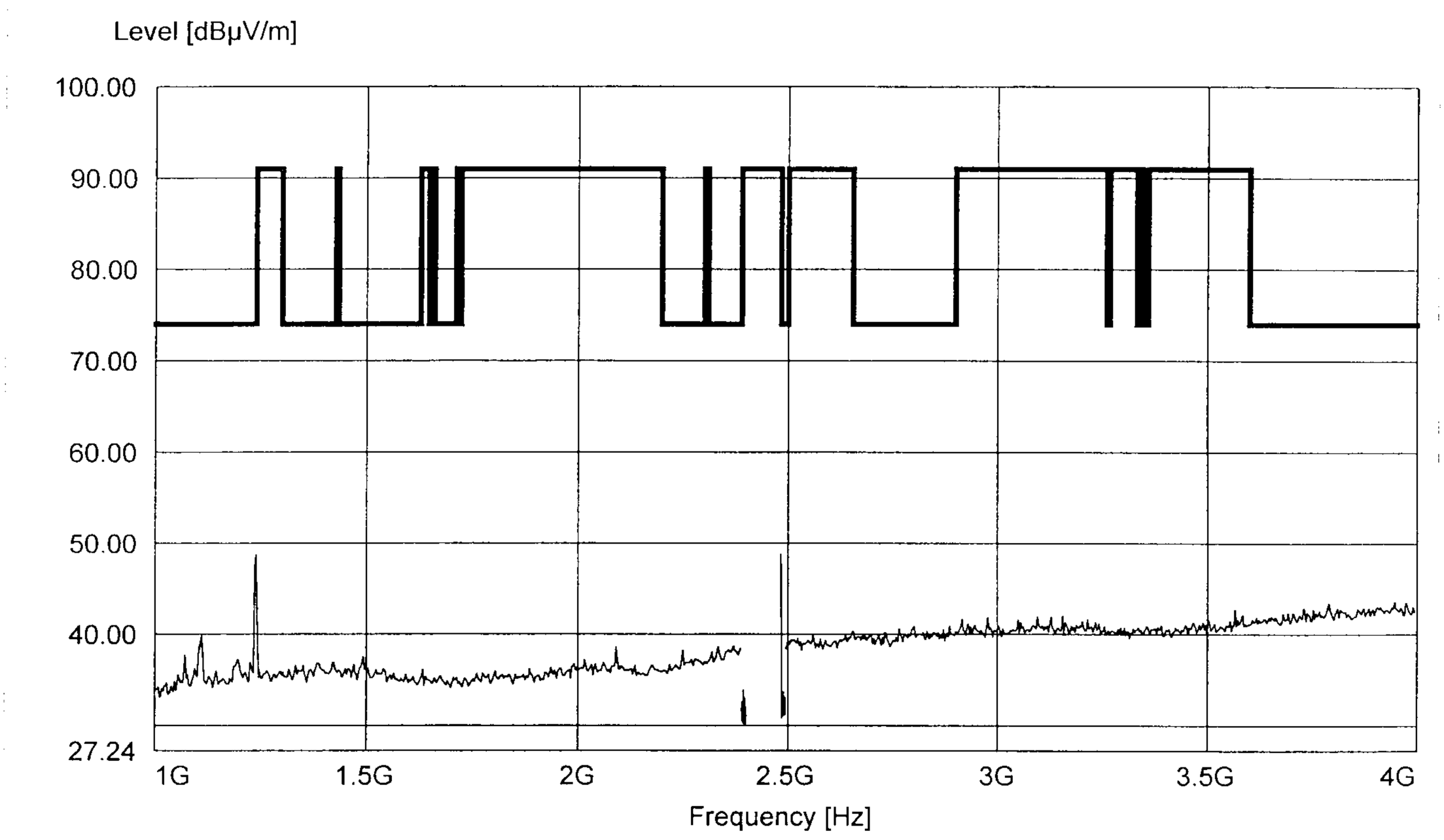
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 2.484GHz, Emax: 56.13dBµV/m, RBW: 1MHz



MES 3_. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, amplif.
Comment 2:	Freq: 2.484GHz, Emax: 48.84dBµV/m, RBW: 1MHz



MES 3 . FCC_part_15
LIM - FCC_restricted

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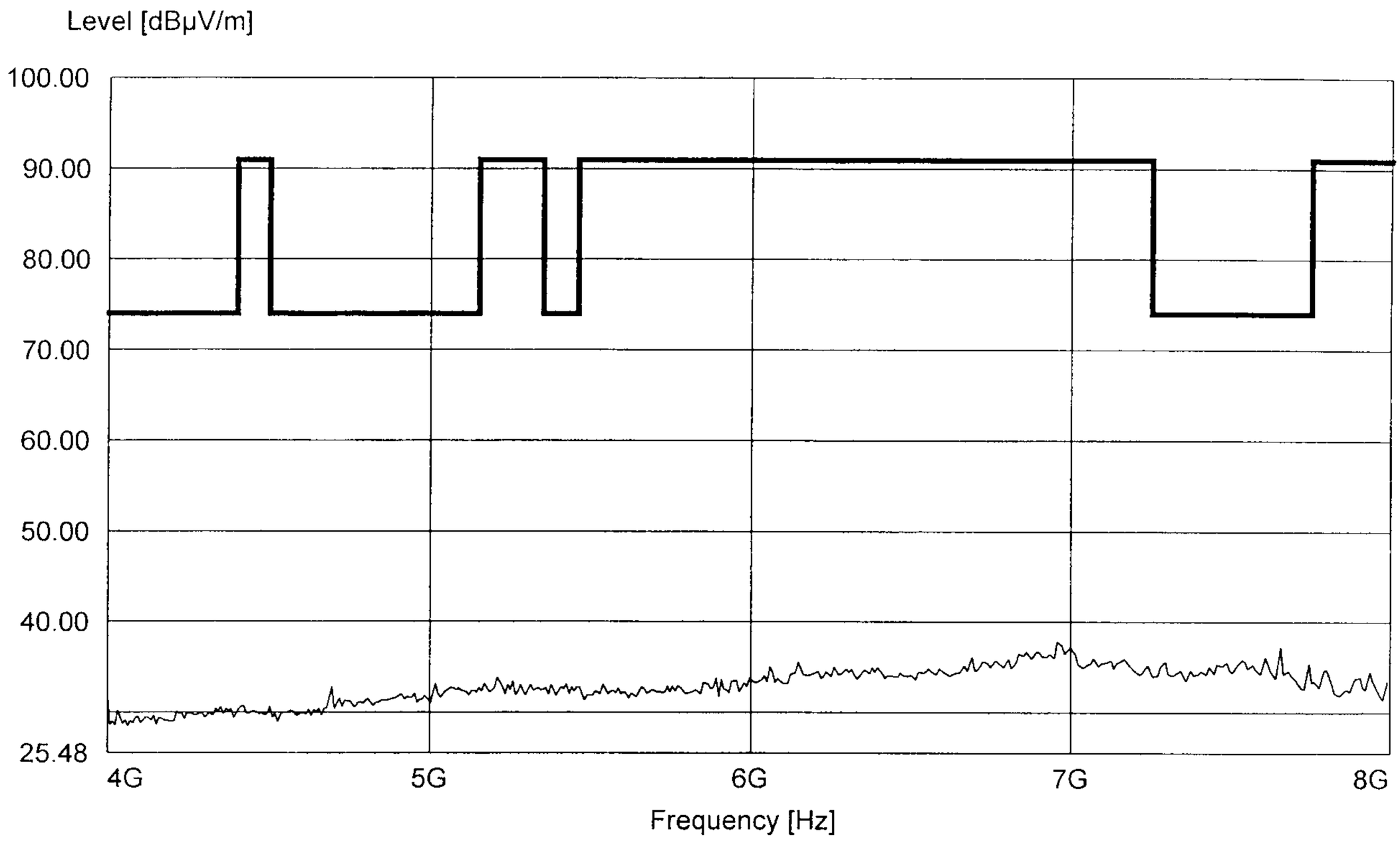
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 6.958GHz, Emax: 37.82dBµV/m, RBW: 1MHz



MES 4 . FCC_part_15
LIM - FCC_restricted

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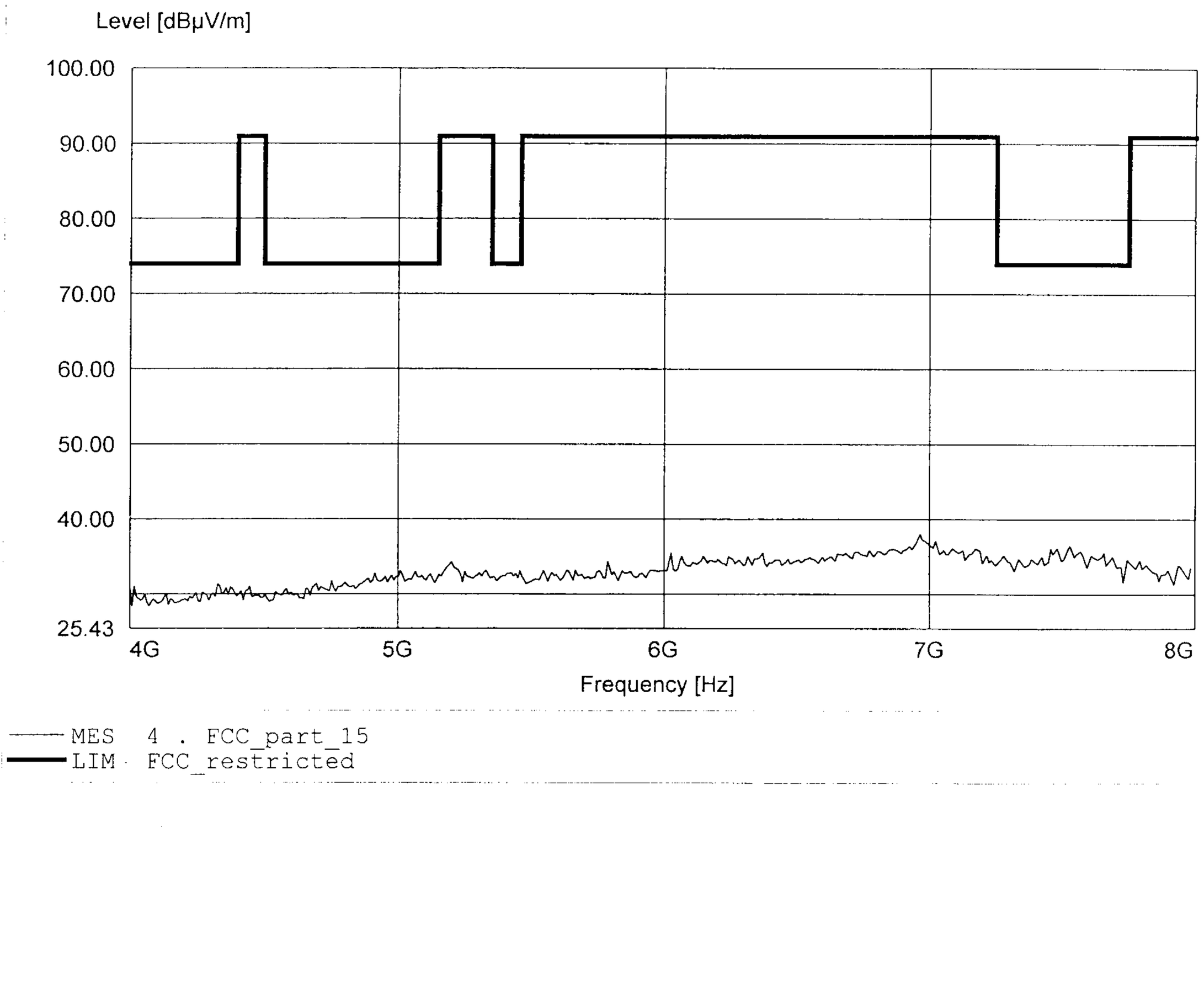
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

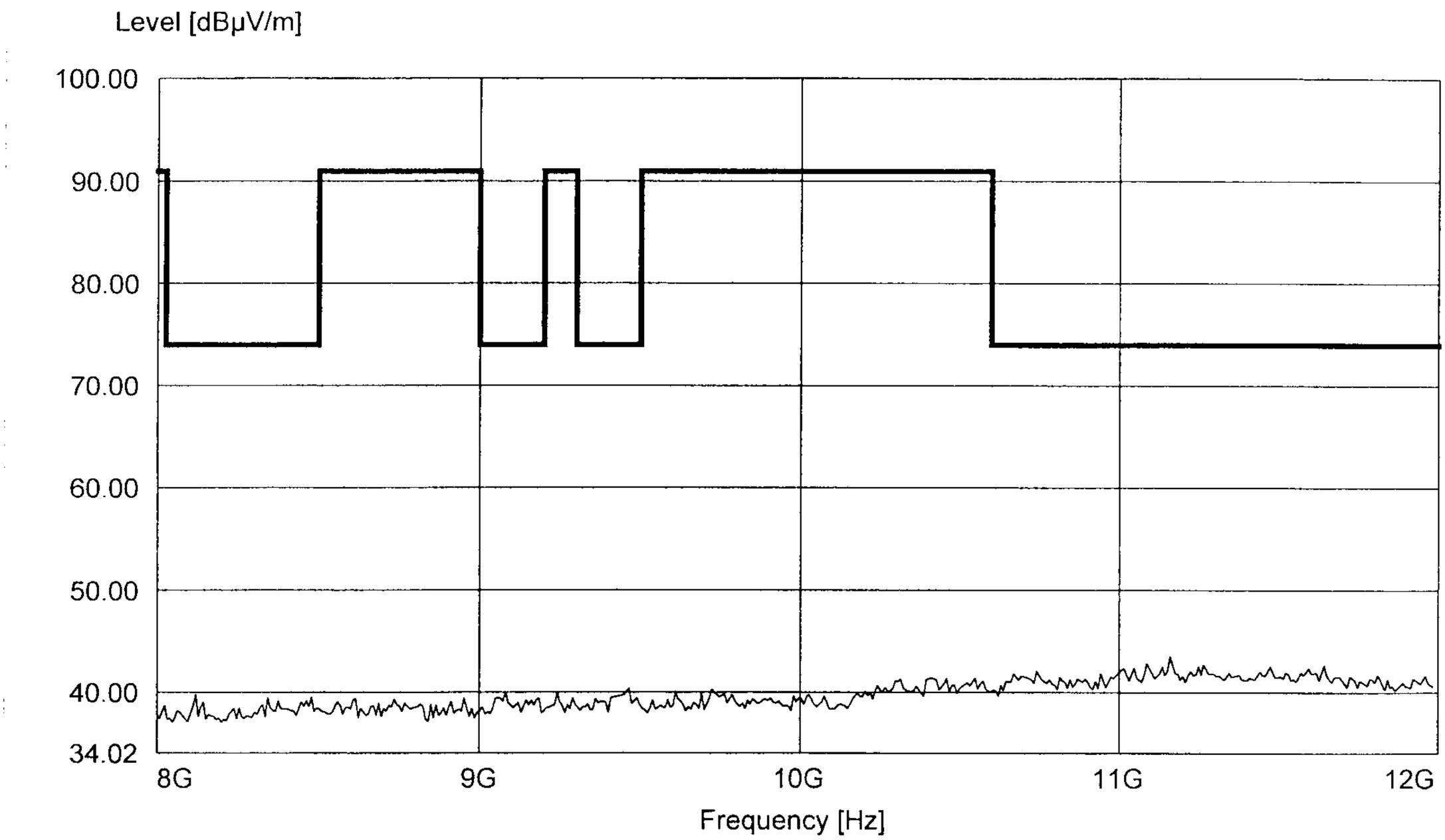
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 6.966GHz, Emax: 38.02dBµV/m, RBW: 1MHz



MES 4 . FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

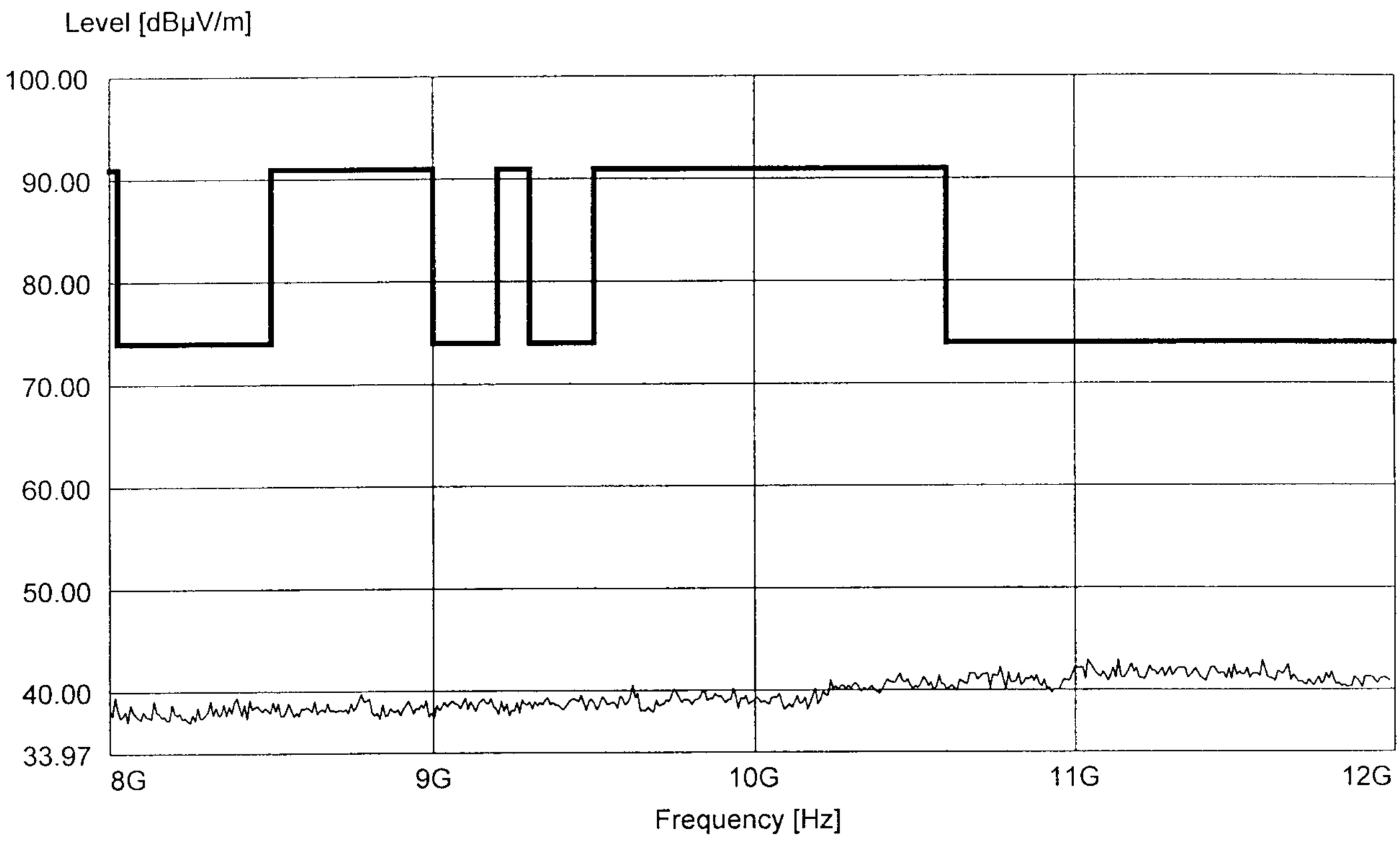
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.158GHz, Emax: 43.50dBµV/m, RBW: 1MHz



MES 5[illegible] . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

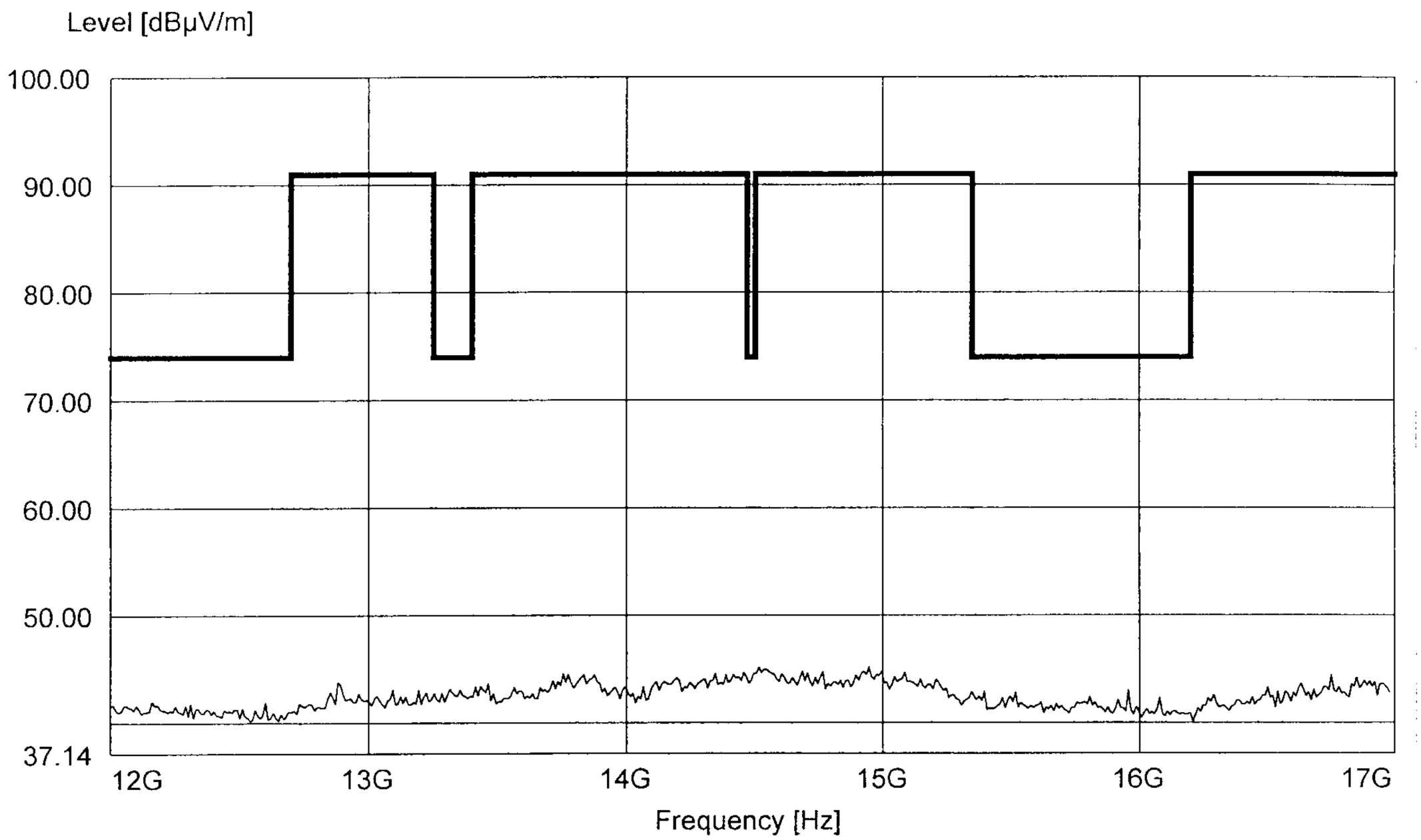
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 11.038GHz, Emax: 42.97dBµV/m, RBW: 1MHz



MES 5. FCC_part_15
LIM FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.946GHz, Emax: 45.19dBµV/m, RBW: 1MHz



MES 6[illegible]. FCC_part_15
LIM - FCC_restricted

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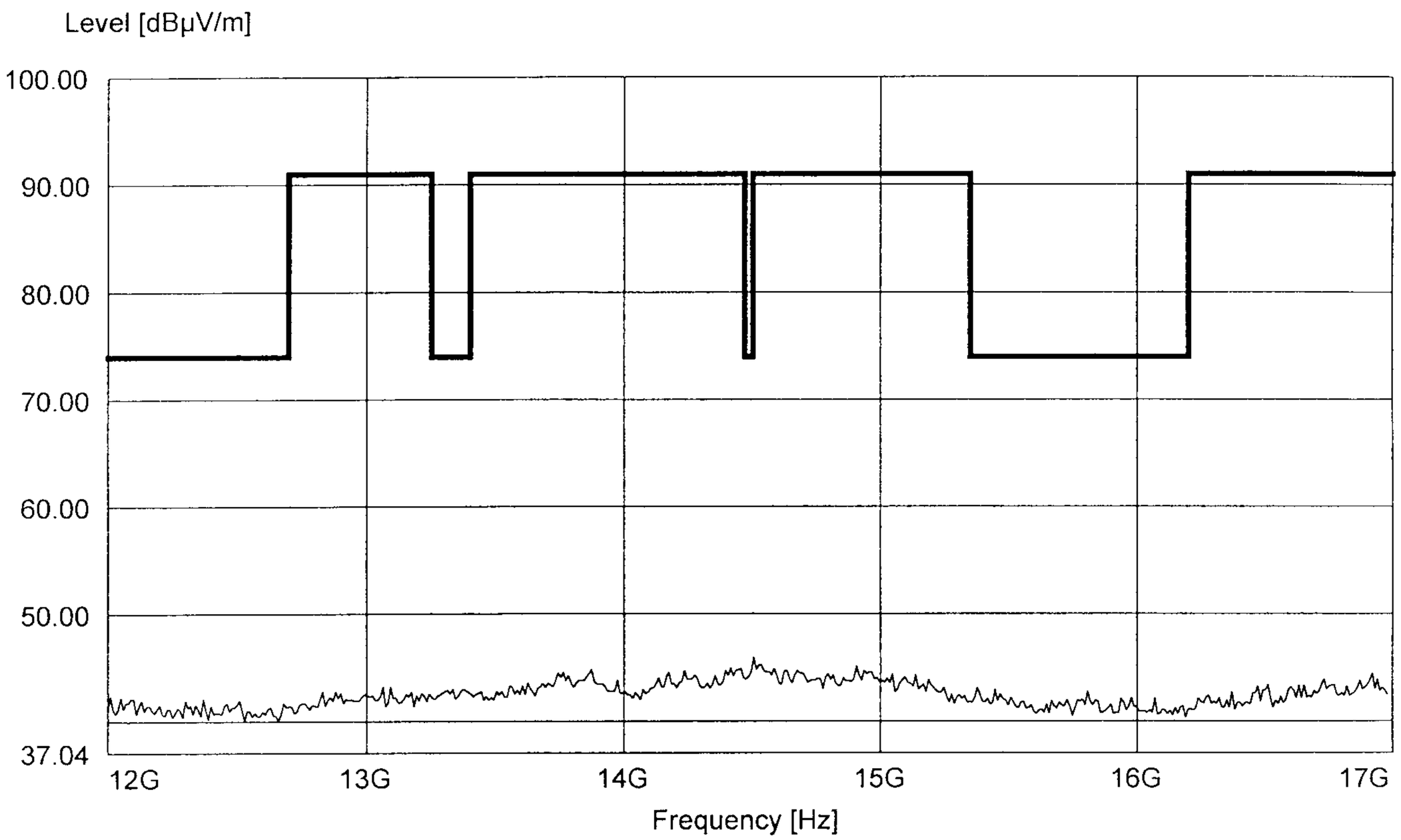
Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

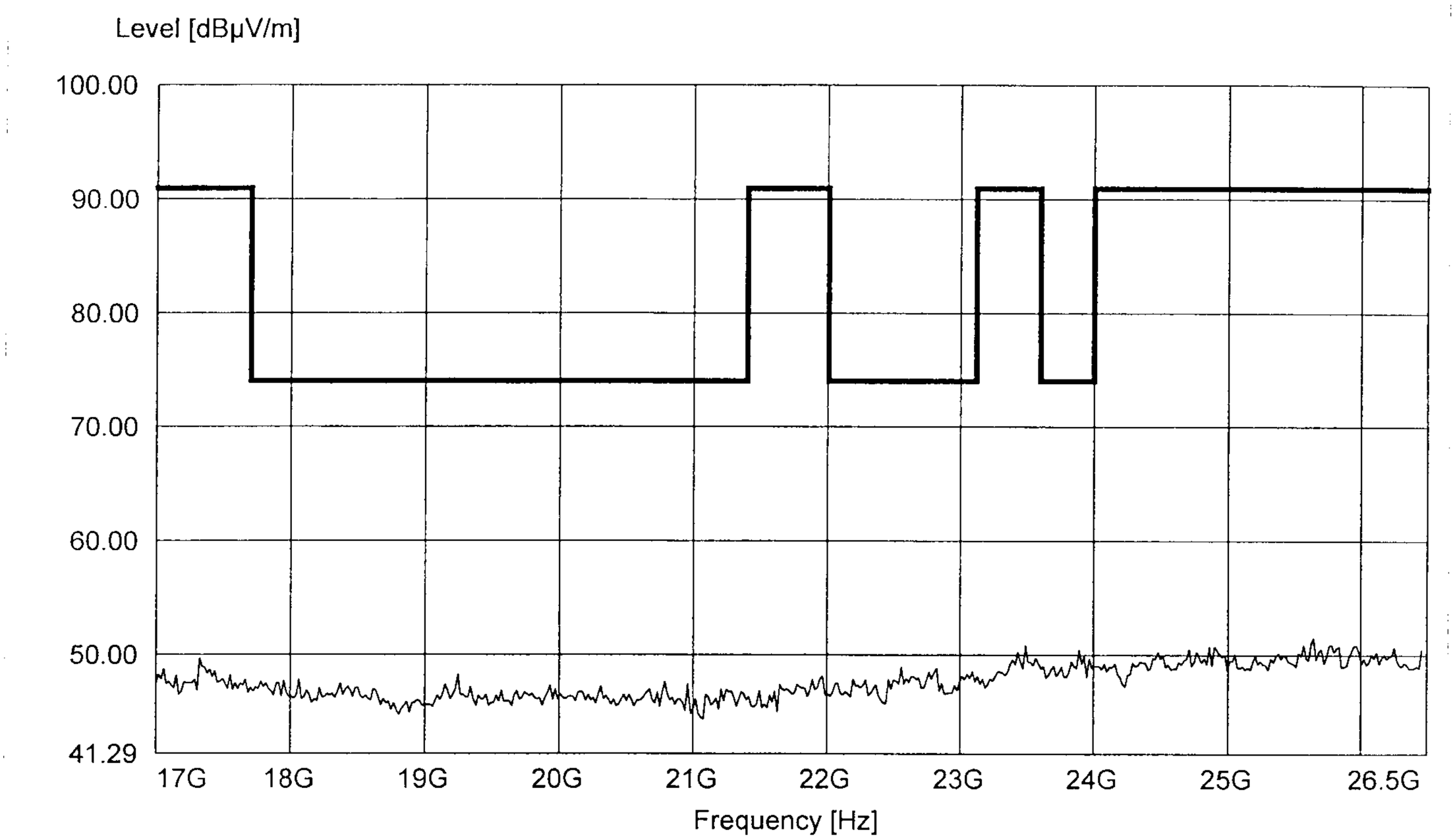
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: BBHA2190D, ampl.+HP.
Comment 2:	Freq: 14.505GHz, Emax: 45.97dBµV/m, RBW: 1MHz



MES 6□. FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

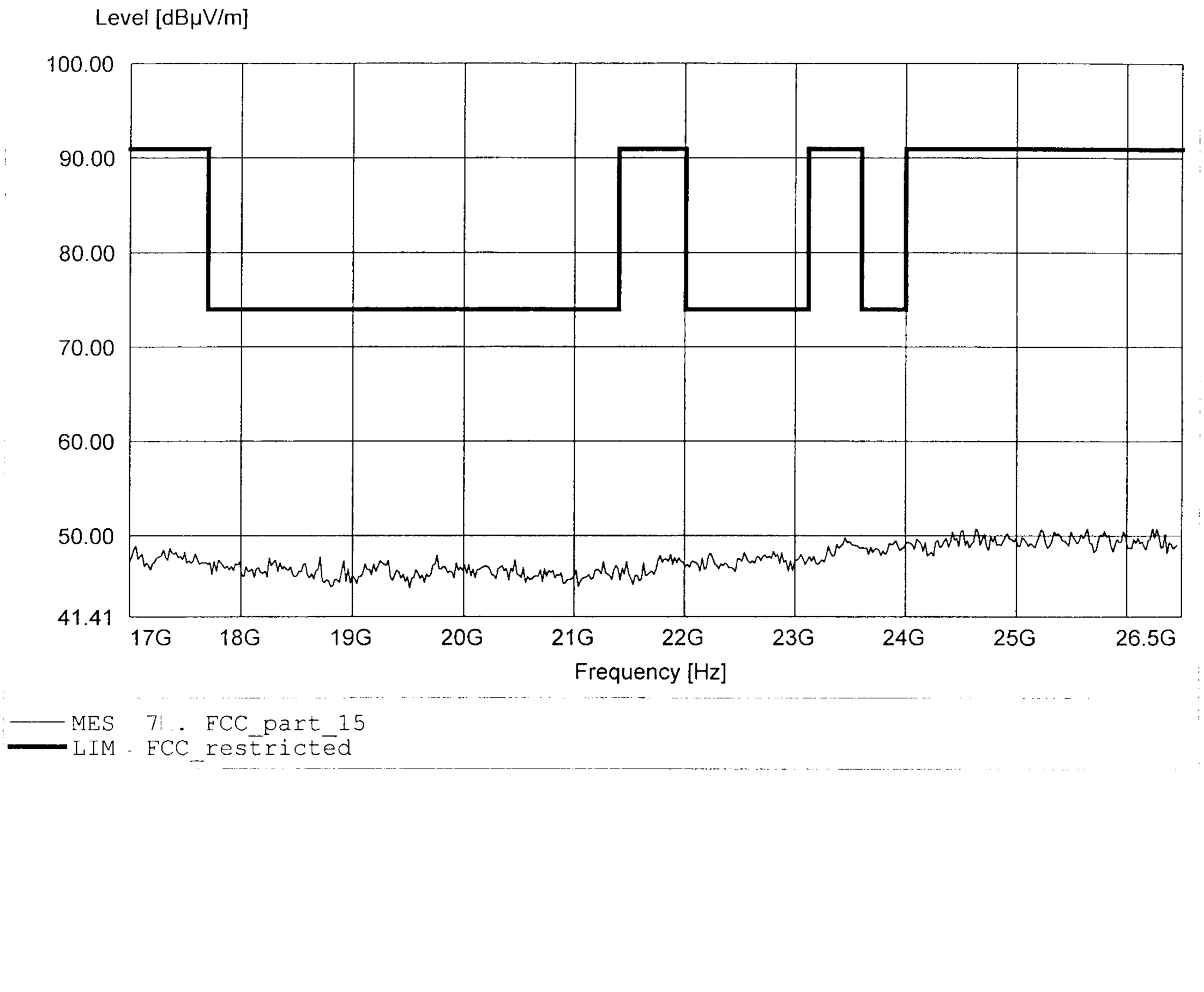
EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 25.643GHz, Emax: 51.53dBµV/m, RBW: 1MHz



MES 7 . FCC_part_15
LIM - FCC_restricted

Spurious emissions Field Strength Tx
FCC RULES PART 15, SUBPART C

EUT:	Bluetooth CompactFlash Card / TX: 2480 MHz
Model:	SOC1S02
Manufacturer:	SysOnChip Inc. Samsung Electro-Mechanics
Operating Condition:	Unom: 3.3 V DC (powered by PCMCIA slot), Tnom:23°C
Test Site / Operator:	ETS / Mr. Hoppe
Test Specification:	according to §15247, Limit 20 dB up peak detector / mode: Tx
Comment 1:	Dist.: 3m, Ant.: HL025, amplif.
Comment 2:	Freq: 26.233GHz, Emax: 50.81dBµV/m, RBW: 1MHz

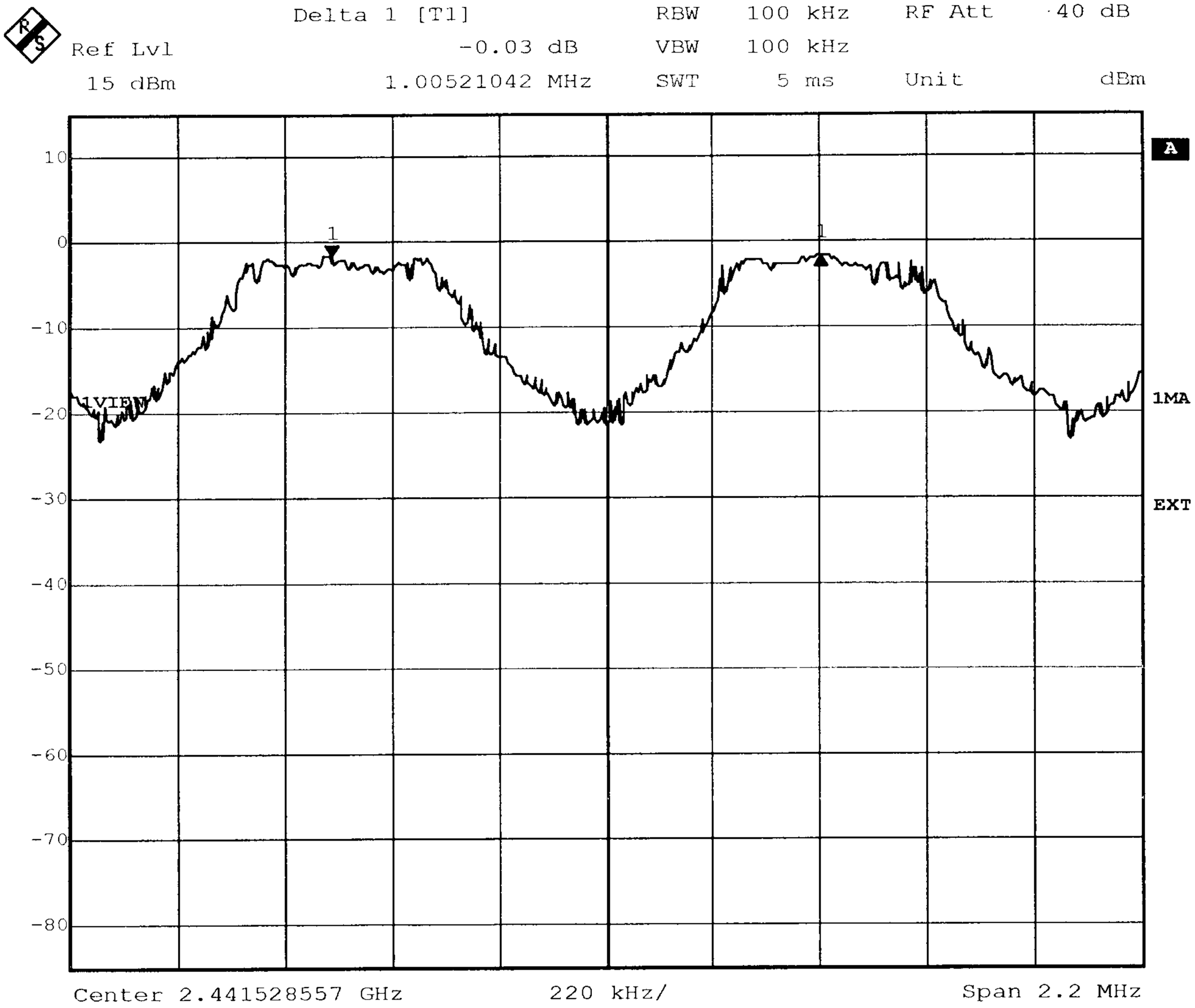


Appendix D

Spurious Emissions conducted - Transmitter operating

Appendix E

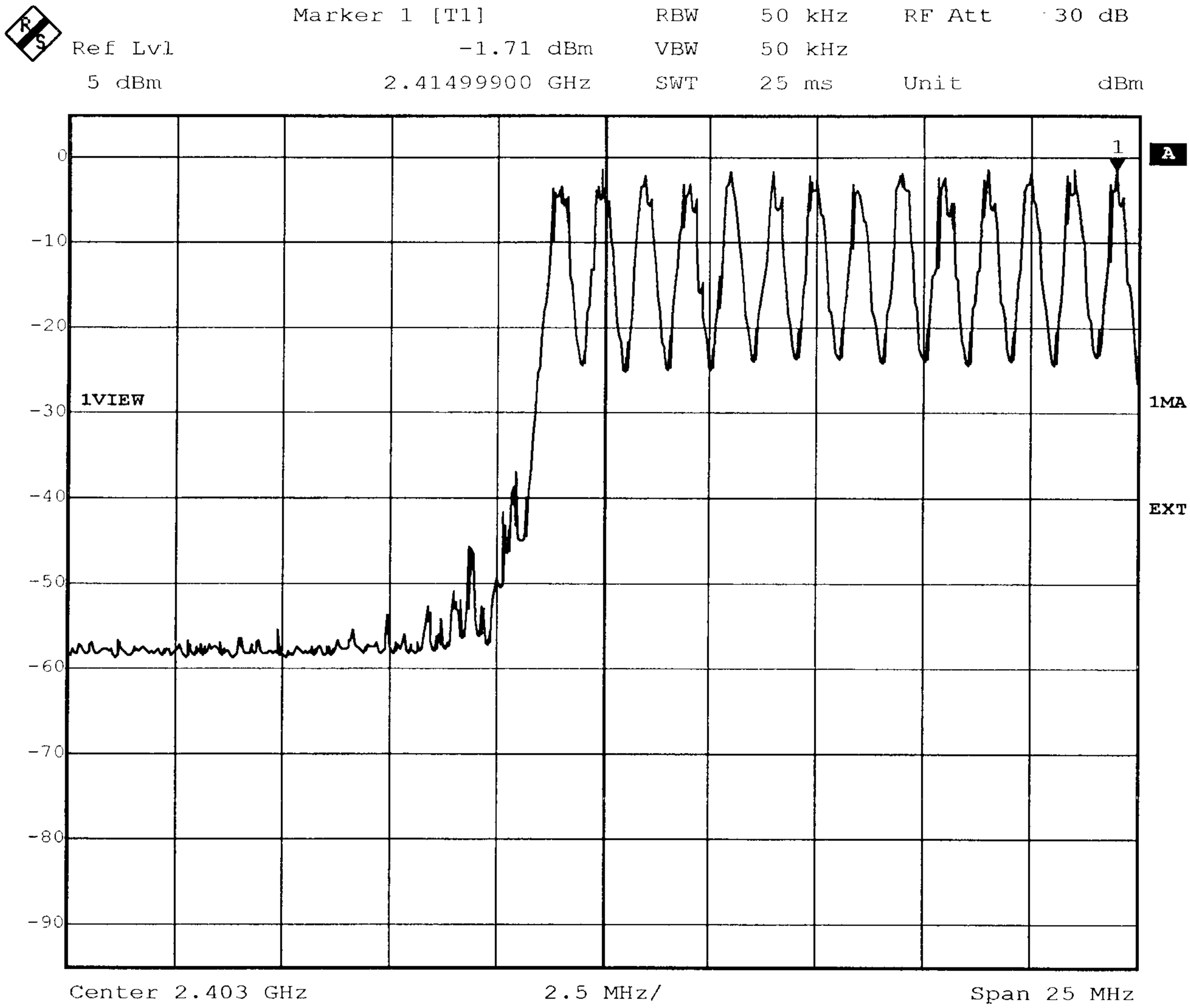
Carrier Frequency Separation



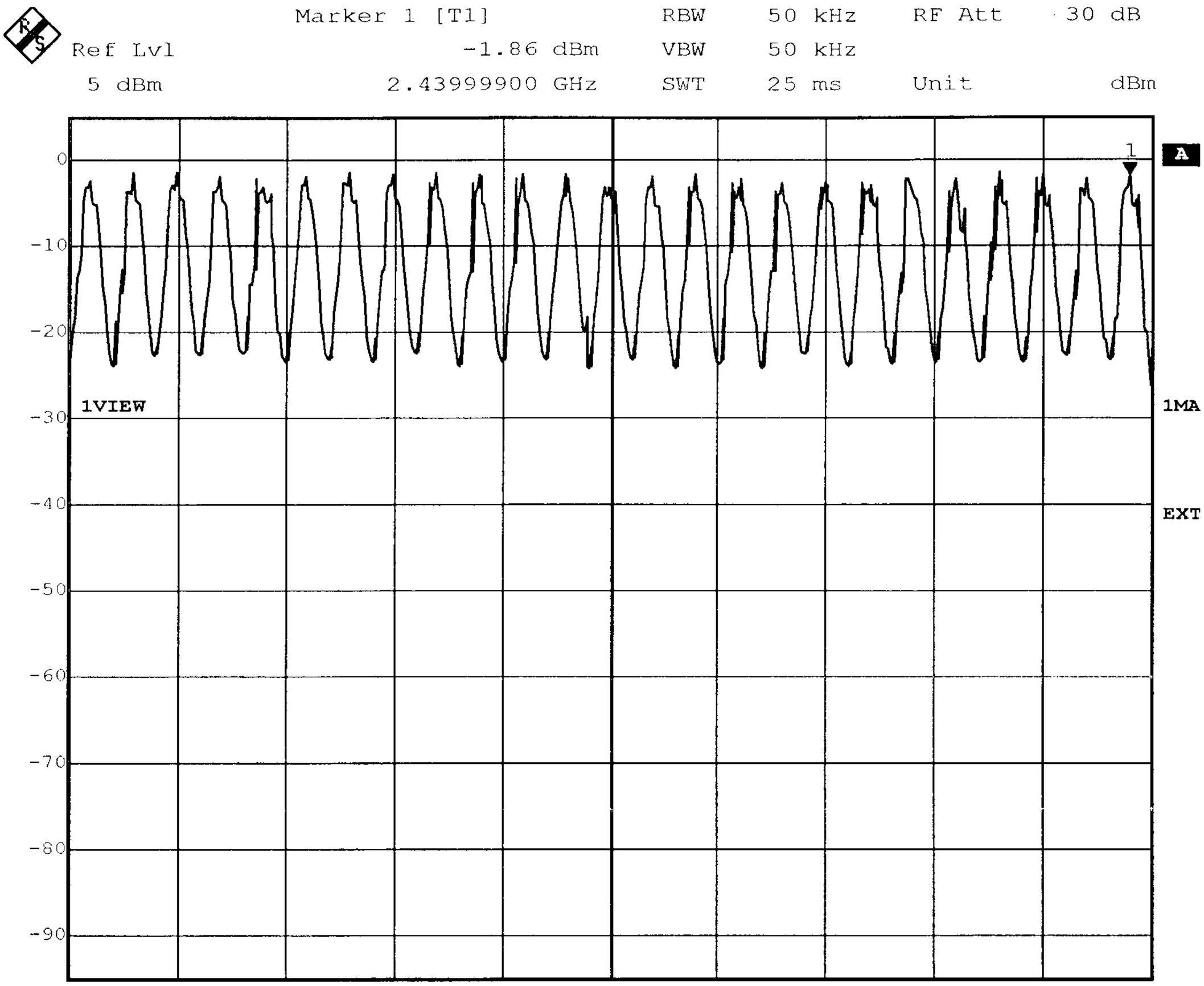
Title: Carrier Frequency Separation
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 12:18:28

Appendix F

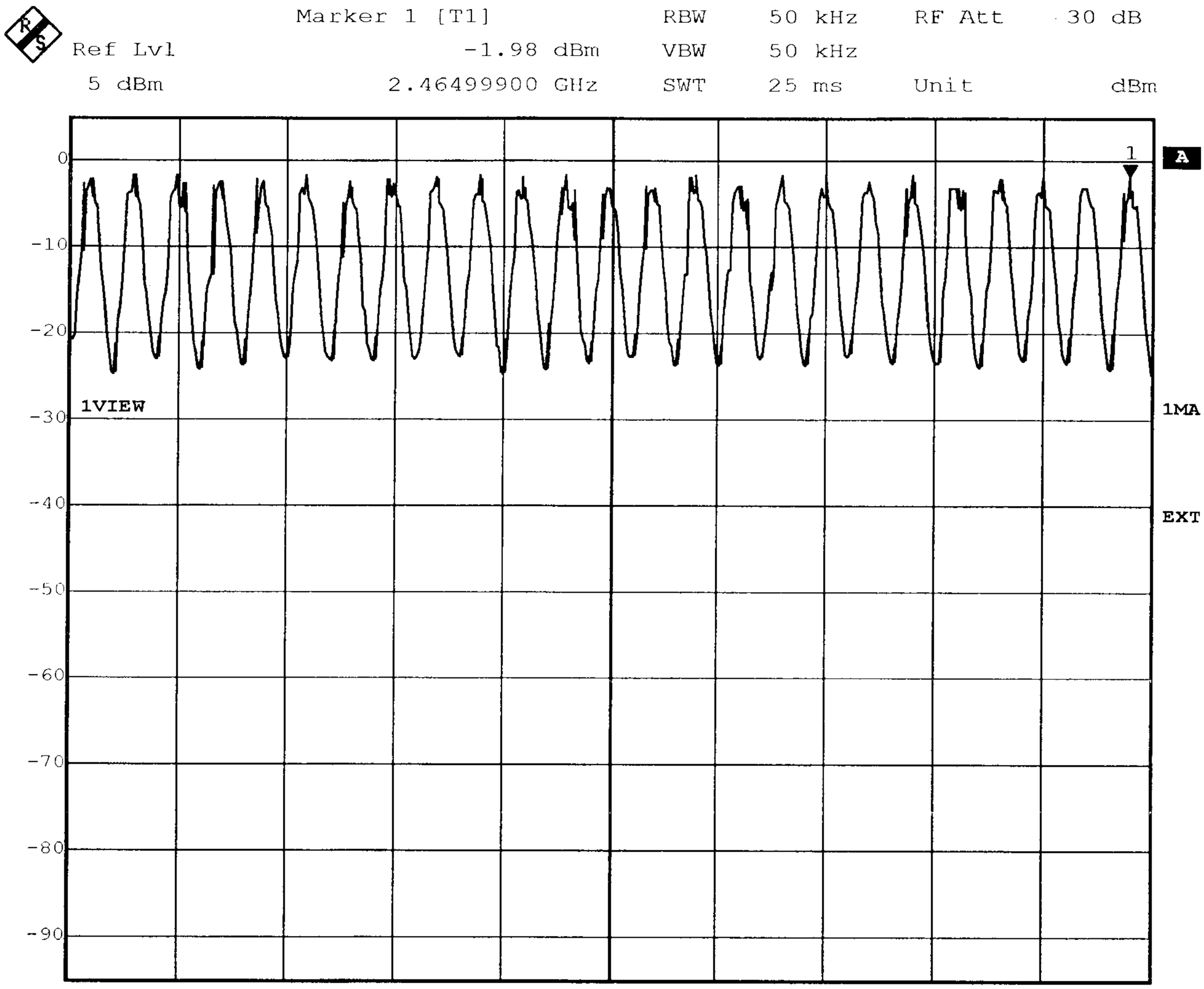
Number of Hopping Frequencies



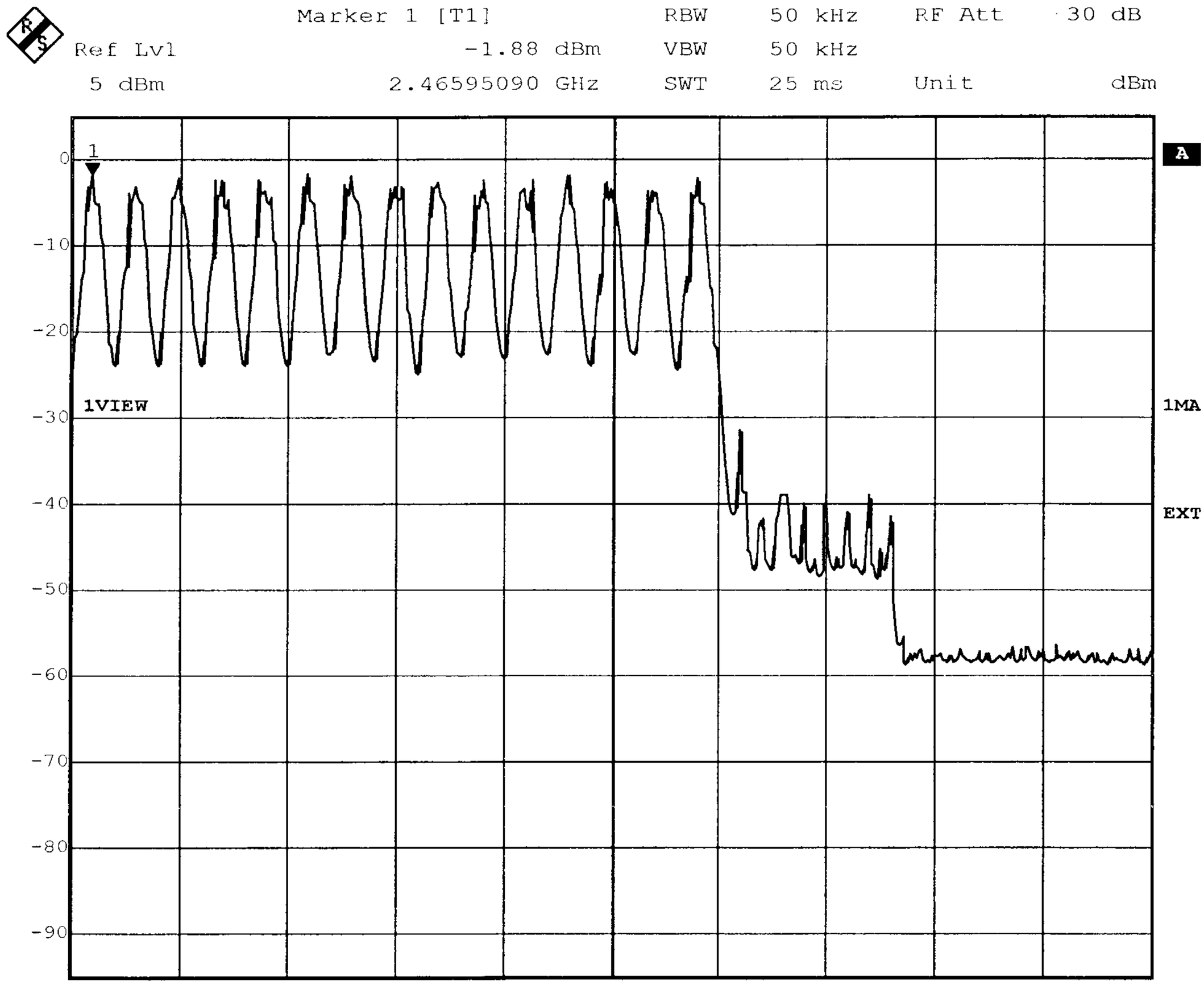
Title: Number of Hopping Frequencies Ch.: 0-13
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 12:44:57



Title: Number of Hopping Frequencies Ch.: 14-38
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 12:53:56



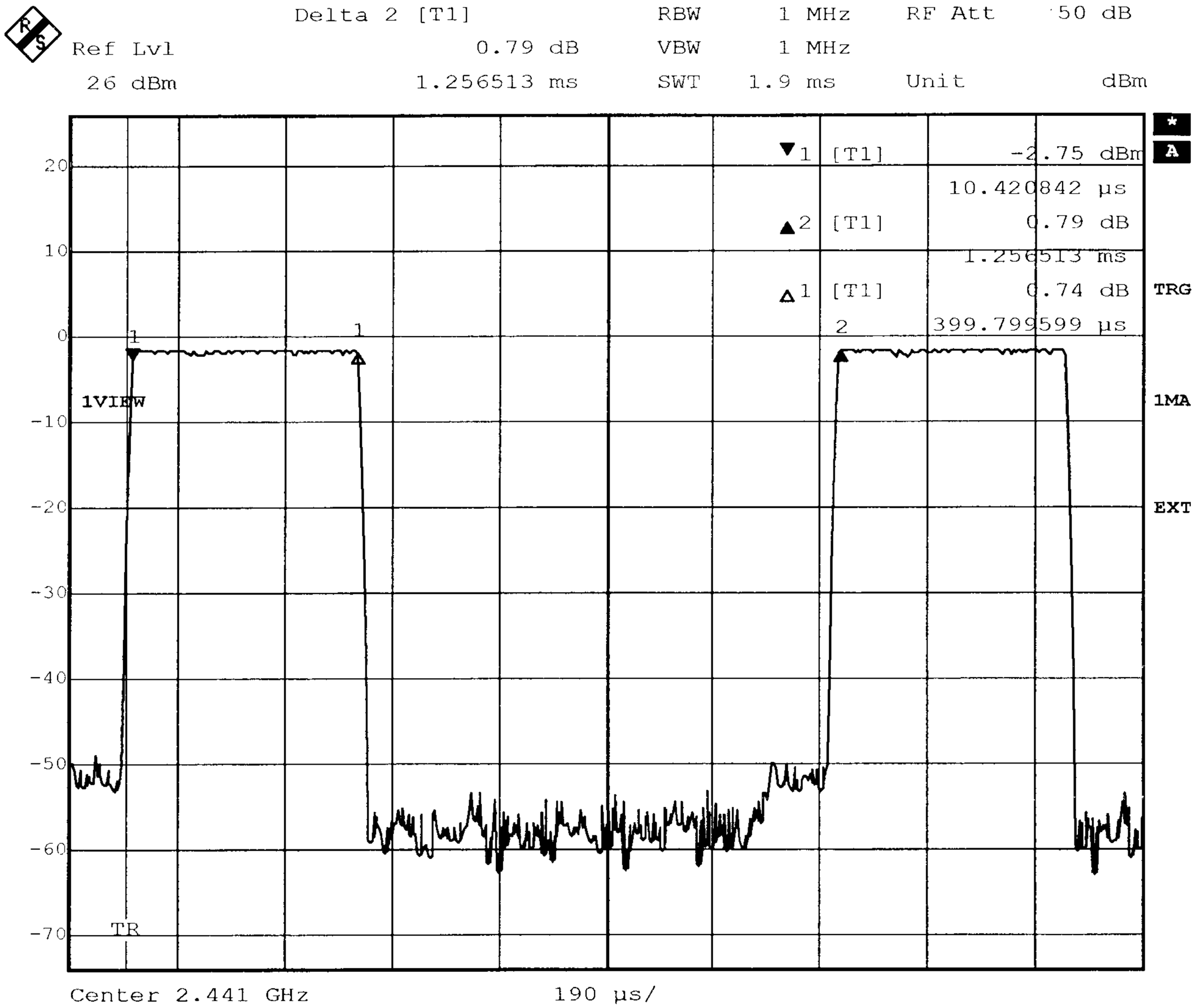
Title: Number of Hopping Frequencies Ch.: 39-63
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 12:58:40



Title: Number of Hopping Frequencies Ch.: 64-78
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 13:03:10

Appendix G

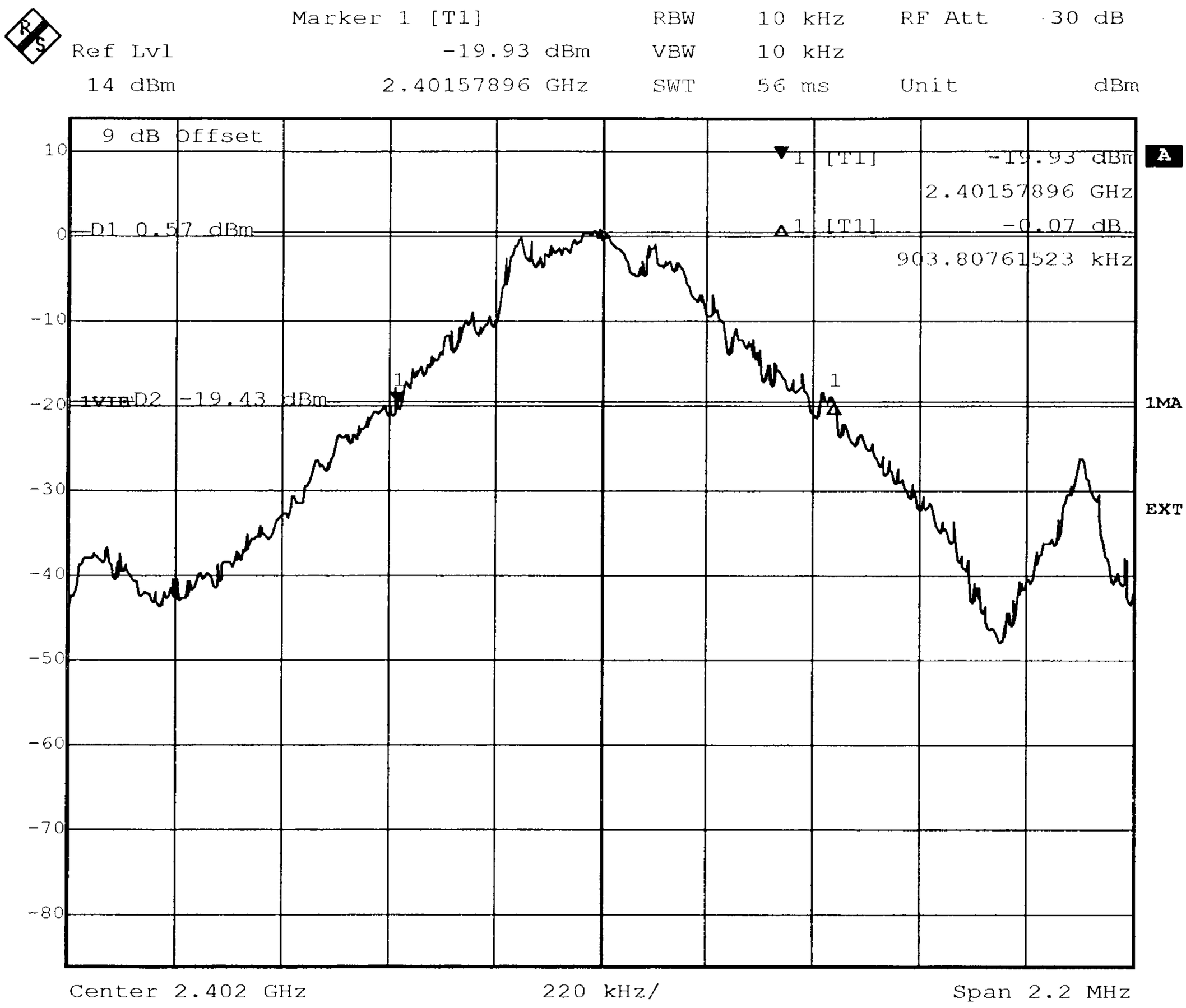
Time of Occupancy (Dwell Time)



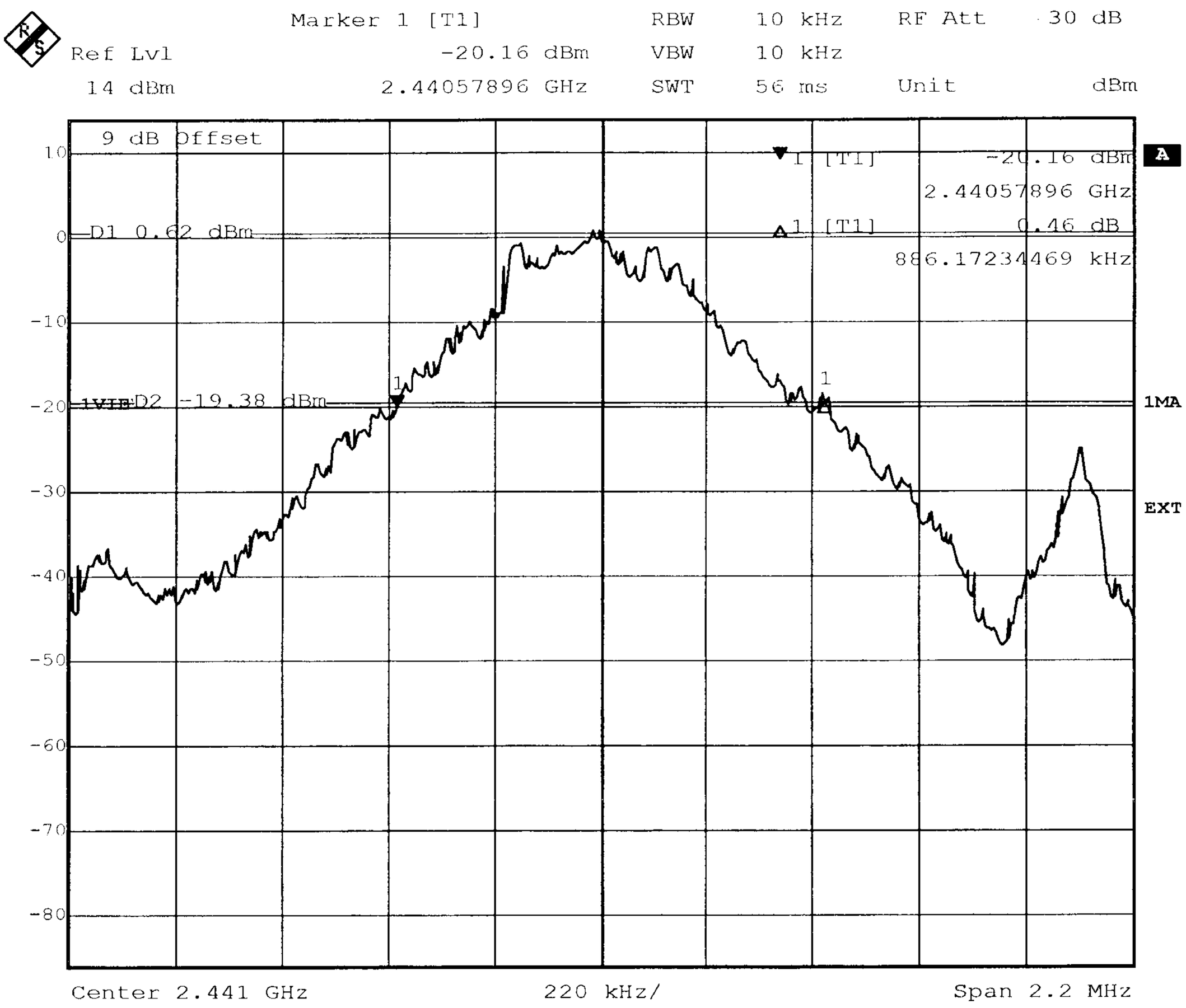
Title: Dwell Time
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 10:47:06

Appendix H

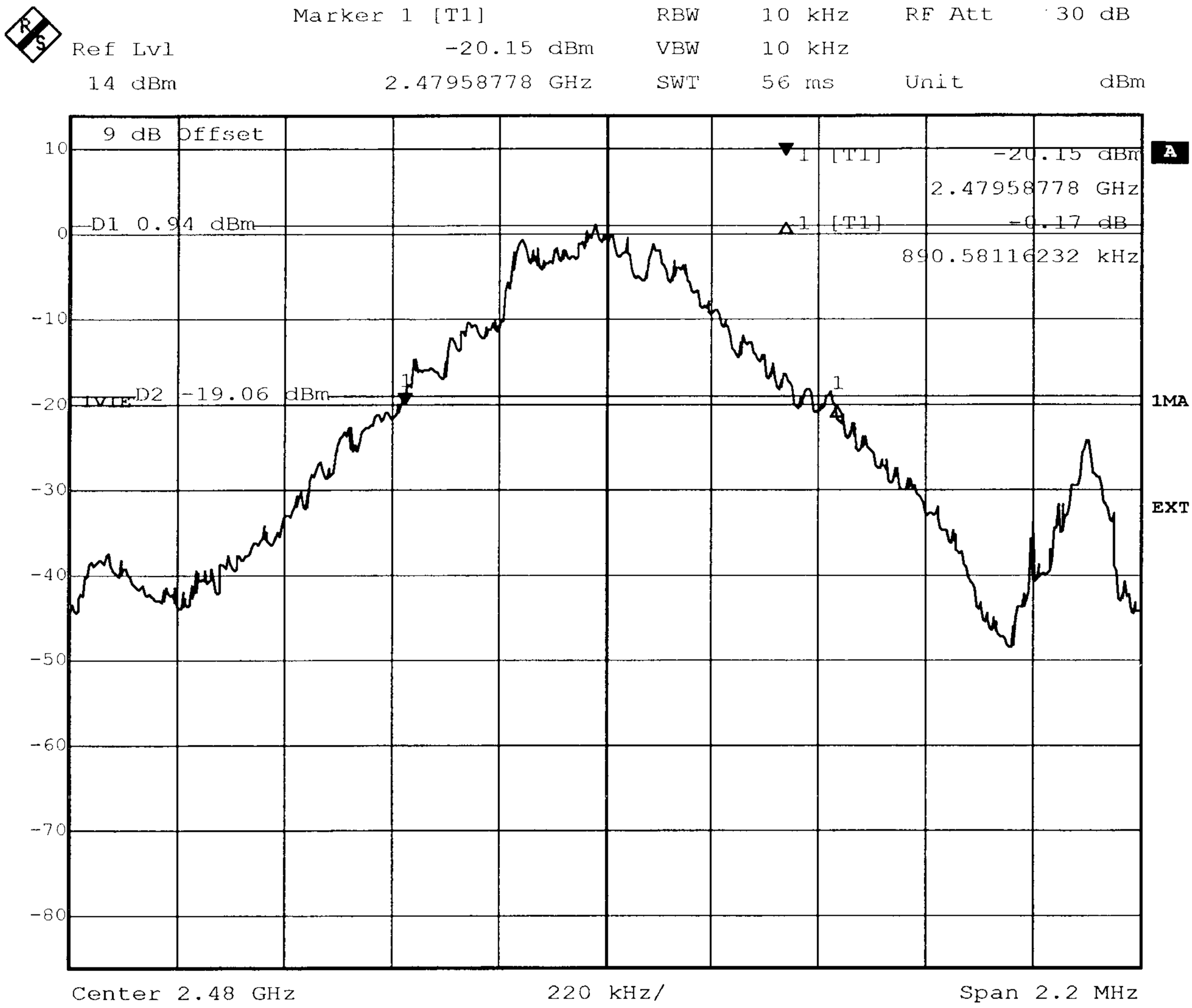
20dB Bandwidth



Title: 20 dB Bandwidth Ch.: 0
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 10:26:54



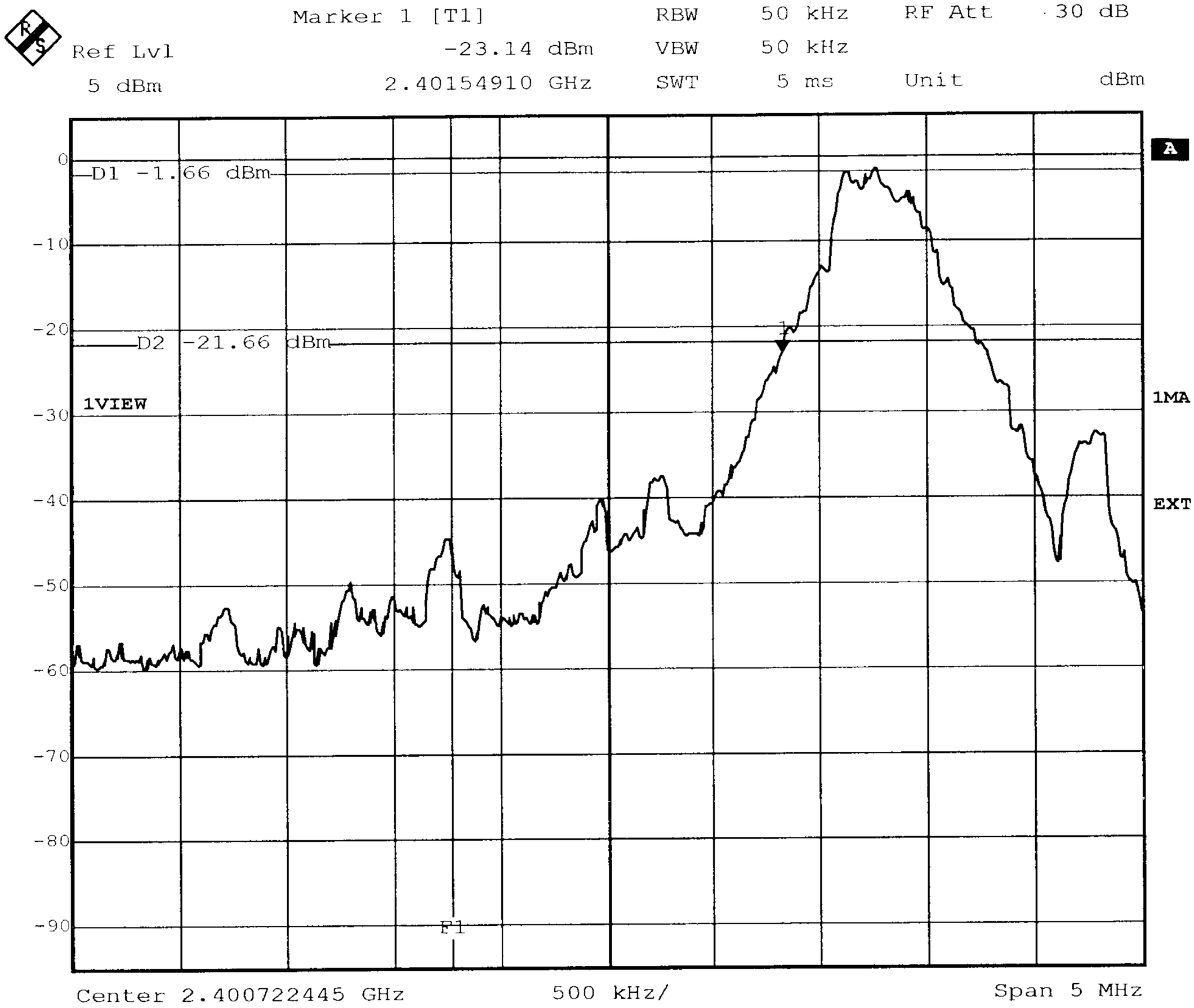
Title: 20 dB Bandwidth Ch.: 39
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 10:22:41



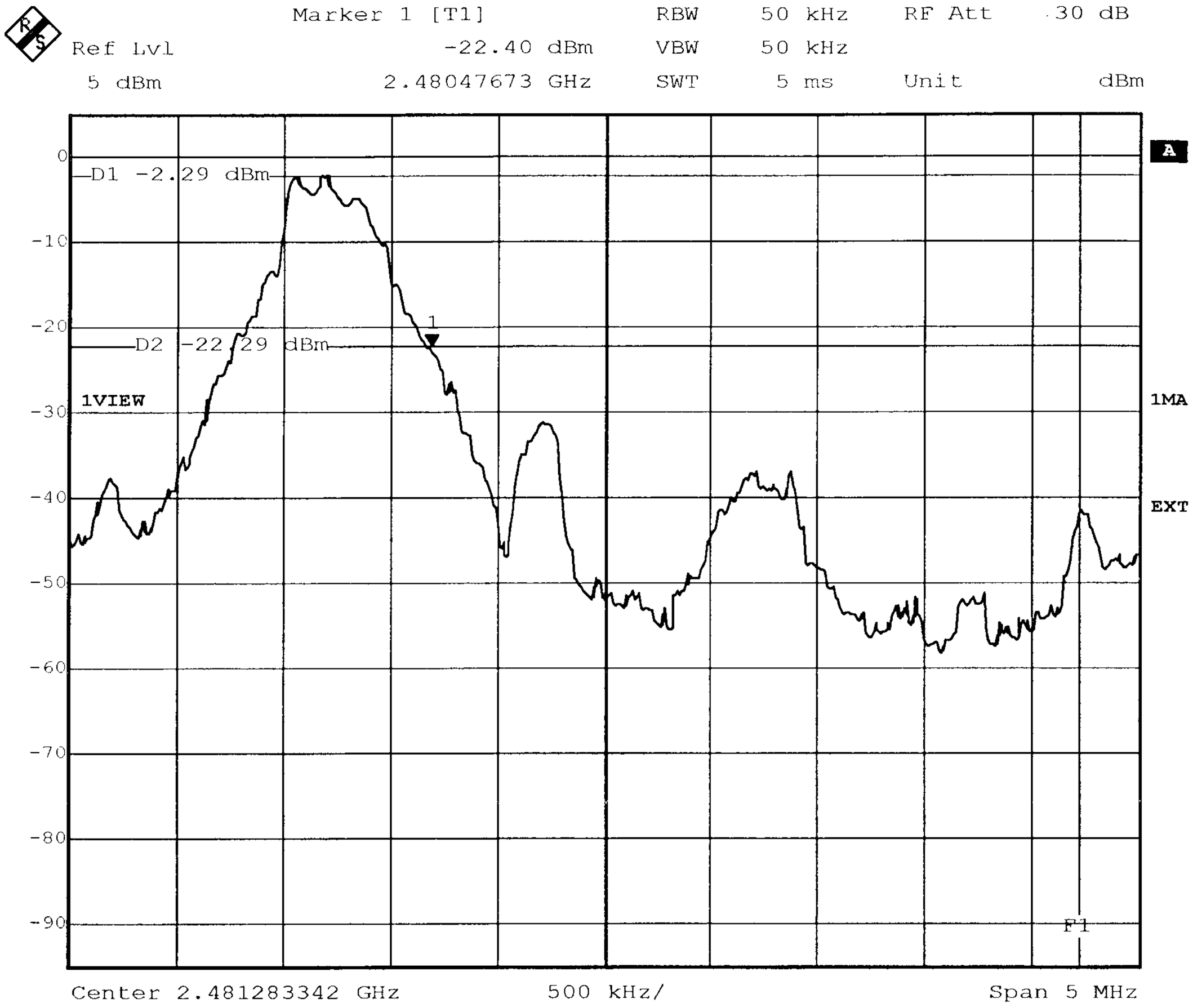
Title: 20 dB Bandwidth Ch.: 78
Comment A: Bluetooth Compactflash Card SOC1S02
Date: 28.NOV.2001 10:30:11

Appendix I

Band-edge Compliance of RF Emissions



Title: Band-edge Compliance of RF Conducted Emissions Ch.: 0
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 10:41:05



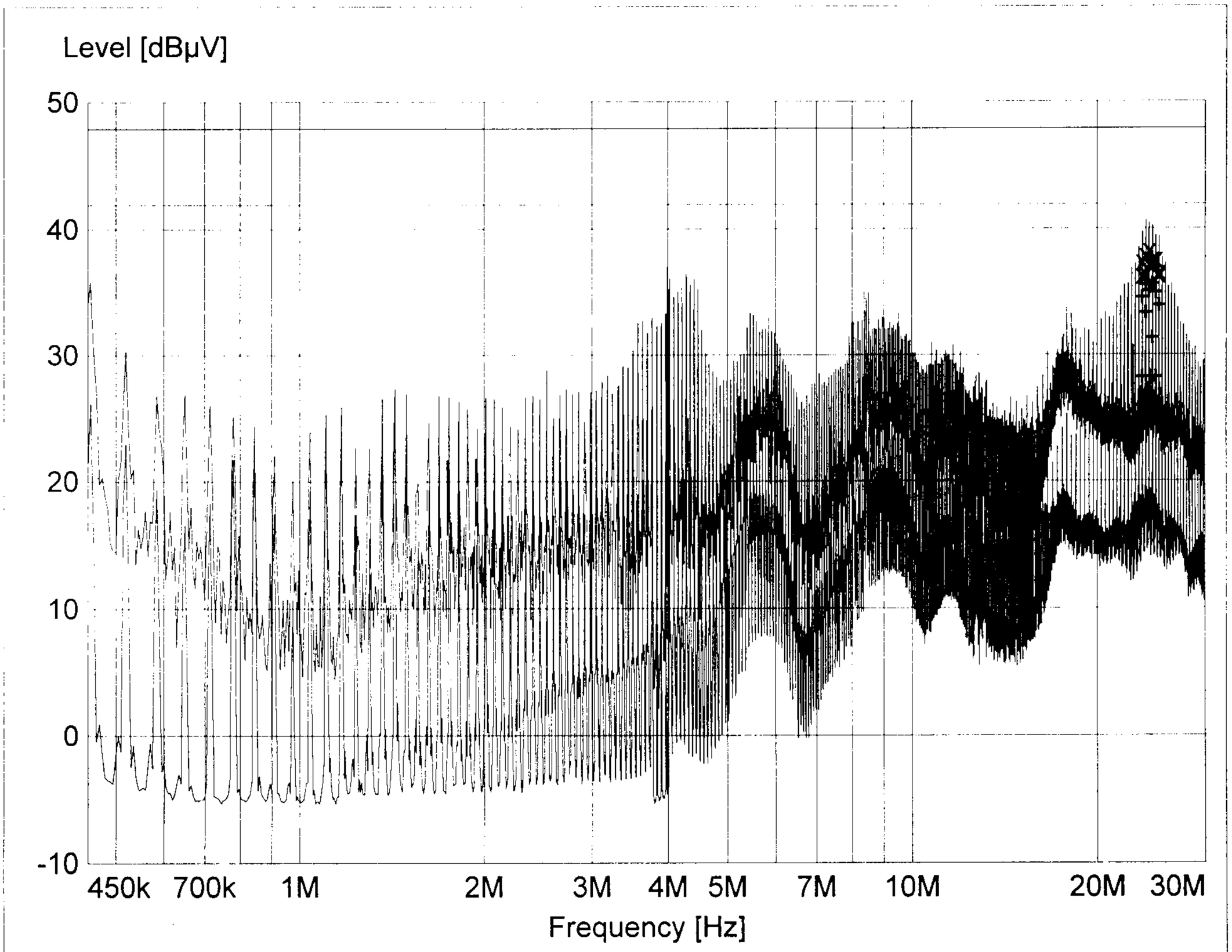
Title: Band-edge Compliance of RF Conducted Emissions Ch.: 78
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 10:34:31

Appendix J

Conducted Measurement at (AC) Power Line

EMI voltage test in the ac-mains according to FCC part 15

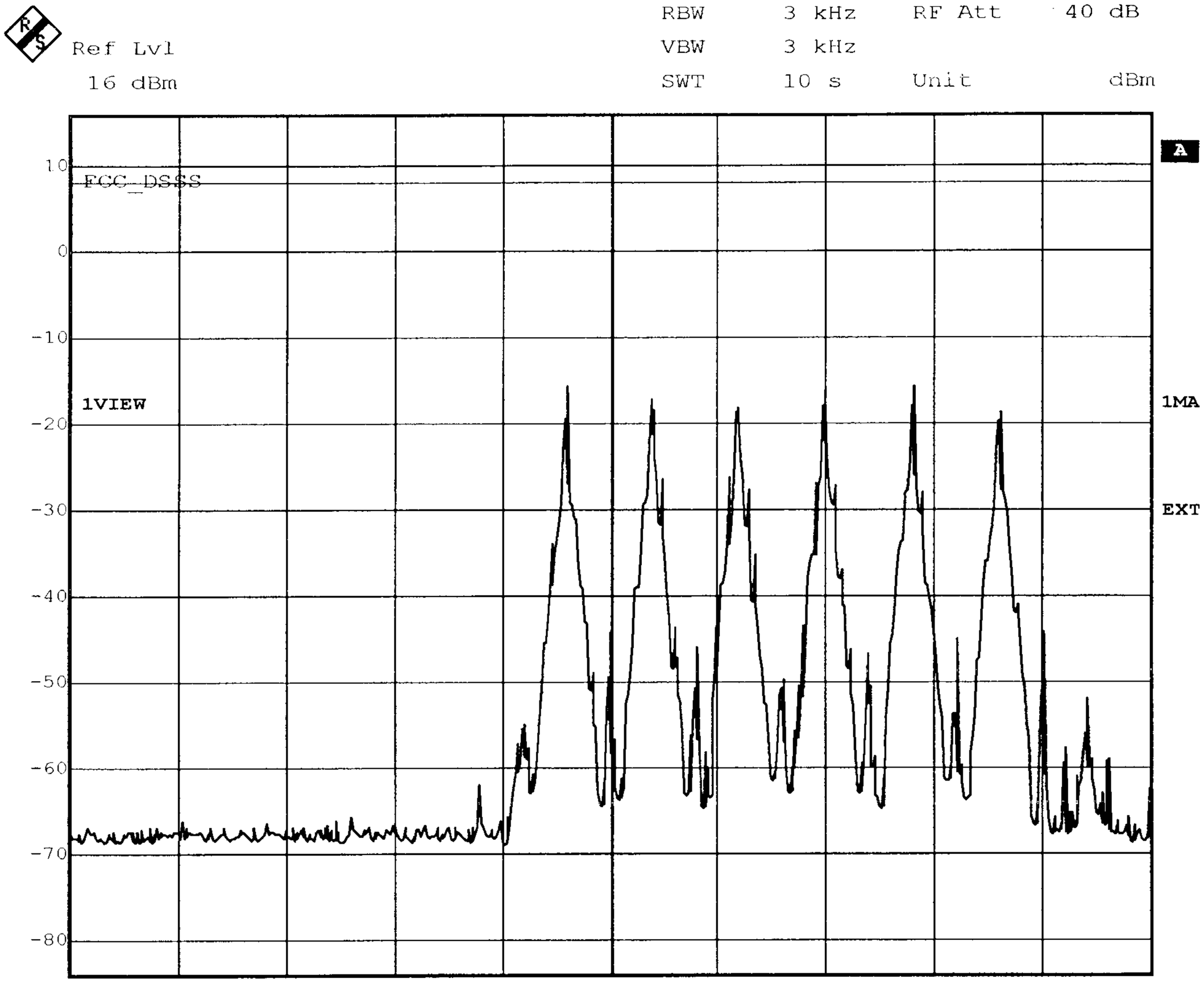
EUT:	BLUETOOTH COMPACT FLASH CARD
Manufacturer:	SysOnChip Inc.
Operating Condition:	Unom: 230VAC(AC/DC-adaptor), Tnom: 23°C
Test Site:	ETS
Operator:	Mr. Pflug
Test Specification:	V-Network: ESH3-Z5
Comment:	model: SOC1S02 mode: link + transmit
	(with IBM Thinkpad serie 1500 + Power Supply IBM 193)



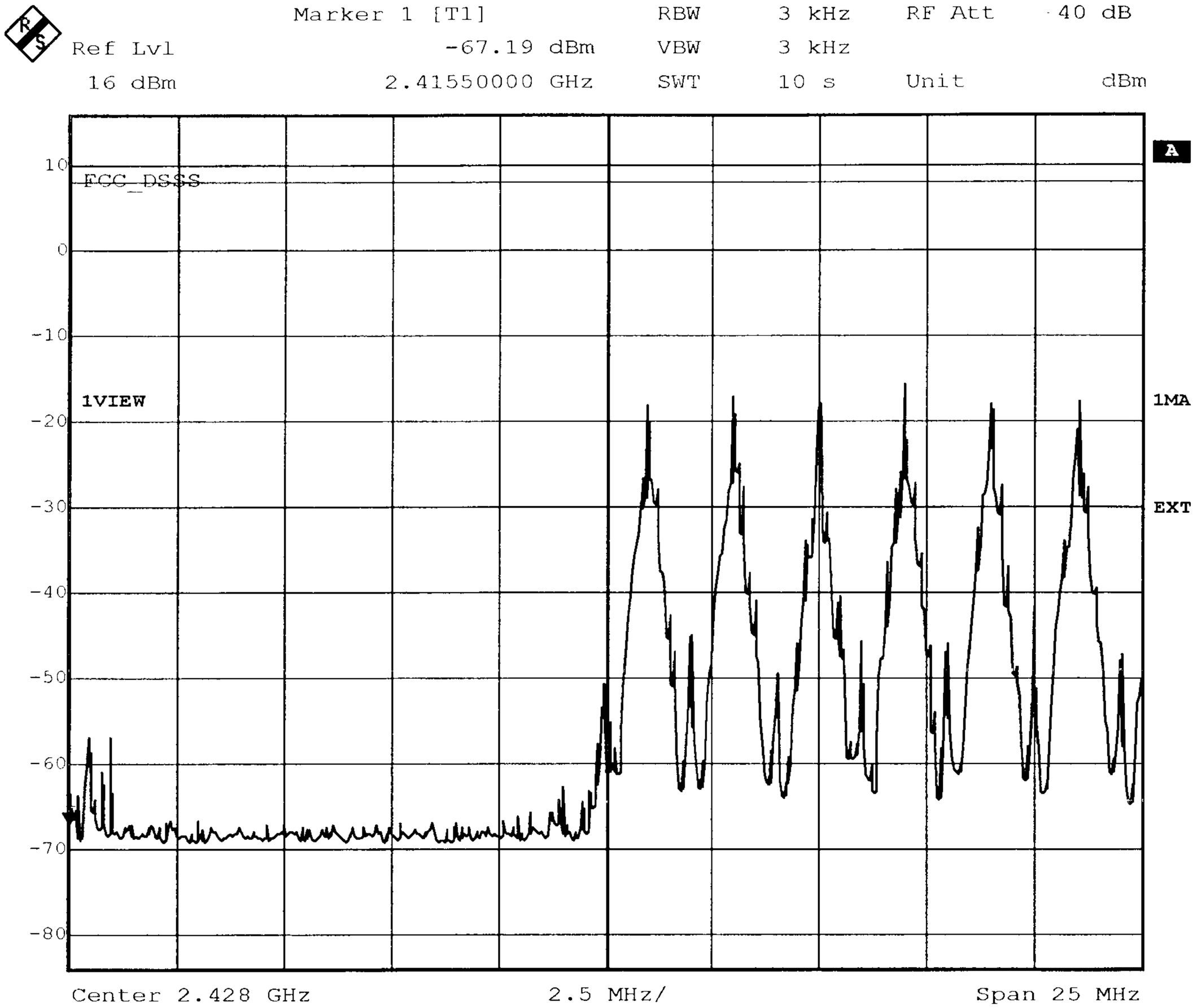
x x	MES	FCC_part15_fin QP	
+ +	MES	FCC_part15_fin AV	
———	MES	FCC_part15_pre PK	
———	MES	FCC_part15_pre AV	
———	LIM	FCC ClassB V QP	FCC ClassB, voltage
———	LIM	FCC_V_helpline	FCC ClassB, voltage

Appendix K

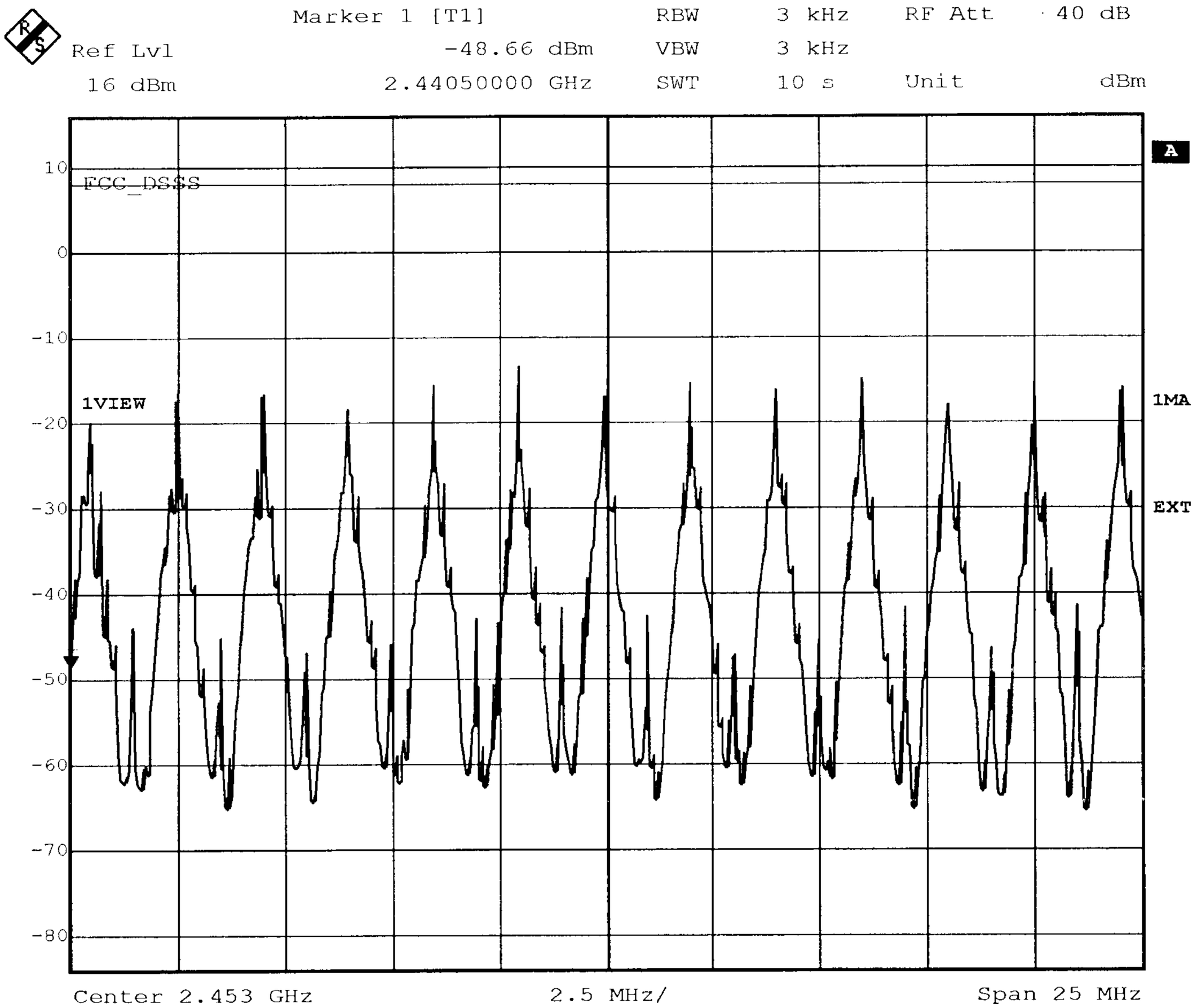
Peak Power Spectral Density (Master Inquiry Mode)



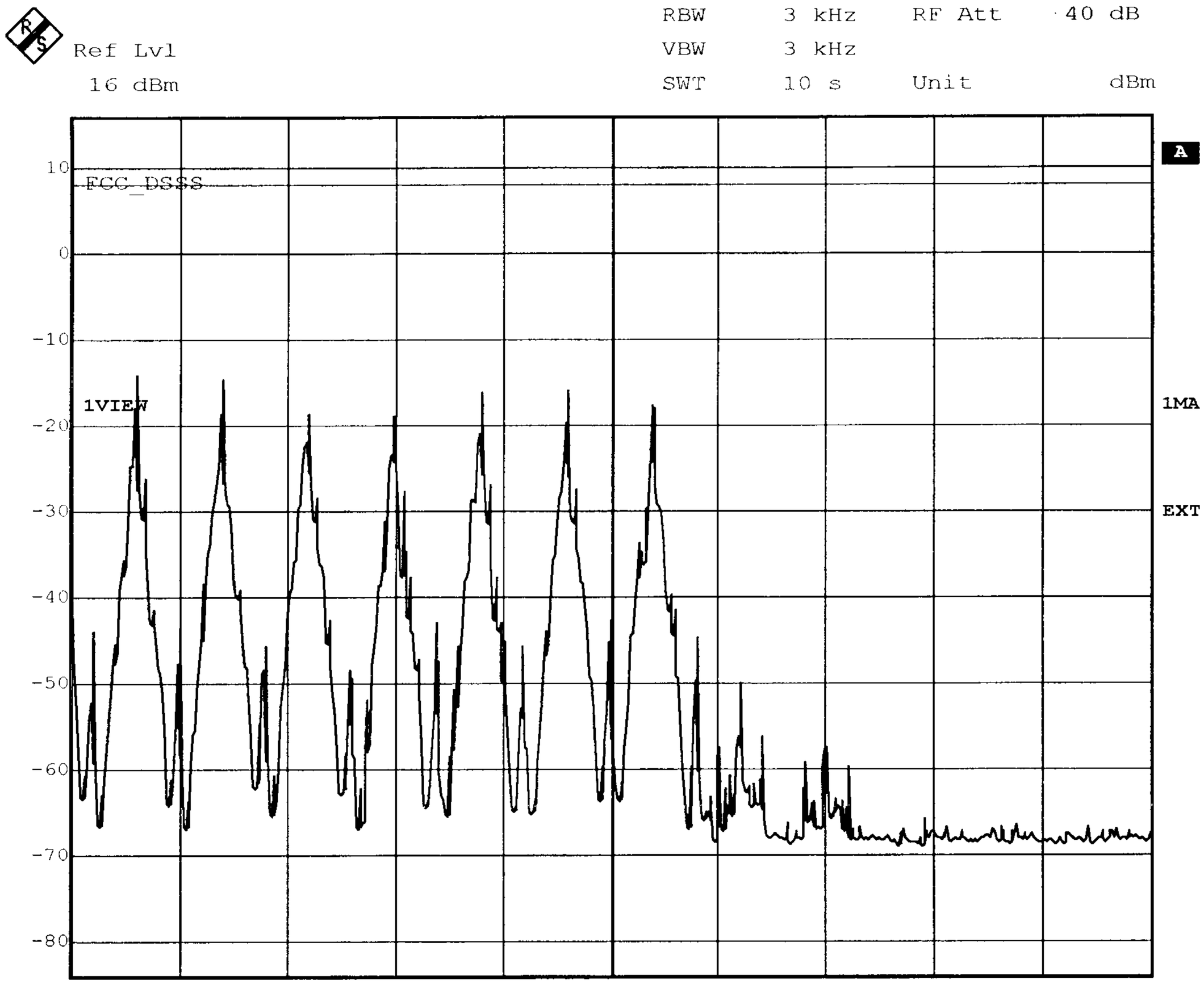
Title: Peak Power Spectral Density (Master Inquiry Mode)
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 13:11:05



Title: Peak Power Spectral Density (Master Inquiry Mode)
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 13:24:30



Title: Peak Power Spectral Density (Master Inquiry Mode)
Comment A: Bluetooth CompactFlash Card SOC1S02
Date: 28.NOV.2001 13:27:46



Title: Peak Power Spectral Density (Master Inquiry Mode)
Comment A: Bluetooth Compactflash Card SOC1S02
Date: 28.NOV.2001 13:35:01